Computer Architecture

Lecture 4: Main Memory and DRAM Fundamentals

Prof. Onur Mutlu
ETH Zürich

Fall 2017

28 September 2017

My Office Hours Tomorrow

- Friday, 29 September 2017
- 14:00-15:30

High-Level Summary of Last Lecture

- Issues in Caching
- More Effective Cache Design
- Memory Level Parallelism
- Miss Buffers (Miss Status Handling Registers)

Agenda for Today

- Enabling High Bandwidth Memories
- Main Memory System: A Broad Perspective
- DRAM Fundamentals and Operation
- Memory Controllers

Review: Hybrid Cache Replacement

- Problem: Not a single policy provides the highest performance
  - For any given set
  - For the entire cache overall

- Idea: Implement both policies and pick the one that is expected to perform best at runtime
  - On a per-set basis or for the entire cache

  + Higher performance

  -- Higher cost, complexity; Need selection mechanism

- How do you determine the best policy?
  - Implement multiple tag stores, each following a particular policy
  - Find the best and have the main tag store follow the best policy

Qureshi et al., "A Case for MLP-Aware Cache Replacement," ISCA 2006.

Required Reading on Hybrid Replacement

- Moinuddin K. Qureshi, Daniel N. Lynch, Onur Mutlu, and Yale N. Patt, **"A Case for MLP-Aware Cache Replacement"** *Proceedings of the 33rd International Symposium on Computer Architecture (**ISCA**)*, pages 167-177, Boston, MA, June 2006. Slides (ppt)

A Case for MLP-Aware Cache Replacement

Moinuddin K. Qureshi Daniel N. Lynch Onur Mutlu Yale N. Patt
Department of Electrical and Computer Engineering
The University of Texas at Austin
{*moin, lynch, onur, patt*}*@hps.utexas.edu*

Enabling High Bandwidth Memories

Multiple Instructions per Cycle

- Processors can generate multiple cache/memory accesses per cycle
- How do we ensure the cache/memory can handle multiple accesses in the same clock cycle?

- Solutions:
  - true multi-porting
  - virtual multi-porting (time sharing a port)
  - multiple cache copies
  - banking (interleaving)

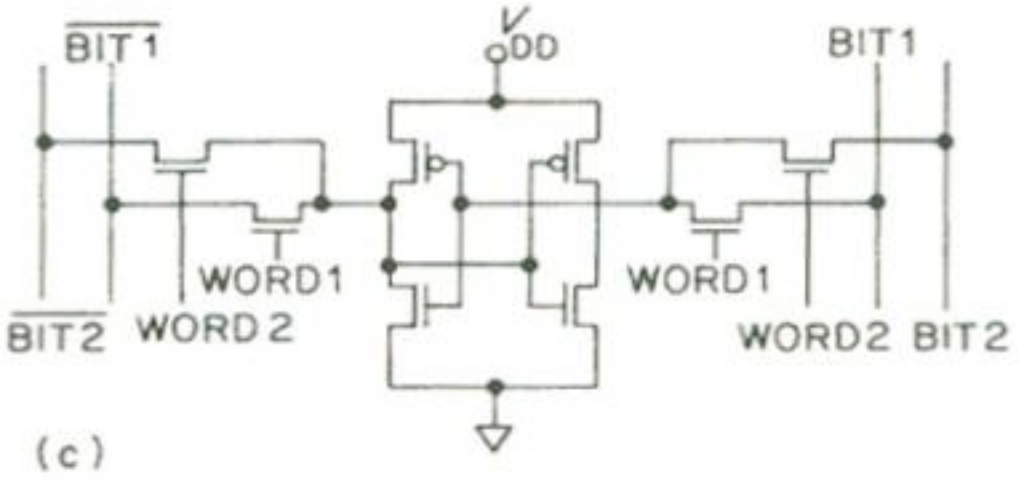
Handling Multiple Accesses per Cycle (I)

- True multiporting
  - Each memory cell has multiple read or write ports

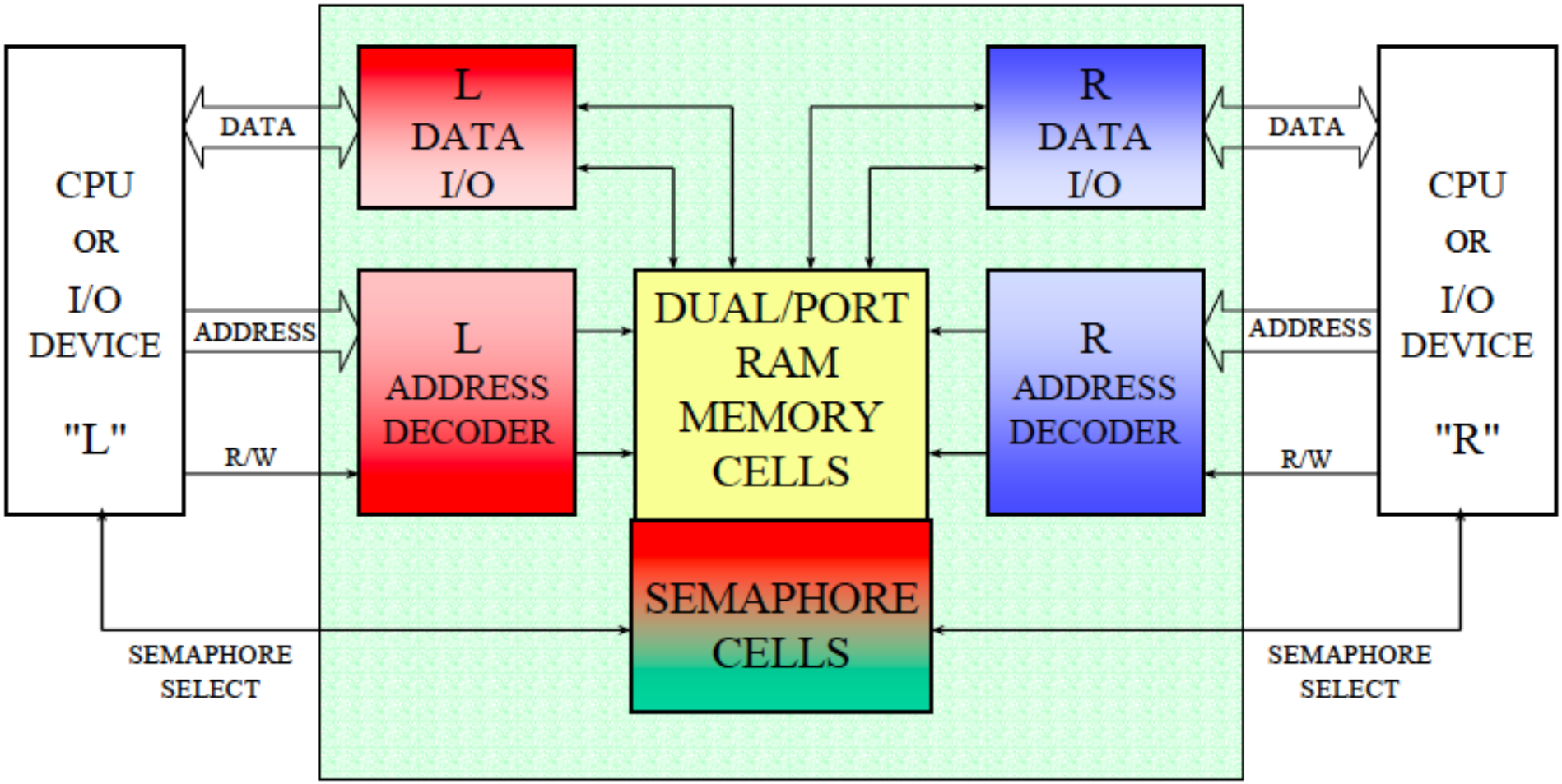
+ Truly concurrent accesses (no conflicts on read accesses)

-- Expensive in terms of latency, power, area

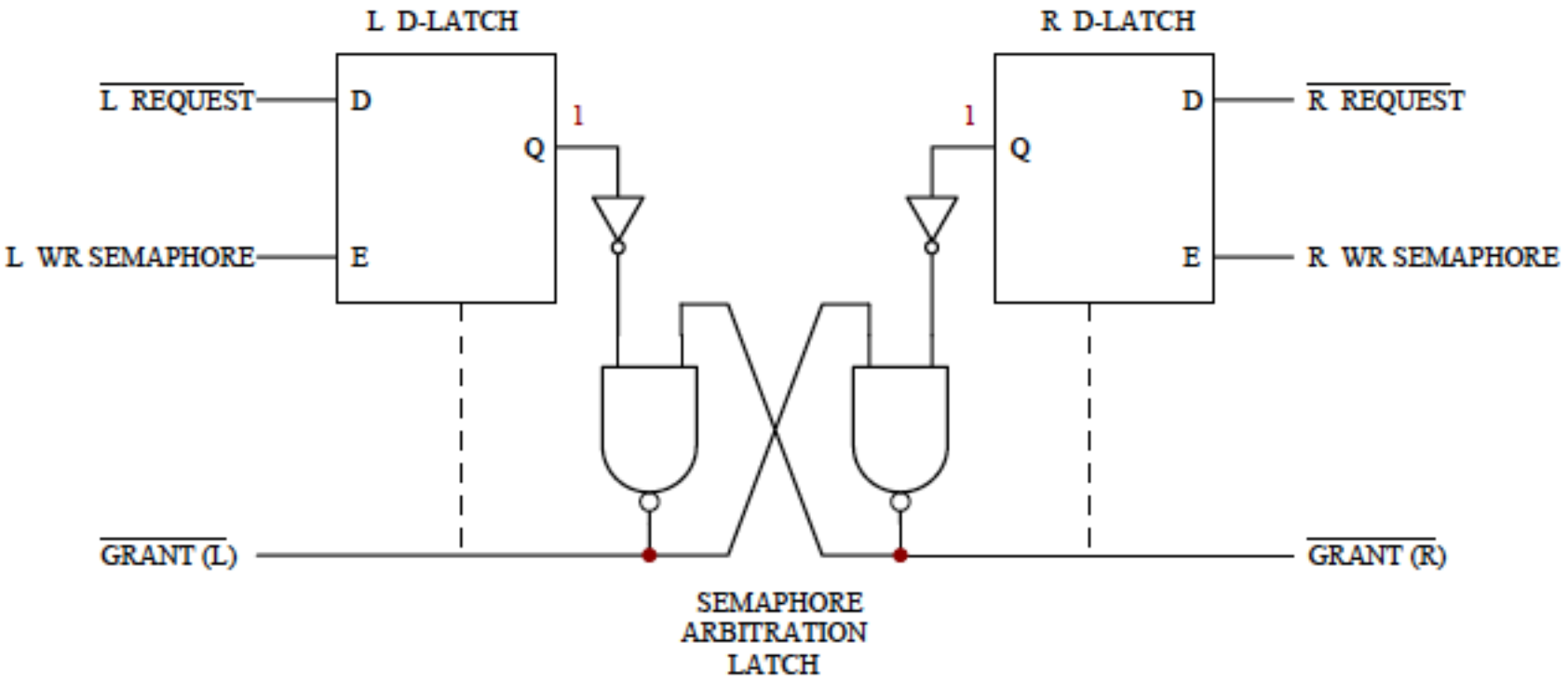
  - What about read and write to the same location at the same time?
    - Peripheral logic needs to handle this



Peripheral Logic for True Multiporting



Peripheral Logic for True Multiporting

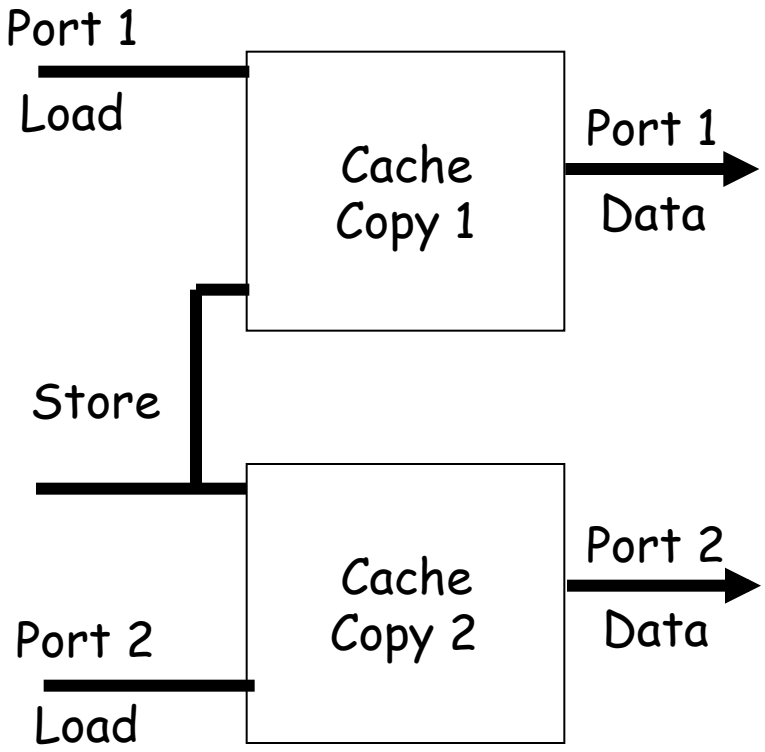


Handling Multiple Accesses per Cycle (II)

- Virtual multiporting
  - Time-share a single port
  - Each access needs to be (significantly) shorter than clock cycle
  - Used in Alpha 21264
  - Is this scalable?

Handling Multiple Accesses per Cycle (III)

- Multiple cache copies
  - Stores update both caches
  - Loads proceed in parallel
- Used in Alpha 21164
- Scalability?
  - Store operations cause a bottleneck
  - Area proportional to “ports”



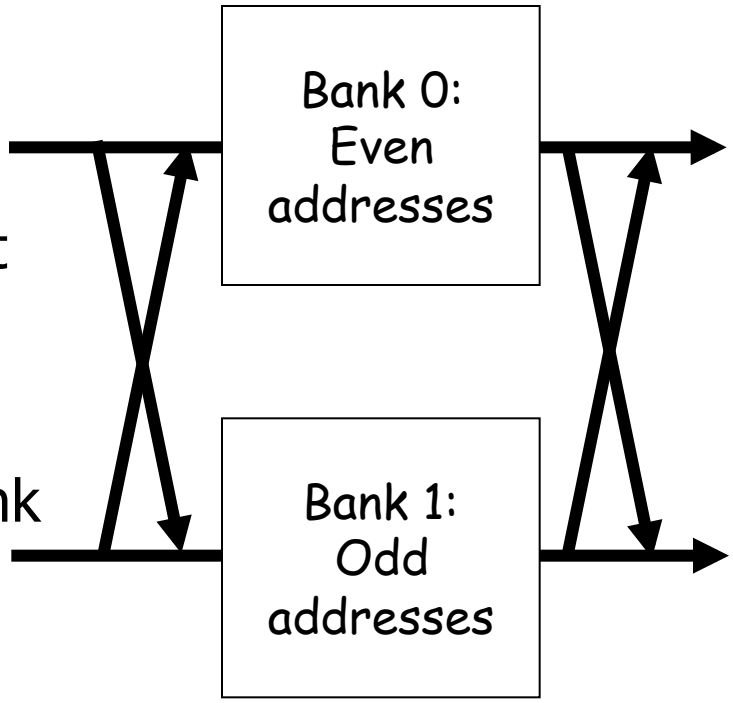
Handling Multiple Accesses per Cycle (III)

- Banking (Interleaving)
  - Address space partitioned into separate banks
    - Bits in address determines which bank an address maps to
    - Which bits to use for "bank address"?

  + No increase in data store area

  -- Cannot satisfy multiple accesses to the same bank in parallel

  -- Crossbar interconnect in input/output



- Bank conflicts
  - Concurrent requests to the same bank
  - How can these be reduced?
    - Hardware? Software?

General Principle: Interleaving

- Interleaving (banking)
  - Problem: a single monolithic memory array takes long to access and does not enable multiple accesses in parallel
  - Goal: Reduce the latency of memory array access and enable multiple accesses in parallel
  - Idea: Divide the array into multiple banks that can be accessed independently (in the same cycle or in consecutive cycles)
    - Each bank is smaller than the entire memory storage
    - Access latencies to different banks can be overlapped
  - A Key Issue: How do you map data to different banks? (i.e., how do you interleave data across banks?)

Further Readings on Caching and MLP

- Required: Qureshi et al., "A Case for MLP-Aware Cache Replacement," ISCA 2006.
- One Pager: Glew, "MLP Yes! ILP No!," ASPLOS Wild and Crazy Ideas Session, 1998.
- Mutlu et al., "Runahead Execution: An Effective Alternative to Large Instruction Windows," IEEE Micro 2003.
- Li et al., "Utility-based Hybrid Memory Management," CLUSTER 2017.
- Mutlu et al., "Parallelism-Aware Batch Scheduling," ISCA 2008

The Main Memory System

State-of-the-art in Main Memory (circa 2015)

- Recommended Reading

- Onur Mutlu and Lavanya Subramanian,
  "Research Problems and Opportunities in Memory Systems"
  Invited Article in
  Supercomputing Frontiers and Innovations (***SUPERFRI***),
  2014.

Required Readings on DRAM

- DRAM Organization and Operation Basics
  - Sections 1 and 2 of: Lee et al., "Tiered-Latency DRAM: A Low Latency and Low Cost DRAM Architecture," HPCA 2013.
    https://people.inf.ethz.ch/omutlu/pub/tldram_hpca13.pdf
  - Sections 1 and 2 of Kim et al., "A Case for Subarray-Level Parallelism (SALP) in DRAM," ISCA 2012.
    https://people.inf.ethz.ch/omutlu/pub/salp-dram_isca12.pdf
- DRAM Refresh Basics
  - Sections 1 and 2 of Liu et al., "RAIDR: Retention-Aware Intelligent DRAM Refresh," ISCA 2012.
    https://people.inf.ethz.ch/omutlu/pub/raidr-dram-refresh_isca12.pdf

Reading on Simulating Main Memory

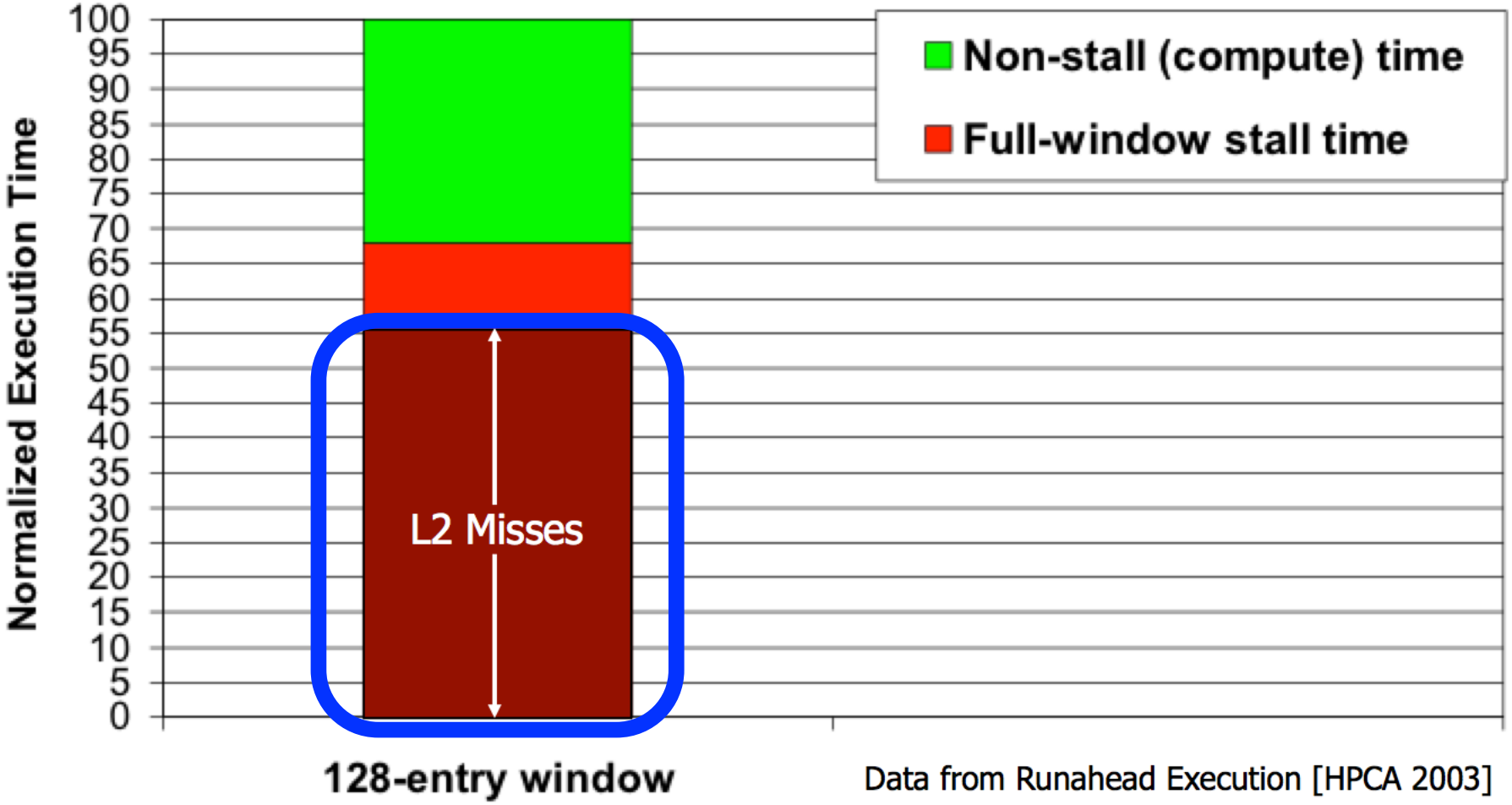
- How to evaluate future main memory systems?
- An open-source simulator and its brief description

- Yoongu Kim, Weikun Yang, and Onur Mutlu,
  "Ramulator: A Fast and Extensible DRAM Simulator"
  IEEE Computer Architecture Letters (***CAL***), March 2015.
  [Source Code]

Why Is Memory So Important? (Especially Today)

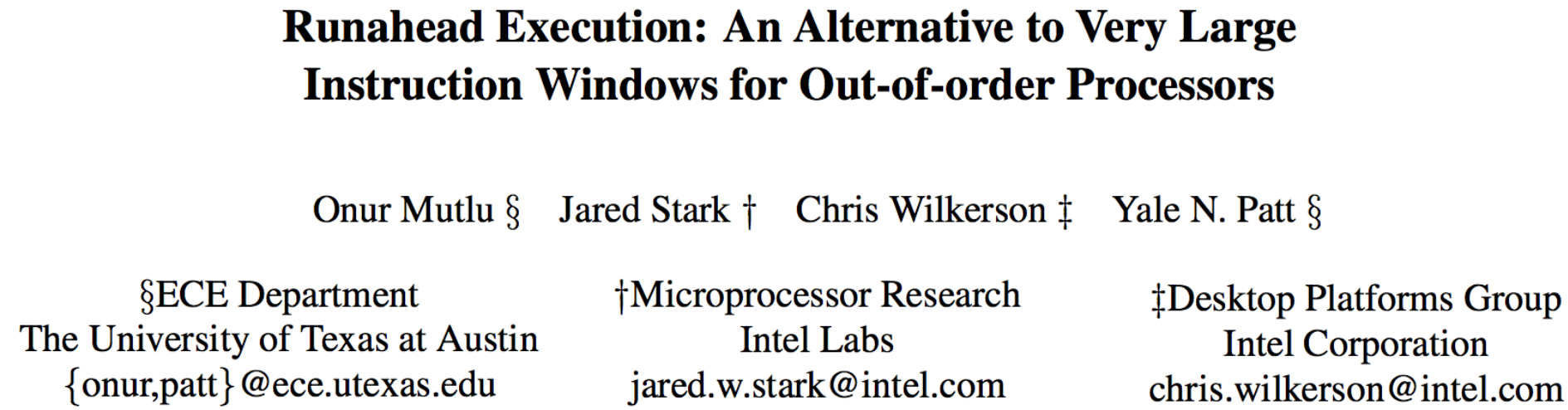
The Performance Perspective

- "**It's the Memory, Stupid!**" (Richard Sites, MPR, 1996)



The Performance Perspective

- Onur Mutlu, Jared Stark, Chris Wilkerson, and Yale N. Patt,
  "Runahead Execution: An Alternative to Very Large Instruction Windows for Out-of-order Processors"
  *Proceedings of the 9th International Symposium on High-Performance Computer Architecture (**HPCA**)*, pages 129-140, Anaheim, CA, February 2003.
  Slides (pdf)



Runahead Execution: An Alternative to Very Large Instruction Windows for Out-of-order Processors

Onur Mutlu § Jared Stark † Chris Wilkerson ‡ Yale N. Patt §

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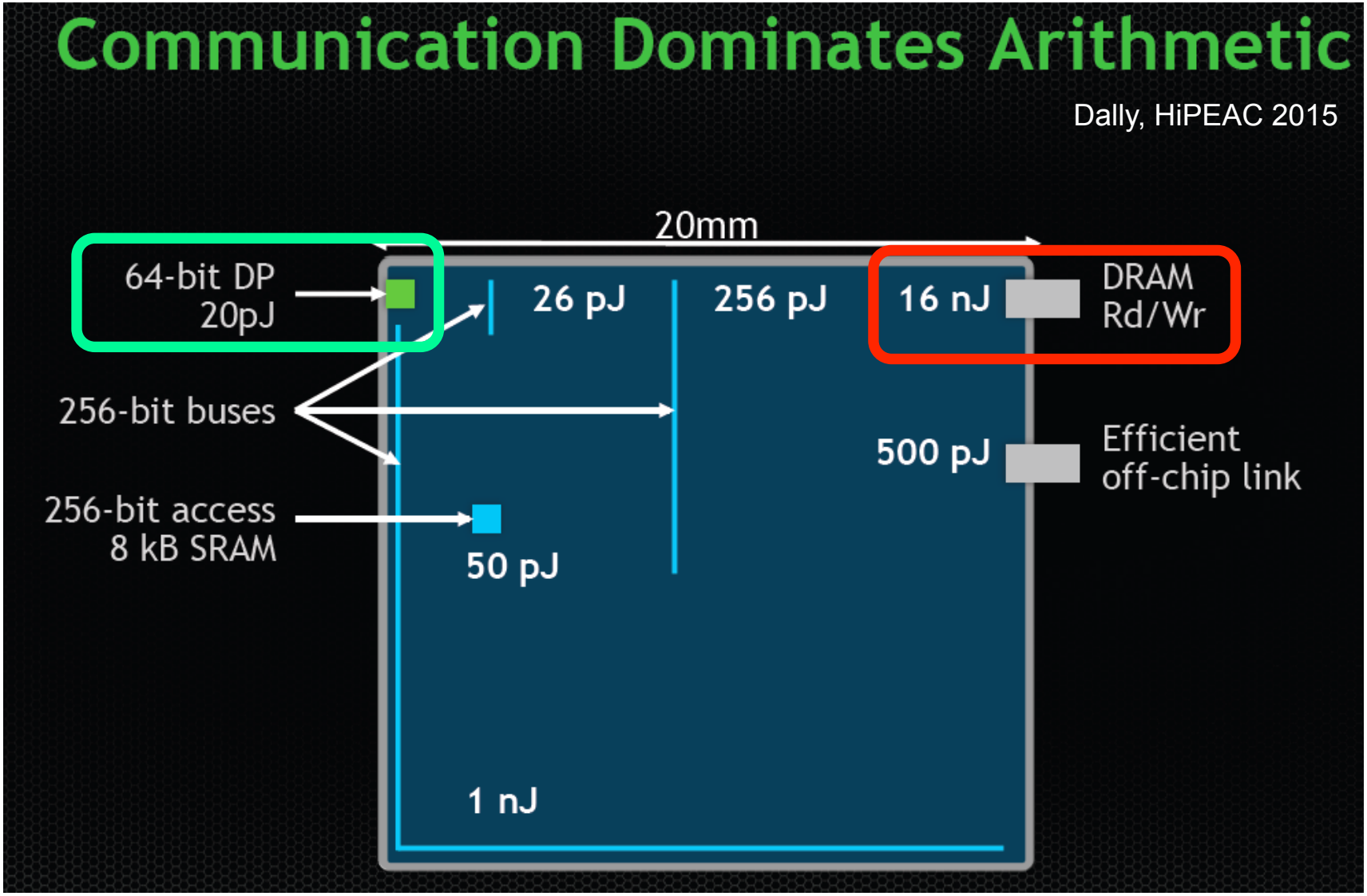
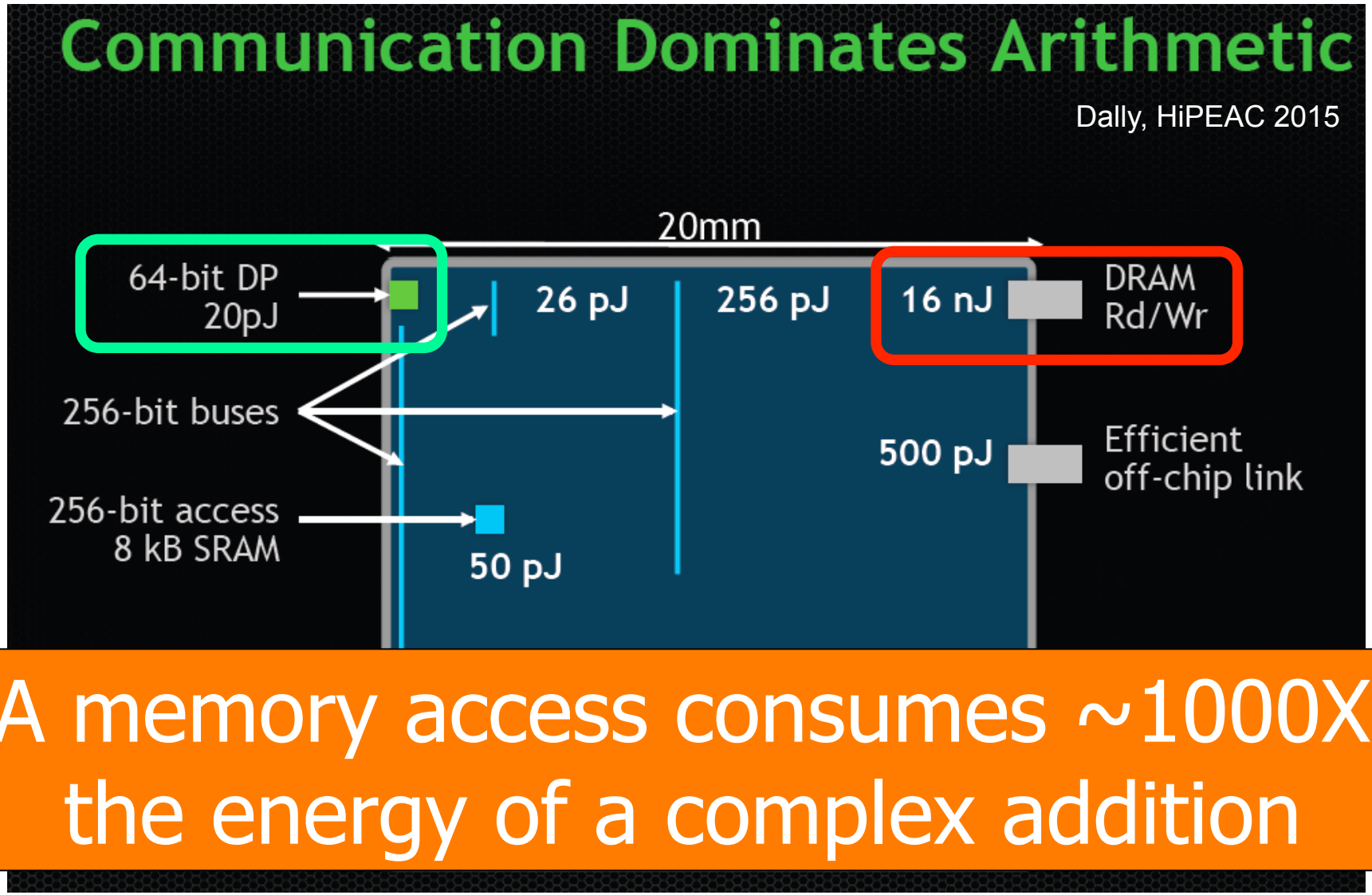
The Energy Perspective



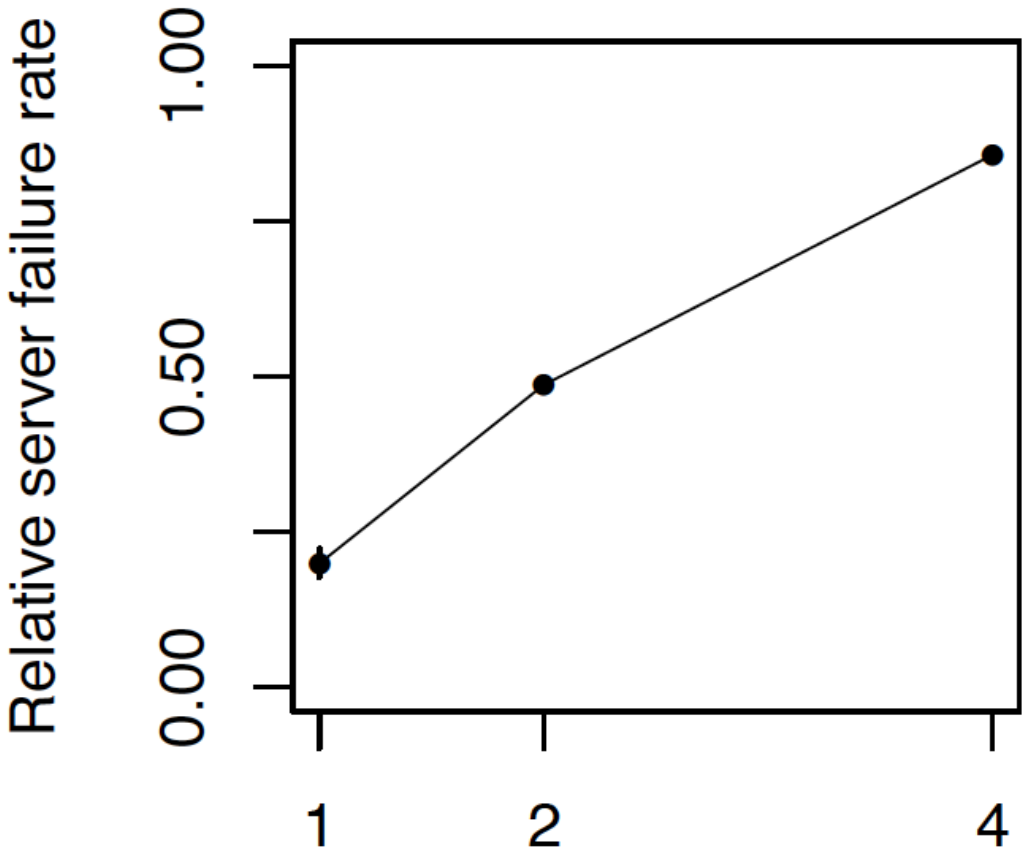
The Energy Perspective



A memory access consumes ~1000X the energy of a complex addition

The Reliability Perspective

- Data from all of Facebook's servers worldwide
- Meza+, "Revisiting Memory Errors in Large-Scale Production Data Centers," DSN'15.



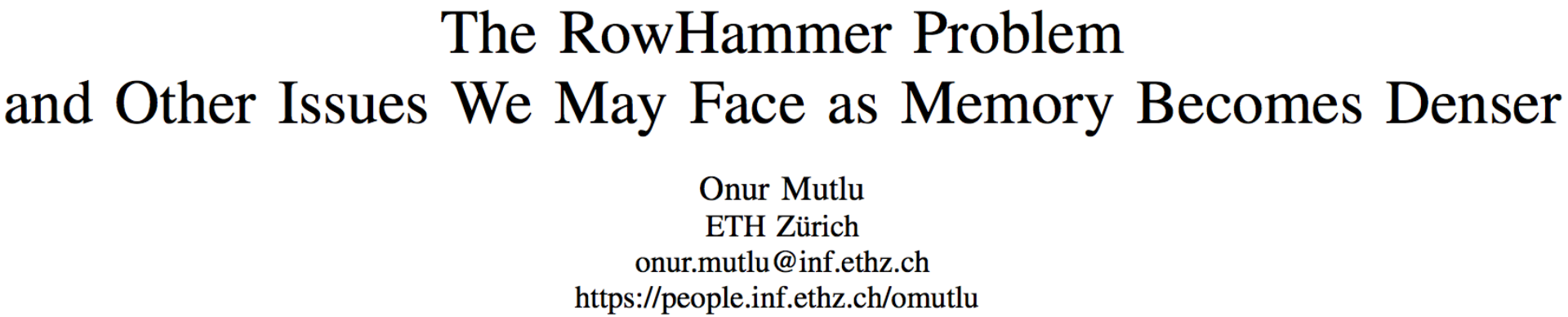
Intuition: quadratic increase in capacity

The Security Perspective

It's like breaking into an apartment by repeatedly slamming a neighbor's door until the vibrations open the door you were after

The Reliability & Security Perspectives

- Onur Mutlu,
  "The RowHammer Problem and Other Issues We May Face as Memory Becomes Denser"
  Invited Paper in Proceedings of the
  Design, Automation, and Test in Europe Conference (***DATE***), Lausanne, Switzerland, March 2017.
  [Slides (pptx) (pdf)]



The RowHammer Problem
and Other Issues We May Face as Memory Becomes Denser

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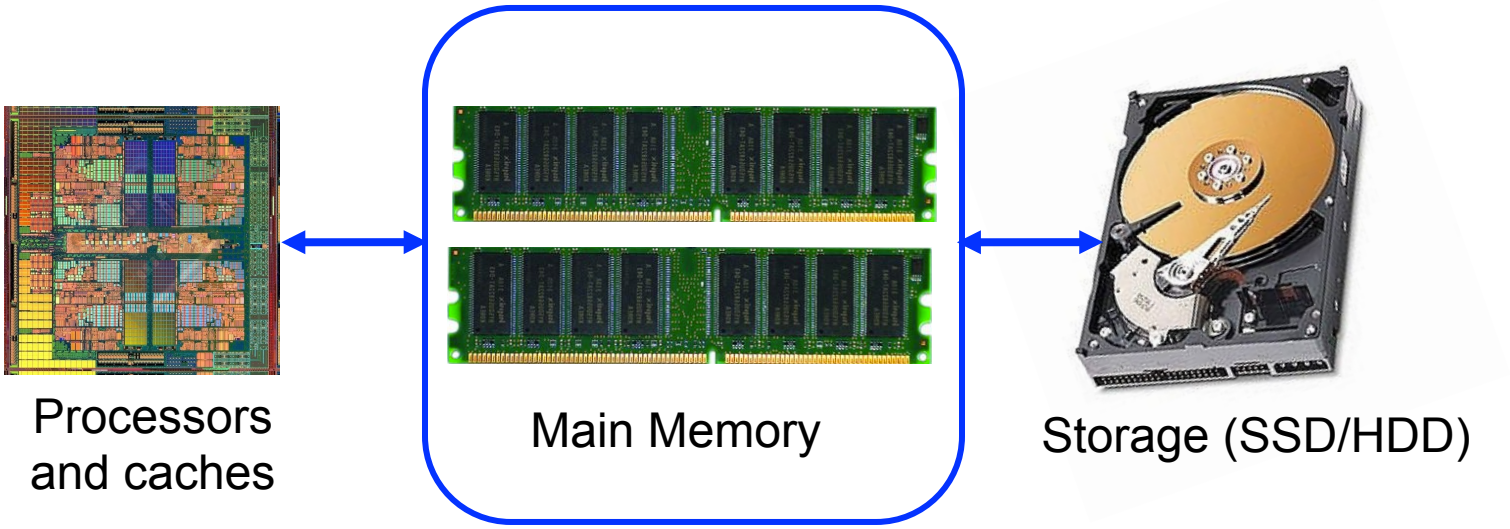
Trends, Challenges, and Opportunities in Main Memory

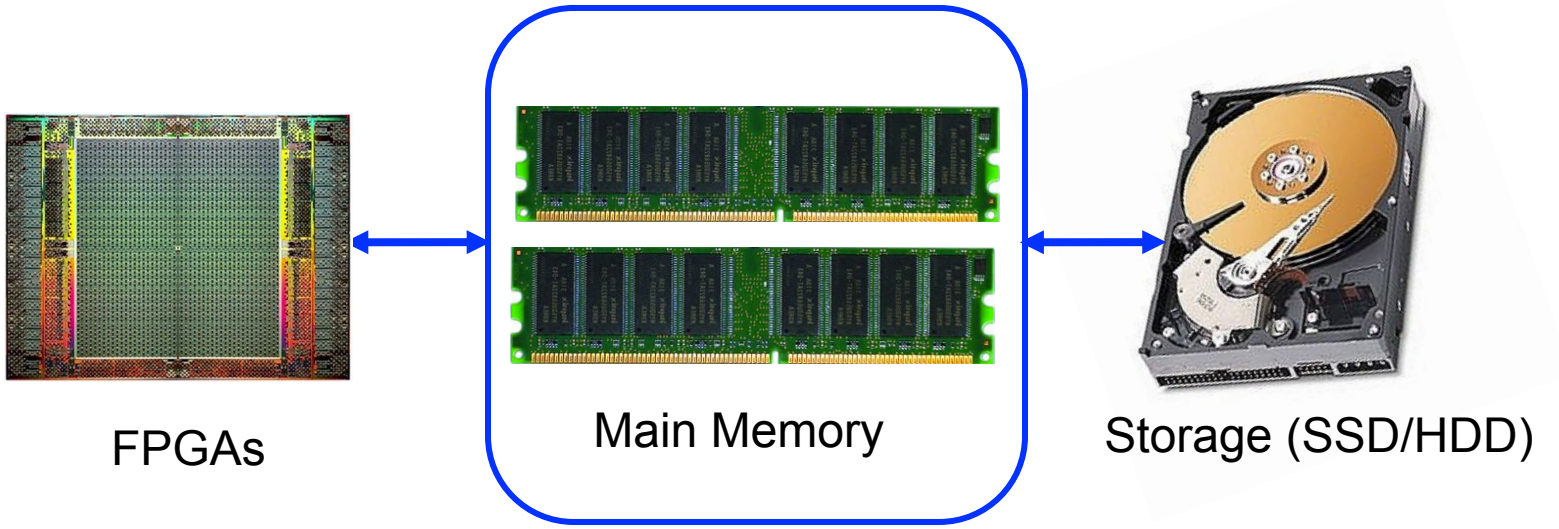
The Main Memory System



- Main memory is a critical component of all computing systems: server, mobile, embedded, desktop, sensor

- Main memory system must scale (in *size*, *technology*, *efficiency*, *cost*, and *management algorithms*) to maintain performance growth and technology scaling benefits

The Main Memory System



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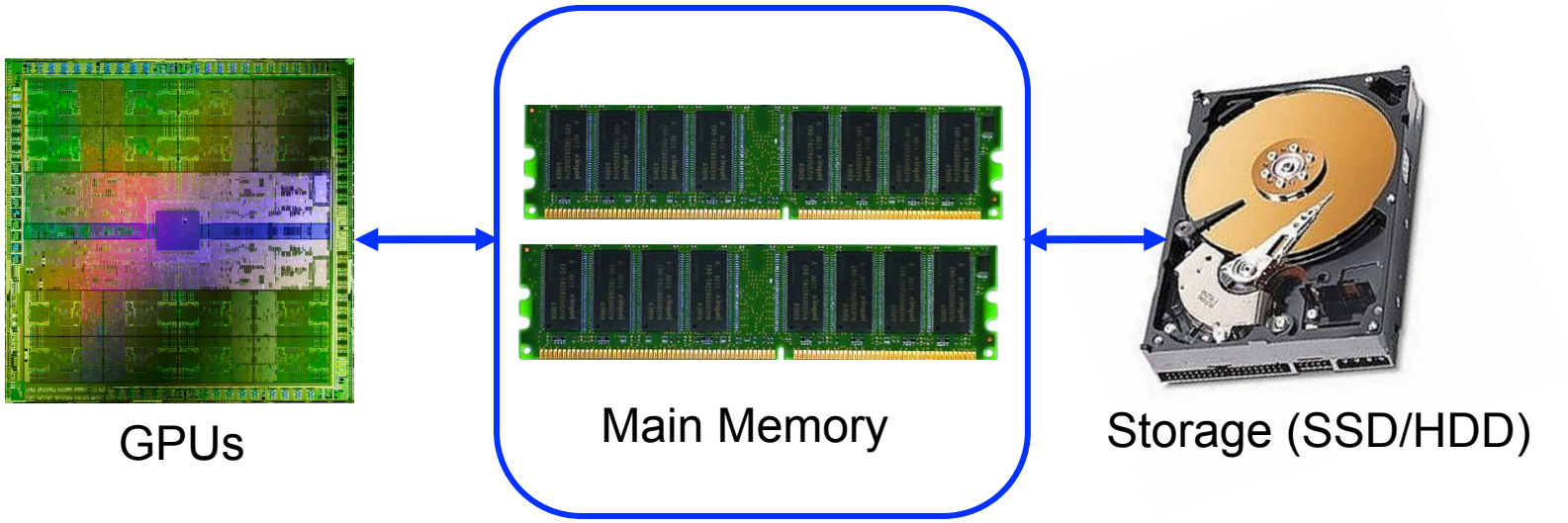

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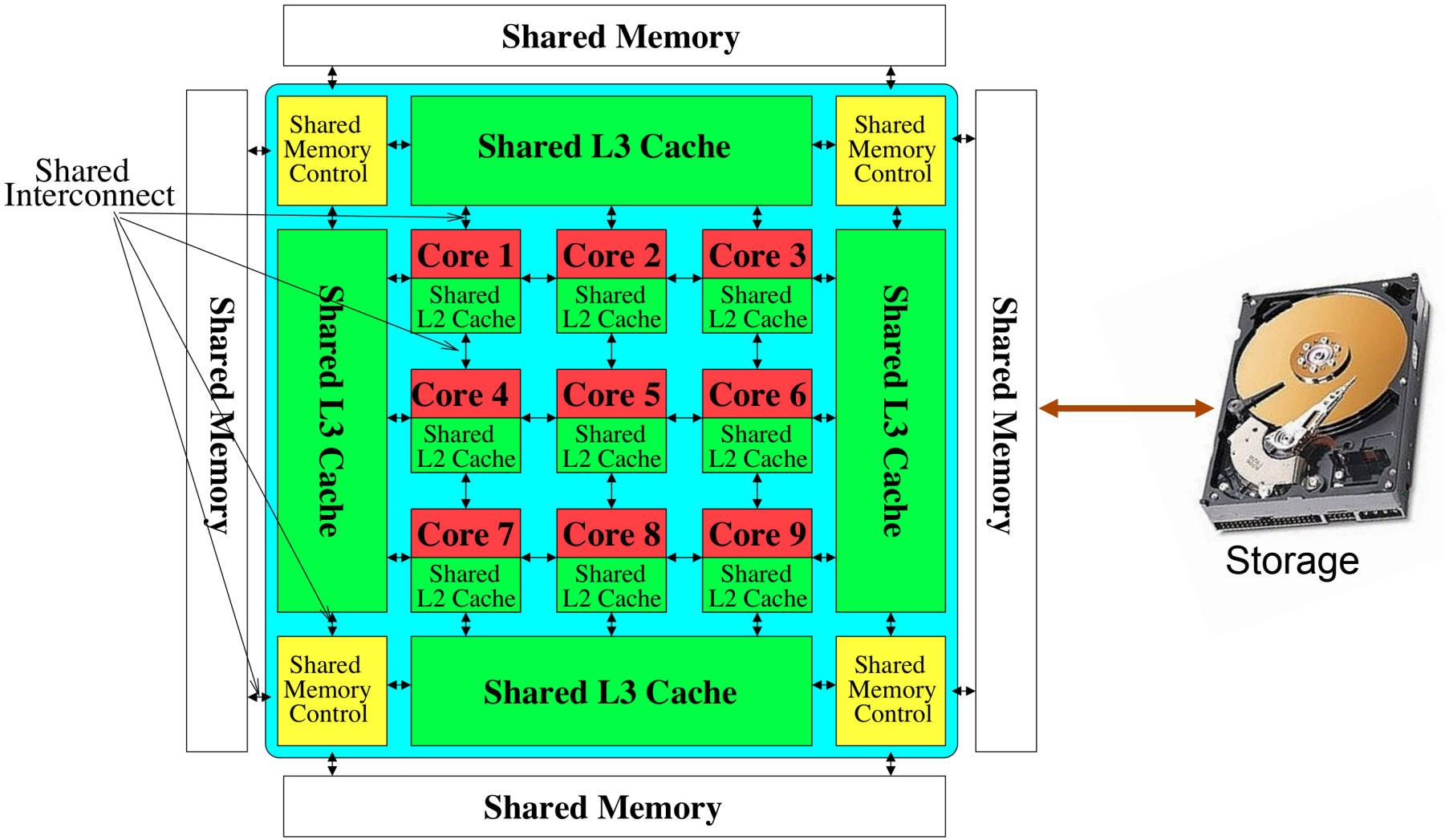
Memory System: A *Shared Resource* View



Most of the system is dedicated to storing and moving data

State of the Main Memory System

- Recent technology, architecture, and application trends
  - lead to new requirements
  - exacerbate old requirements

- DRAM and memory controllers, as we know them today, are (will be) unlikely to satisfy all requirements

- Some emerging non-volatile memory technologies (e.g., PCM) enable new opportunities: memory+storage merging

- We need to rethink the main memory system
  - to fix DRAM issues and enable emerging technologies
  - to satisfy all requirements

Major Trends Affecting Main Memory (I)

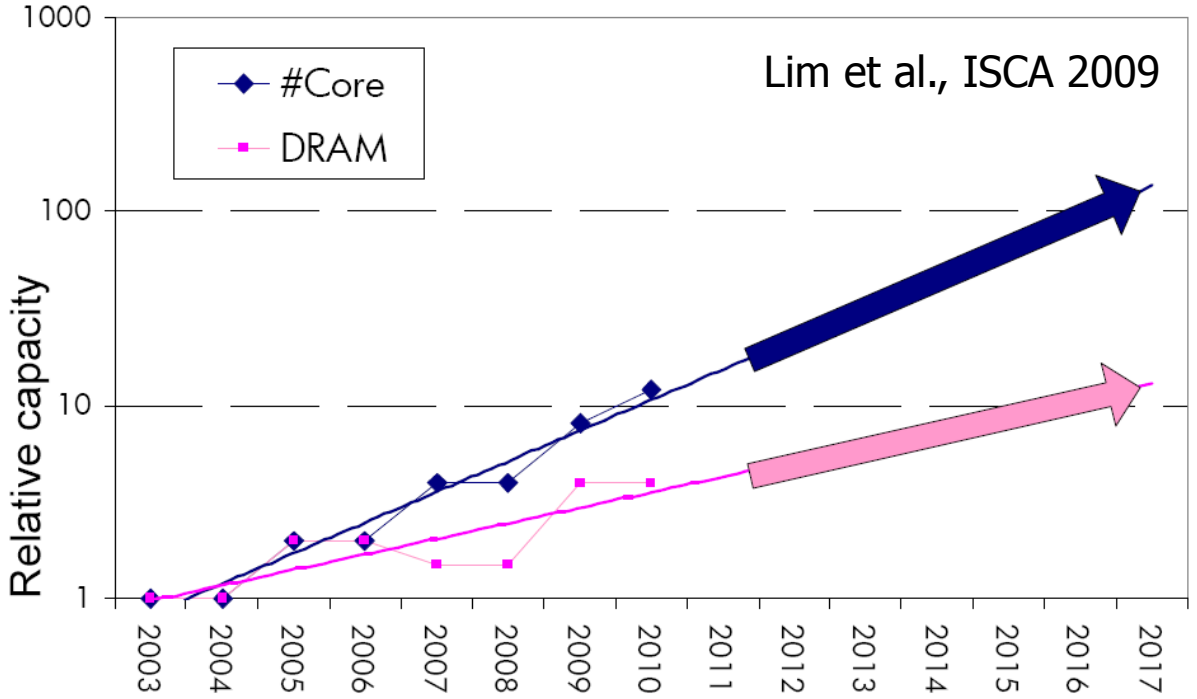
- Need for main memory capacity, bandwidth, QoS increasing
- Main memory energy/power is a key system design concern
- DRAM technology scaling is ending

Major Trends Affecting Main Memory (II)

- Need for main memory capacity, bandwidth, QoS increasing
  - Multi-core: increasing number of cores/agents
  - Data-intensive applications: increasing demand/hunger for data
  - Consolidation: cloud computing, GPUs, mobile, heterogeneity
- Main memory energy/power is a key system design concern
- DRAM technology scaling is ending

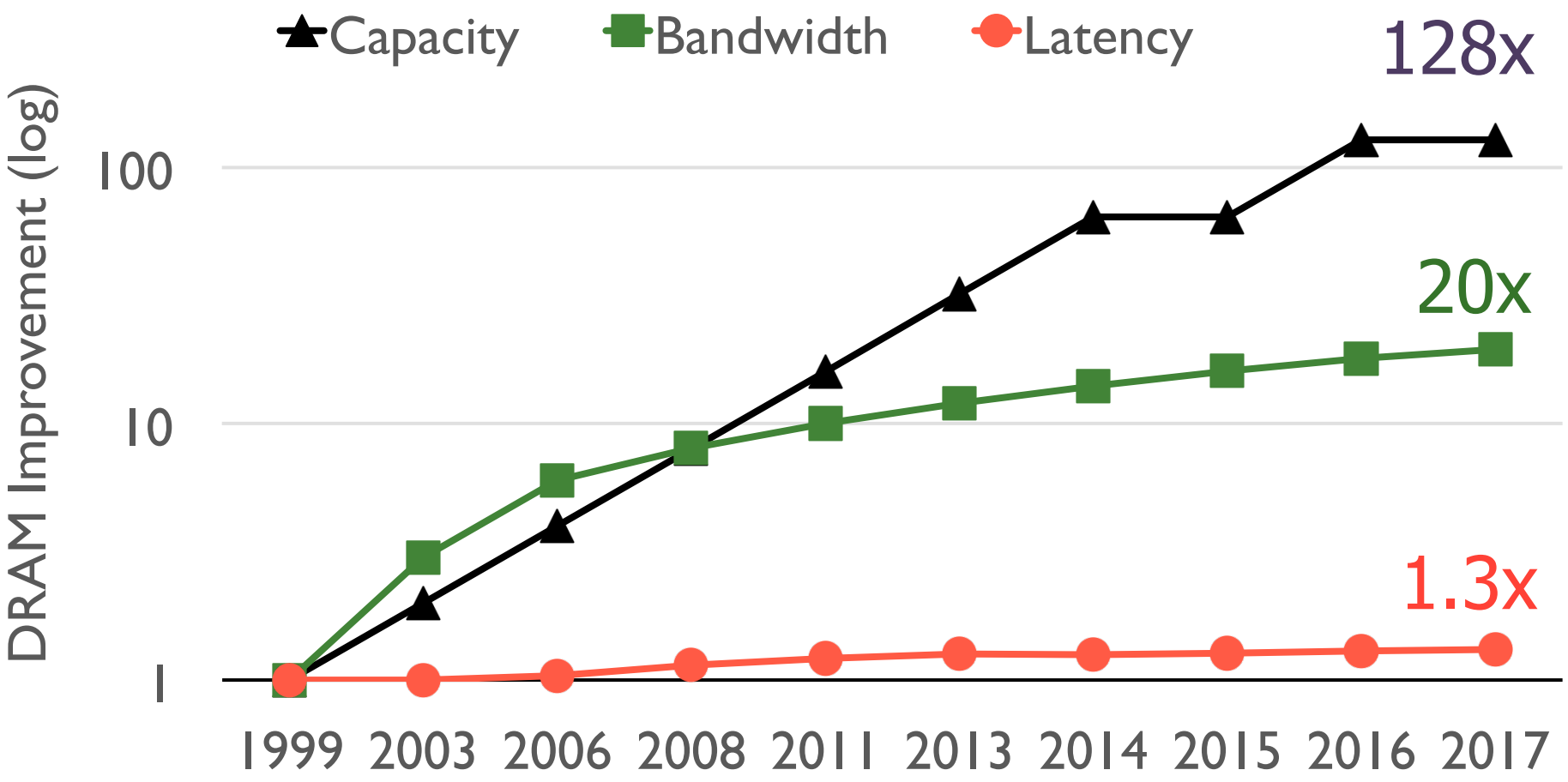
Example: The Memory Capacity Gap

Core count doubling ~ every 2 years
DRAM DIMM capacity doubling ~ every 3 years



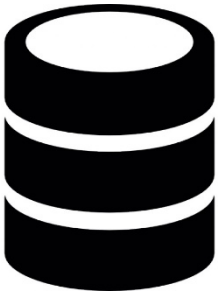
- *Memory capacity per core* expected to drop by 30% every two years
- Trends worse for *memory bandwidth per core*!

Example: Memory Bandwidth & Latency

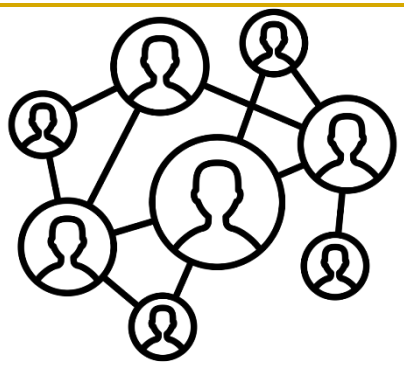


Memory latency remains almost constant

DRAM Latency Is Critical for Performance

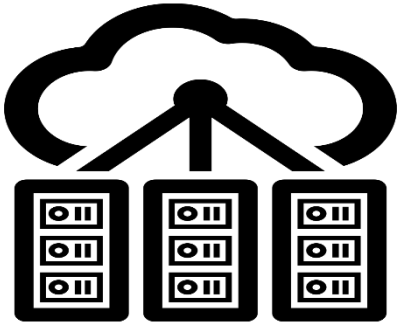


In-memory Databases
[Mao+, EuroSys'12;
Clapp+ (**Intel**), IISWC'15]



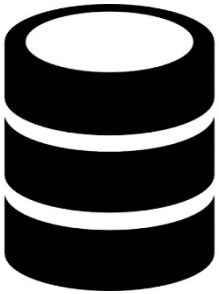
Graph/Tree Processing
[Xu+, IISWC'12; Umuroglu+, FPL'15]

In-Memory Data Analytics
[Clapp+ (**Intel**), IISWC'15;
Awan+, BDCloud'15]

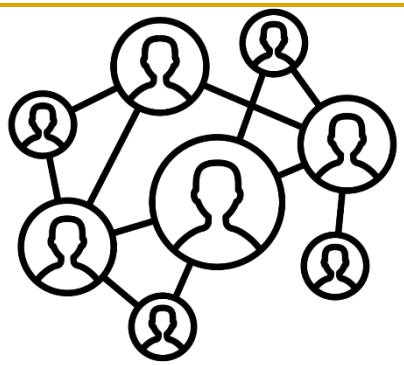


Datacenter Workloads
[Kanev+ (**Google**), ISCA'15]

DRAM Latency Is Critical for Performance



In-memory Databases

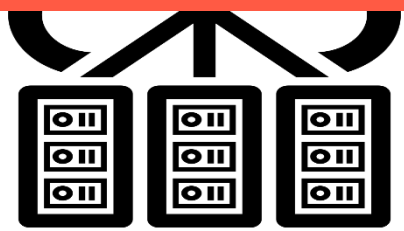


Graph/Tree Processing

Long memory latency → performance bottleneck

In-Memory Data Analytics

[Clapp+ (**Intel**), IISWC'15; Awan+, BDCloud'15]



Datacenter Workloads

[Kanev+ (**Google**), ISCA'15]

Major Trends Affecting Main Memory (III)

- Need for main memory capacity, bandwidth, QoS increasing

- Main memory energy/power is a key system design concern
  - ~40-50% energy spent in off-chip memory hierarchy [Lefurgy, IEEE Computer'03] >40% power in DRAM [Ware, HPCA'10][Paul,ISCA'15]
  - DRAM consumes power even when not used (periodic refresh)

- DRAM technology scaling is ending

Major Trends Affecting Main Memory (IV)

- Need for main memory capacity, bandwidth, QoS increasing

- Main memory energy/power is a key system design concern

- DRAM technology scaling is ending
  - ITRS projects DRAM will not scale easily below X nm
  - Scaling has provided many benefits:
    - higher capacity (density), lower cost, lower energy

Major Trends Affecting Main Memory (V)

- DRAM scaling has already become increasingly difficult
  - Increasing cell leakage current, reduced cell reliability, increasing manufacturing difficulties [Kim+ ISCA 2014], [Liu+ ISCA 2013], [Mutlu IMW 2013], [Mutlu DATE 2017]
  - **Difficult to significantly improve capacity, energy**
- **Emerging memory technologies** are promising

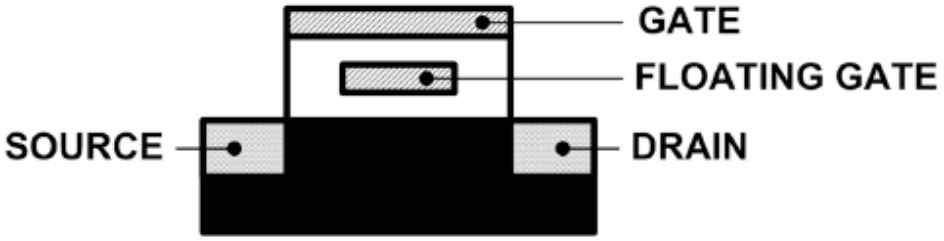
Major Trends Affecting Main Memory (V)

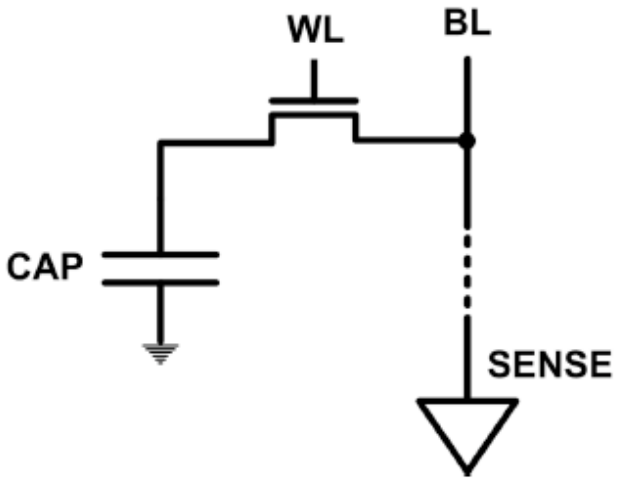
- DRAM scaling has already become increasingly difficult
  - Increasing cell leakage current, reduced cell reliability, increasing manufacturing difficulties [Kim+ ISCA 2014], [Liu+ ISCA 2013], [Mutlu IMW 2013], [Mutlu DATE 2017]
  - **Difficult to significantly improve capacity, energy**
- **Emerging memory technologies** are promising

3D-Stacked DRAM	higher bandwidth	smaller capacity
Reduced-Latency DRAM (e.g., RL/TL-DRAM, FLY-RAM)	lower latency	higher cost
Low-Power DRAM (e.g., LPDDR3, LPDDR4, Voltron)	lower power	higher latency higher cost
Non-Volatile Memory (NVM) (e.g., PCM, STTRAM, ReRAM, 3D Xpoint)	larger capacity	higher latency higher dynamic power lower endurance

Limits of Charge Memory

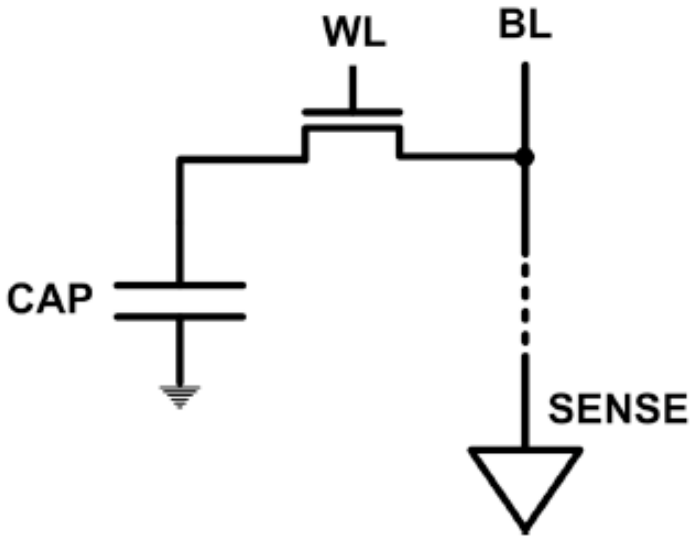
- Difficult charge placement and control
  - Flash: floating gate charge
  - DRAM: capacitor charge, transistor leakage
- Reliable sensing becomes difficult as charge storage unit size reduces





The DRAM Scaling Problem

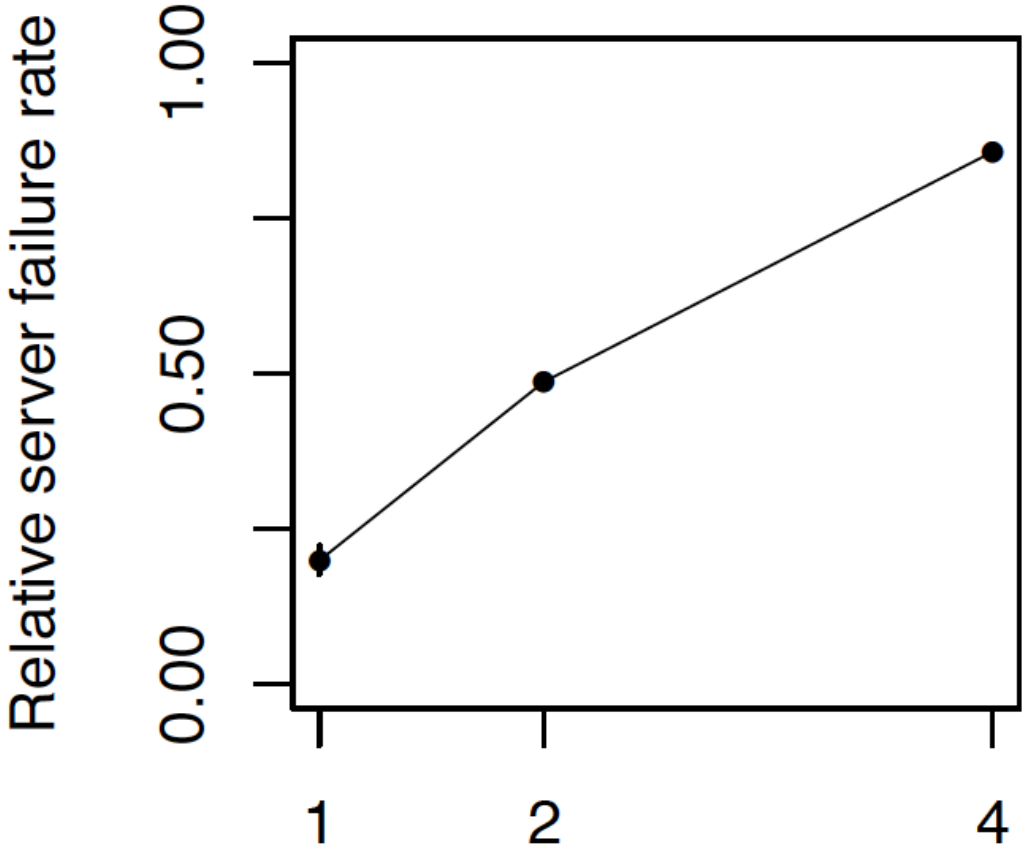
- DRAM stores charge in a capacitor (charge-based memory)
  - Capacitor must be large enough for reliable sensing
  - Access transistor should be large enough for low leakage and high retention time
  - Scaling beyond 40-35nm (2013) is challenging [ITRS, 2009]



- DRAM capacity, cost, and energy/power hard to scale

As Memory Scales, It Becomes Unreliable

- Data from all of Facebook's servers worldwide
- Meza+, "Revisiting Memory Errors in Large-Scale Production Data Centers," DSN'15.



Intuition: quadratic increase in capacity

Large-Scale Failure Analysis of DRAM Chips

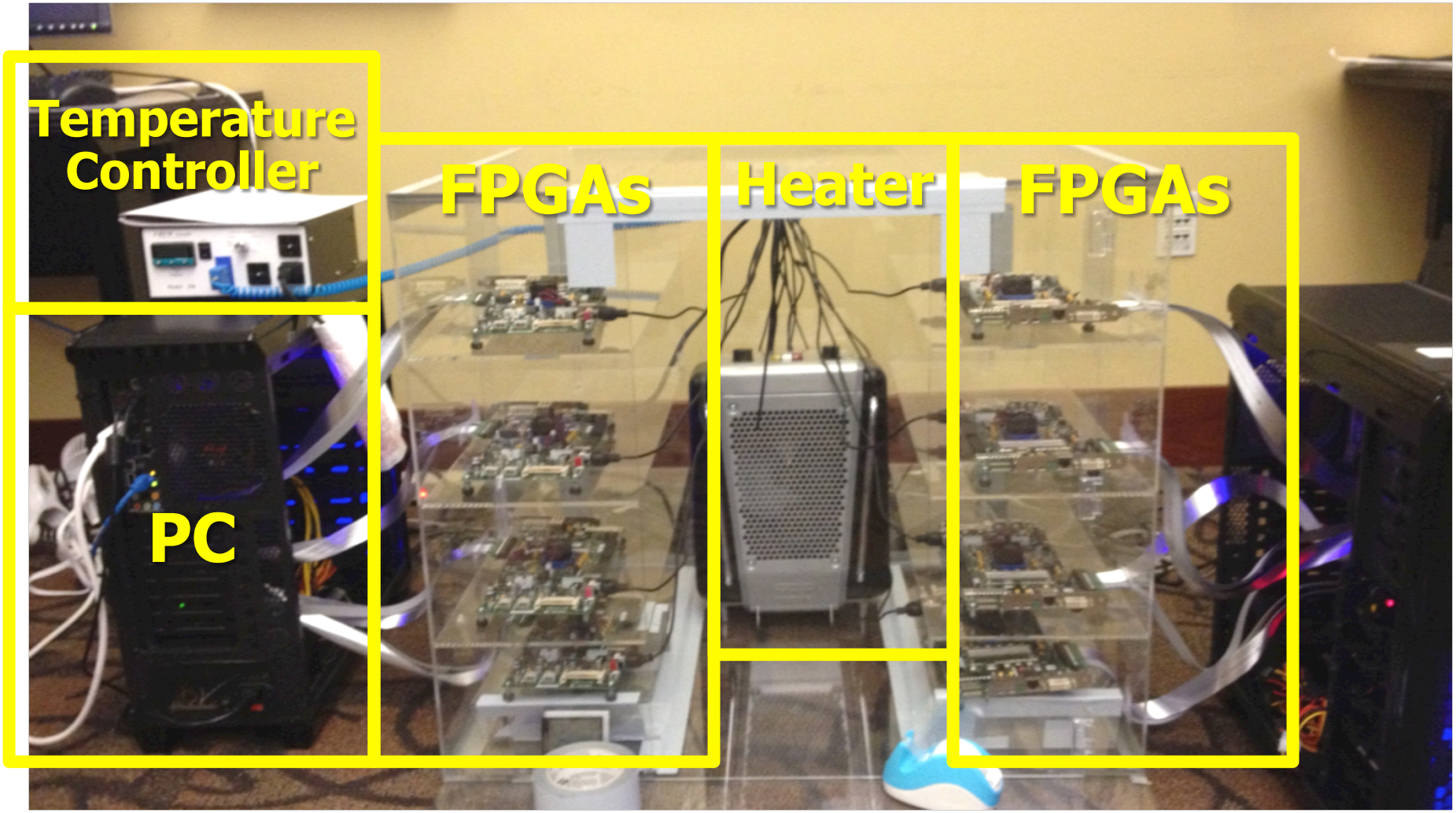
- Analysis and modeling of memory errors found in all of Facebook's server fleet

- Justin Meza, Qiang Wu, Sanjeev Kumar, and Onur Mutlu, **"Revisiting Memory Errors in Large-Scale Production Data Centers: Analysis and Modeling of New Trends from the Field"** *Proceedings of the 45th Annual IEEE/IFIP International Conference on Dependable Systems and Networks* (***DSN***), Rio de Janeiro, Brazil, June 2015. [Slides (pptx) (pdf)] [DRAM Error Model]

Revisiting Memory Errors in Large-Scale Production Data Centers: Analysis and Modeling of New Trends from the Field

Justin Meza Qiang Wu * Sanjeev Kumar * Onur Mutlu
Carnegie Mellon University * Facebook, Inc.

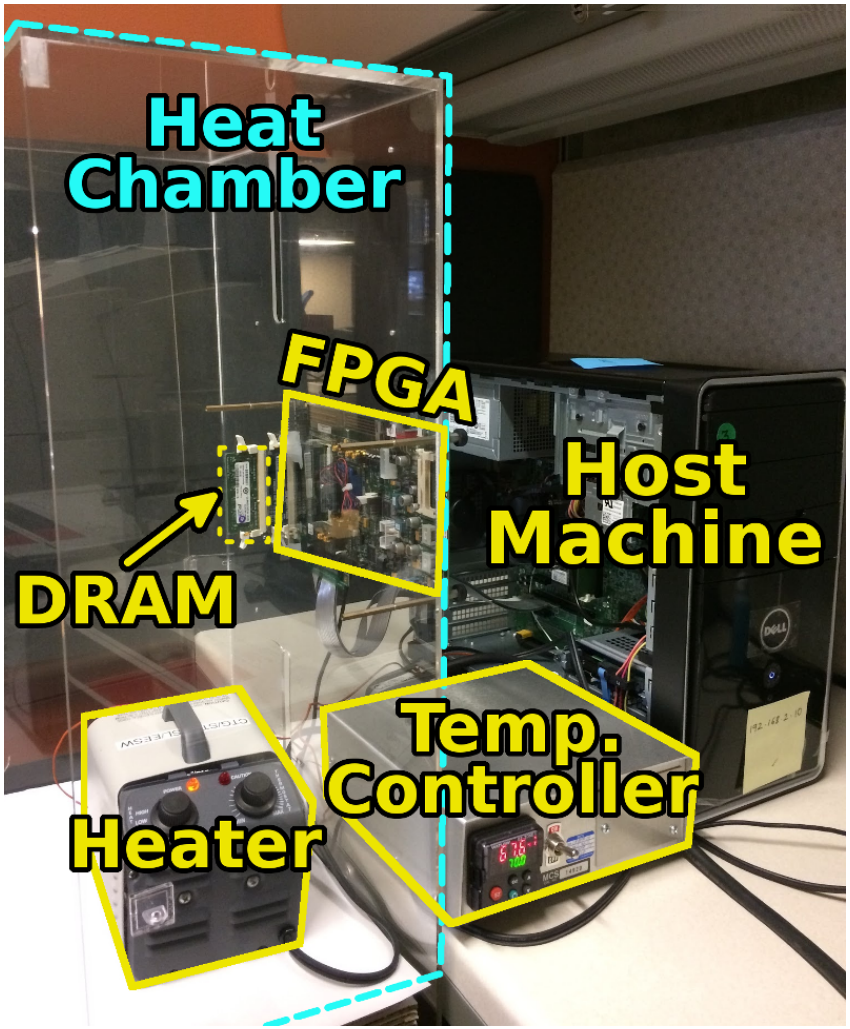
Infrastructures to Understand Such Issues



Kim+, "Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors," ISCA 2014.

SoftMC: Open Source DRAM Infrastructure

- Hasan Hassan et al., "**SoftMC: A Flexible and Practical Open-Source Infrastructure for Enabling Experimental DRAM Studies**," HPCA 2017.



- **Flexible**
- **Easy to Use (C++ API)**
- **Open-source**

github.com/CMU-SAFARI/SoftMC

SoftMC

- https://github.com/CMU-SAFARI/SoftMC

SoftMC: A Flexible and Practical Open-Source Infrastructure for Enabling Experimental DRAM Studies

Hasan Hassan[1,2,3] Nandita Vijaykumar[3] Samira Khan[4,3] Saugata Ghose[3] Kevin Chang[3]
Gennady Pekhimenko[5,3] Donghyuk Lee[6,3] Oguz Ergin[2] Onur Mutlu[1,3]

[1]*ETH Zürich* [2]*TOBB University of Economics & Technology* [3]*Carnegie Mellon University*
[4]*University of Virginia* [5]*Microsoft Research* [6]*NVIDIA Research*

A Curious Discovery [Kim et al., ISCA 2014]

One can

predictably induce errors

in most DRAM memory chips

DRAM RowHammer

A simple hardware failure mechanism
can create a widespread
system security vulnerability

WIRED

Forget Software—Now Hackers Are Exploiting Physics

BUSINESS | CULTURE | DESIGN | GEAR | SCIENCE

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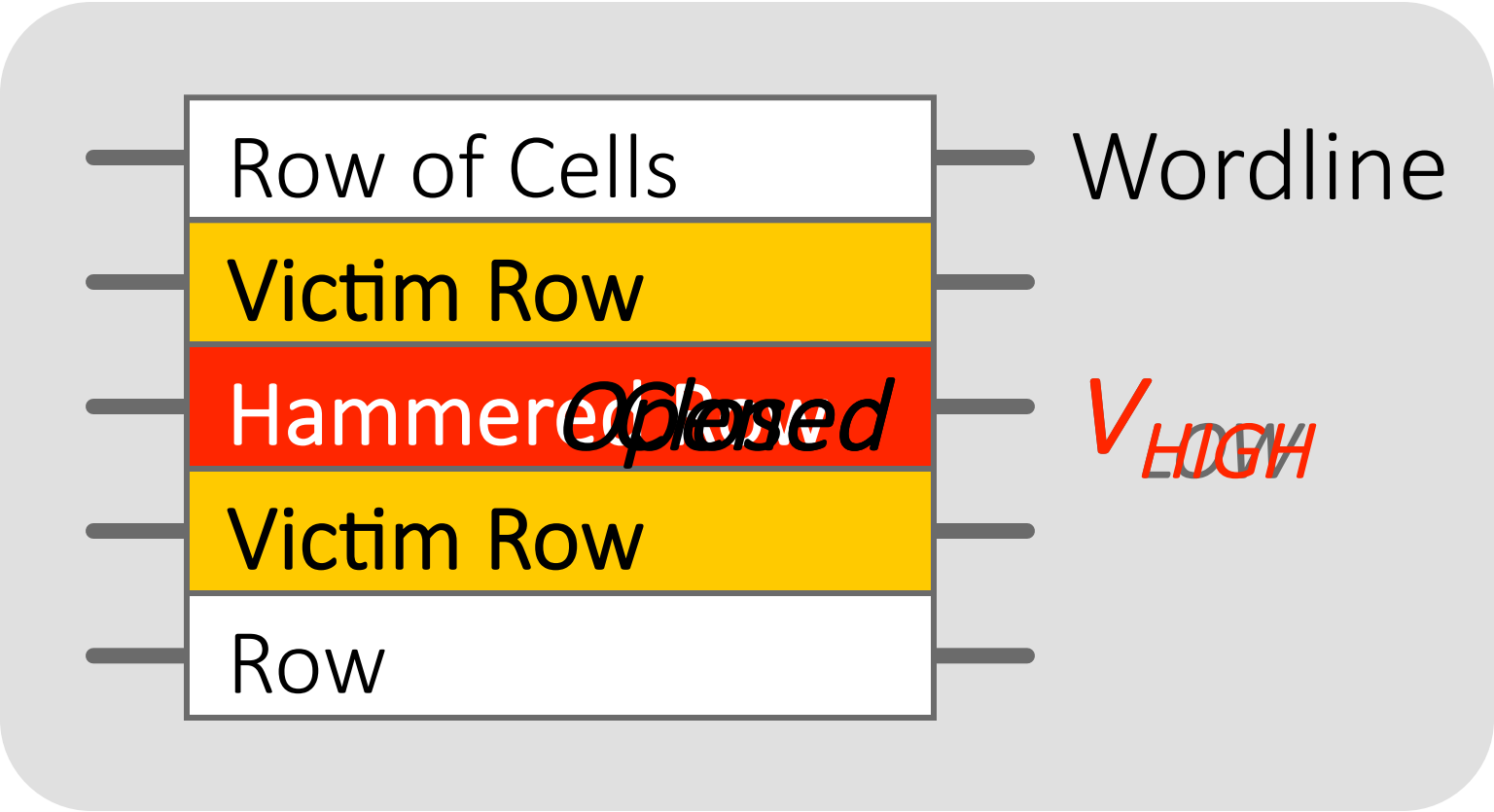
18276

TWEET

ANDY GREENBERG SECURITY 08.31.16 7:00 AM

FORGET SOFTWARE—NOW HACKERS ARE EXPLOITING PHYSICS

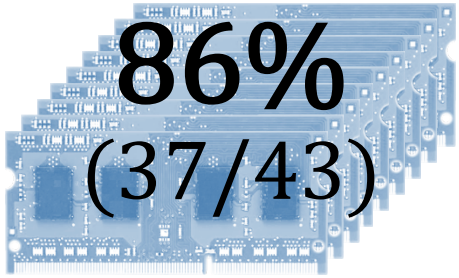
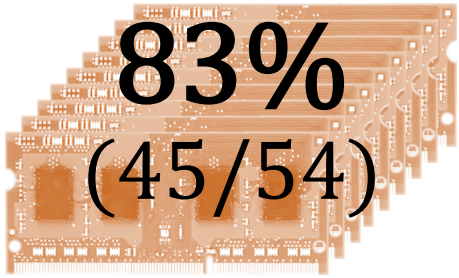
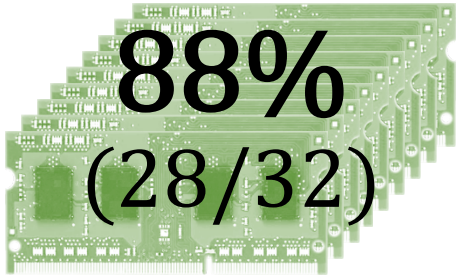
Modern DRAM is Prone to Disturbance Errors



Repeatedly reading a row enough times (before memory gets refreshed) induces disturbance errors in **adjacent rows** in most real DRAM chips you can buy today

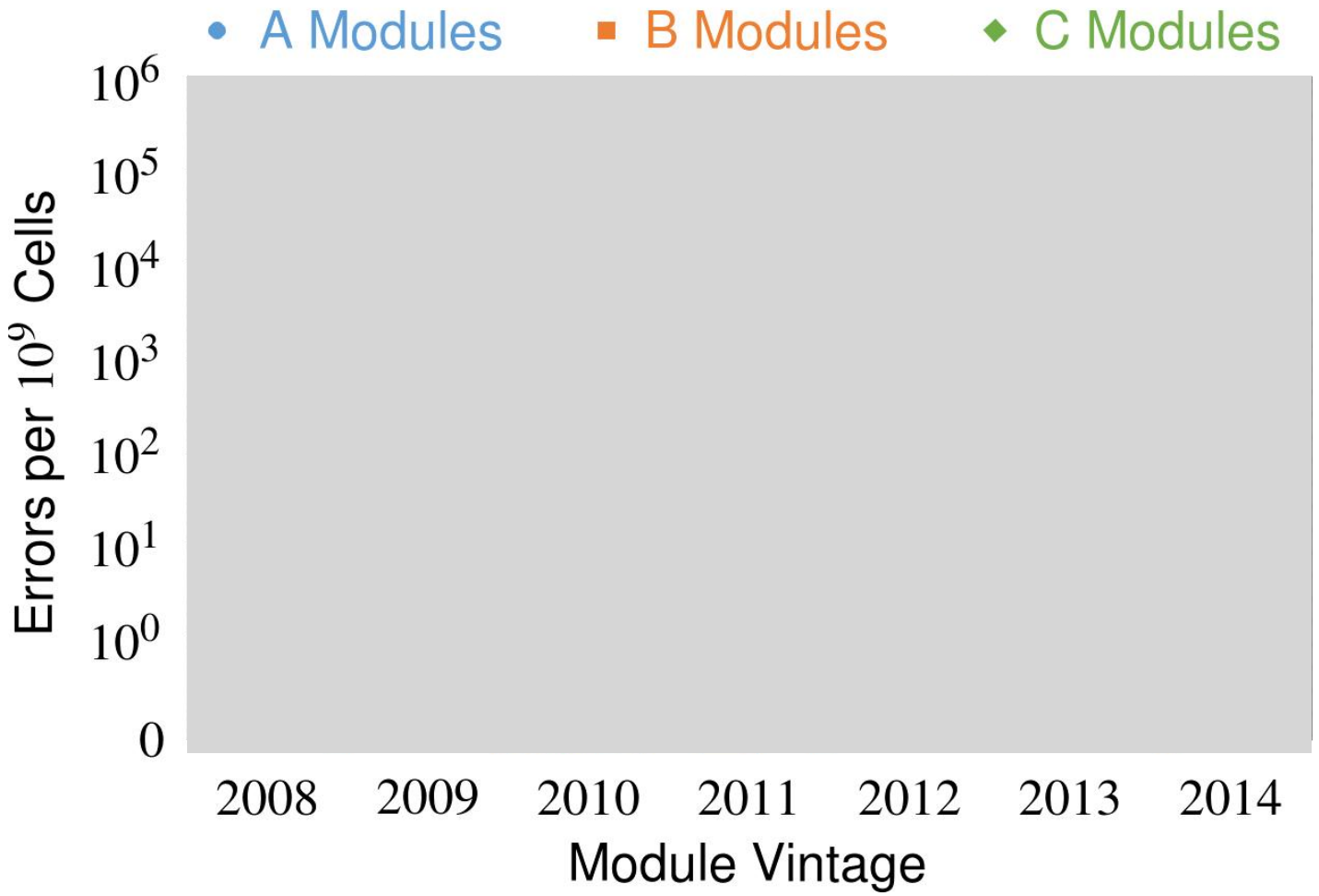
Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors, (Kim et al., ISCA 2014)

Most DRAM Modules Are Vulnerable

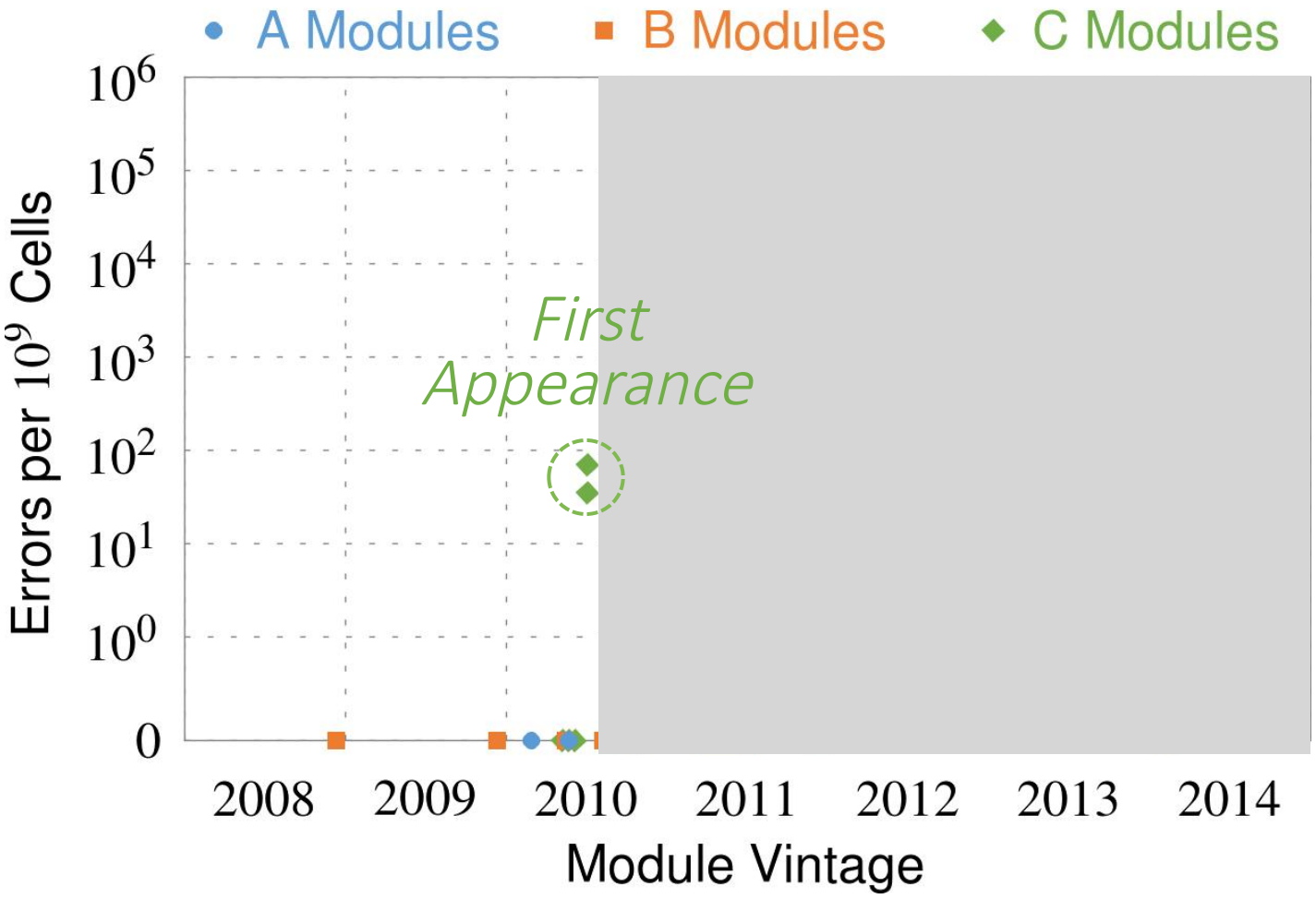
A company	B company	C company
		
86% (37/43)	83% (45/54)	88% (28/32)
Up to 1.0×10^{7} errors	Up to 2.7×10^{6} errors	Up to 3.3×10^{5} errors

Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors, (Kim et al., ISCA 2014)

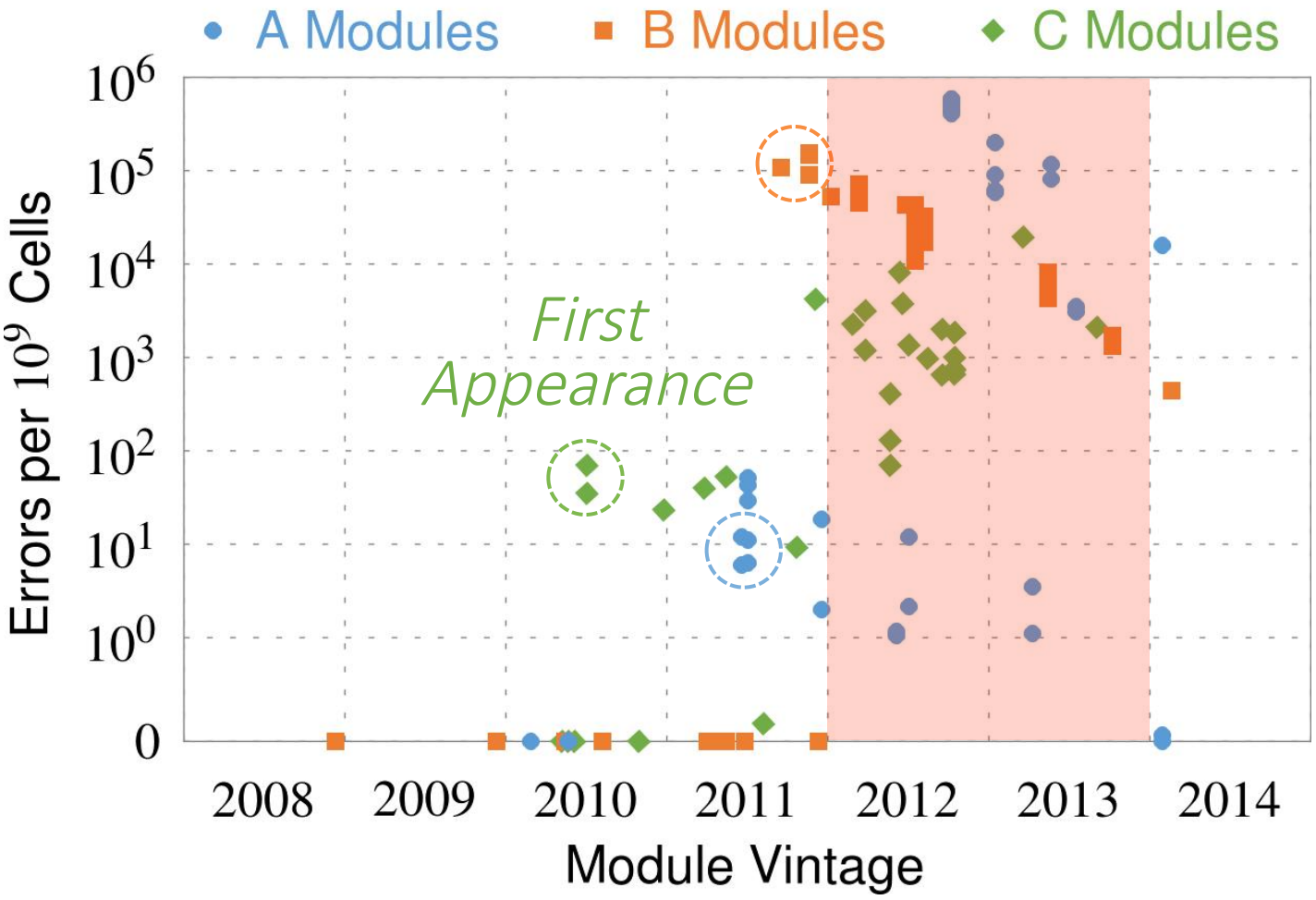
Recent DRAM Is More Vulnerable



Recent DRAM Is More Vulnerable

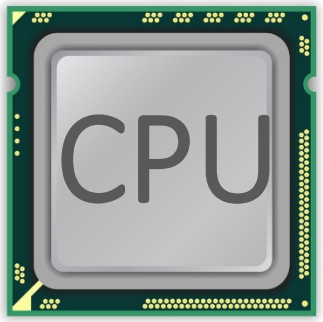


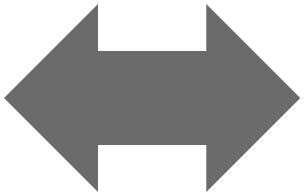
Recent DRAM Is More Vulnerable

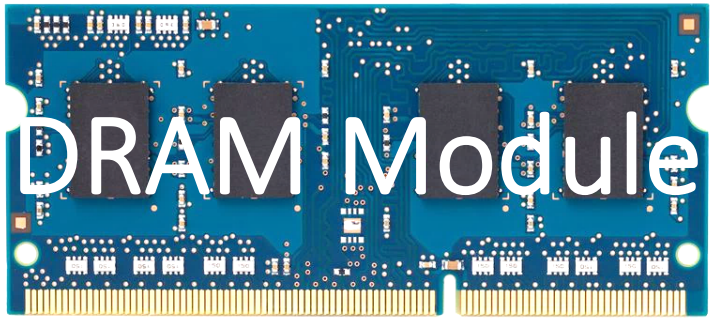


All modules from 2012–2013 are vulnerable

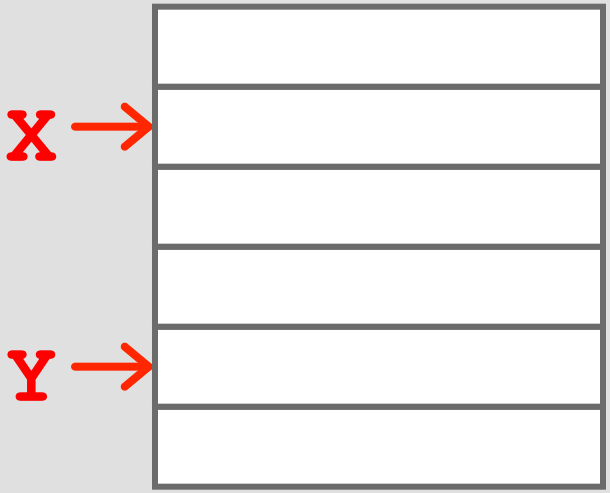
A Simple Program Can Induce Many Errors





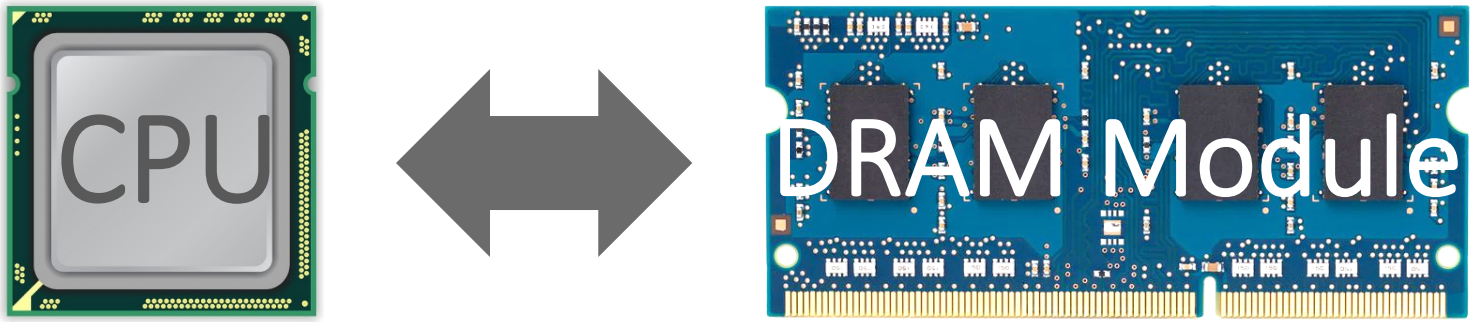



```
loop:
   mov (X), %eax
   mov (Y), %ebx
   clflush (X)
   clflush (Y)
   mfence
   jmp loop
```



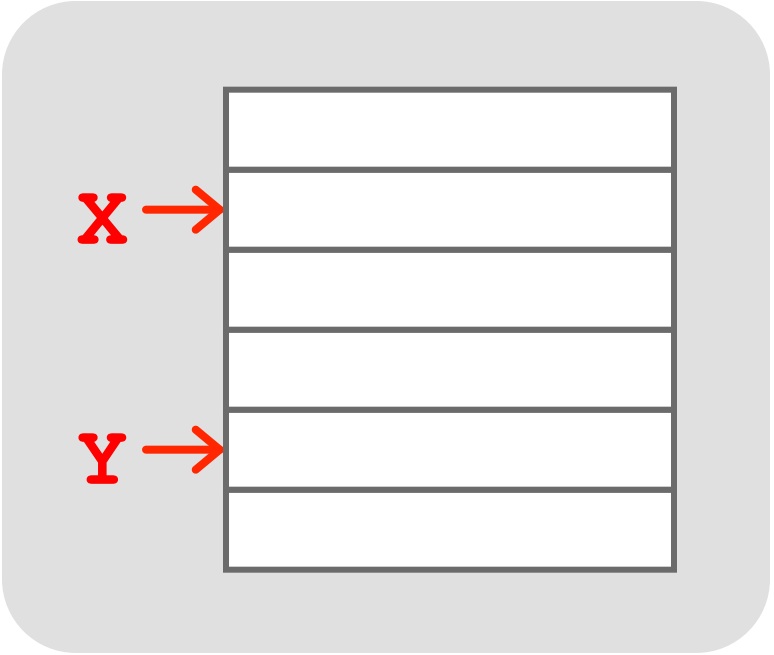
Download from: https://github.com/CMU-SAFARI/rowhammer

A Simple Program Can Induce Many Errors



1. Avoid *cache hits*
   – Flush **X** from cache

2. Avoid *row hits* to **X**
   – Read **Y** in another row



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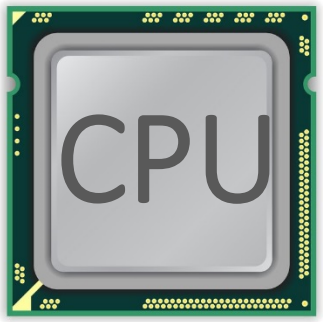

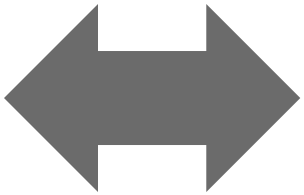

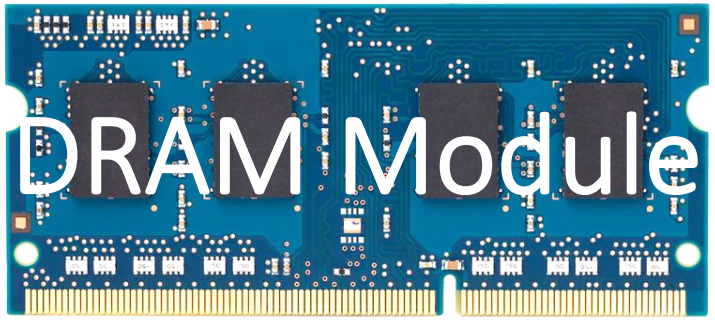


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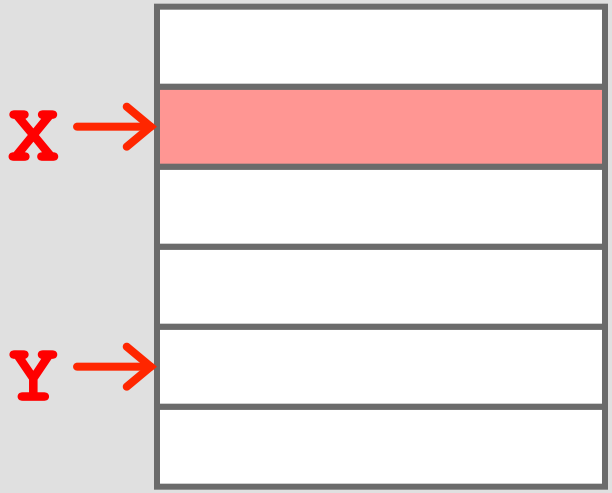

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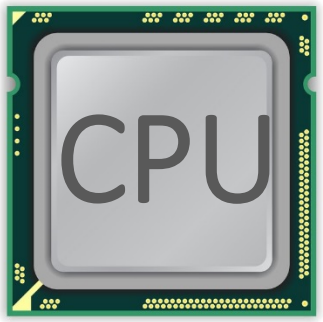

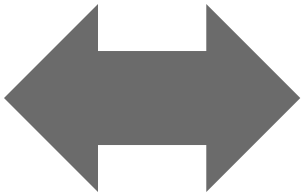

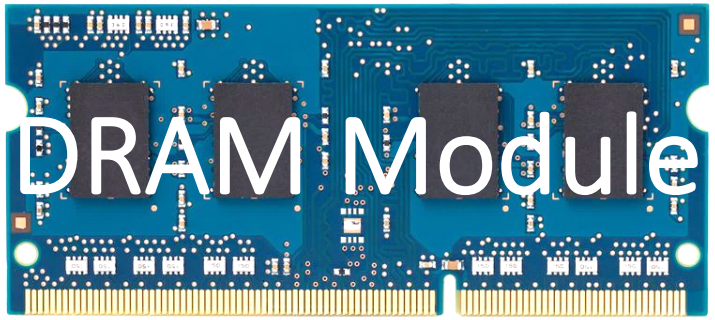


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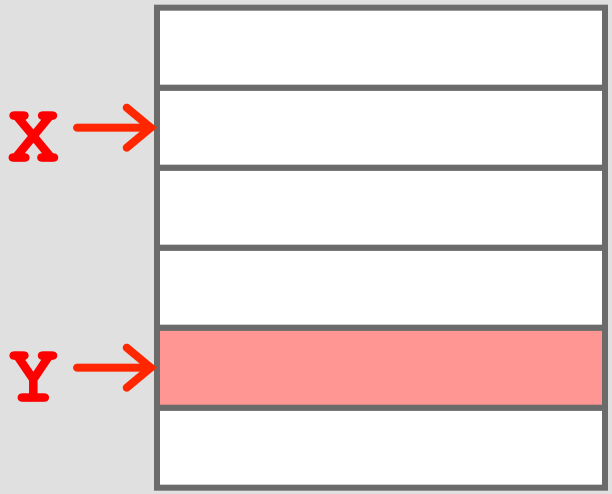

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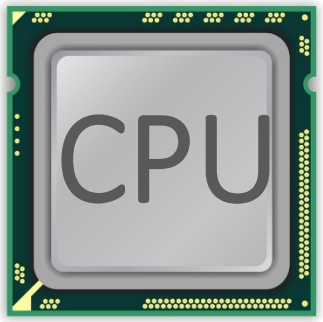

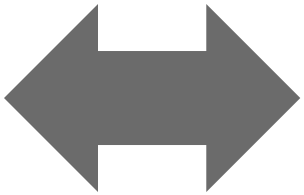

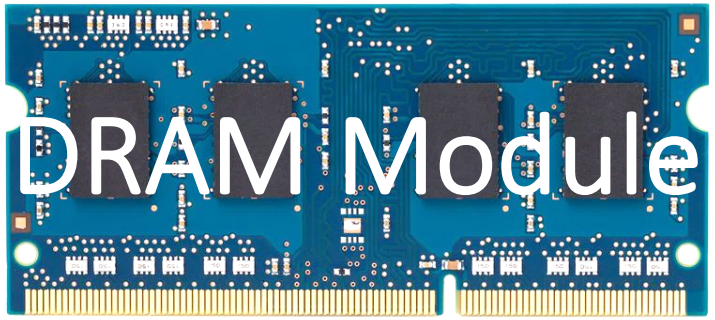


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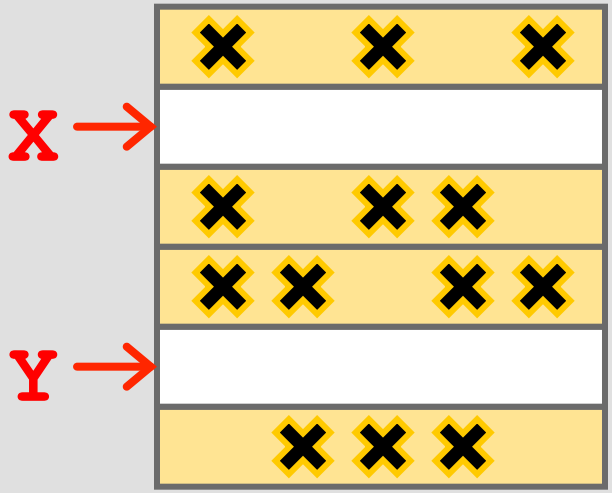


Download from: https://github.com/CMU-SAFARI/rowhammer

Observed Errors in Real Systems

CPU Architecture	Errors	Access-Rate
Intel Haswell (2013)	22.9K	12.3M/sec
Intel Ivy Bridge (2012)	20.7K	11.7M/sec
Intel Sandy Bridge (2011)	16.1K	11.6M/sec
AMD Piledriver (2012)	59	6.1M/sec

A real reliability & security issue

Kim+, "Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors," ISCA 2014.

One Can Take Over an Otherwise-Secure System

Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors

Abstract. Memory isolation is a key property of a reliable and secure computing system — an access to one memory address should not have unintended side effects on data stored in other addresses. However, as DRAM process technology

Project Zero

[Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors] (Kim et al., ISCA 2014)

News and updates from the Project Zero team at Google

[Exploiting the DRAM rowhammer bug to gain kernel privileges] (Seaborn, 2015)

Monday, March 9, 2015

Exploiting the DRAM rowhammer bug to gain kernel privileges

RowHammer Security Attack Example

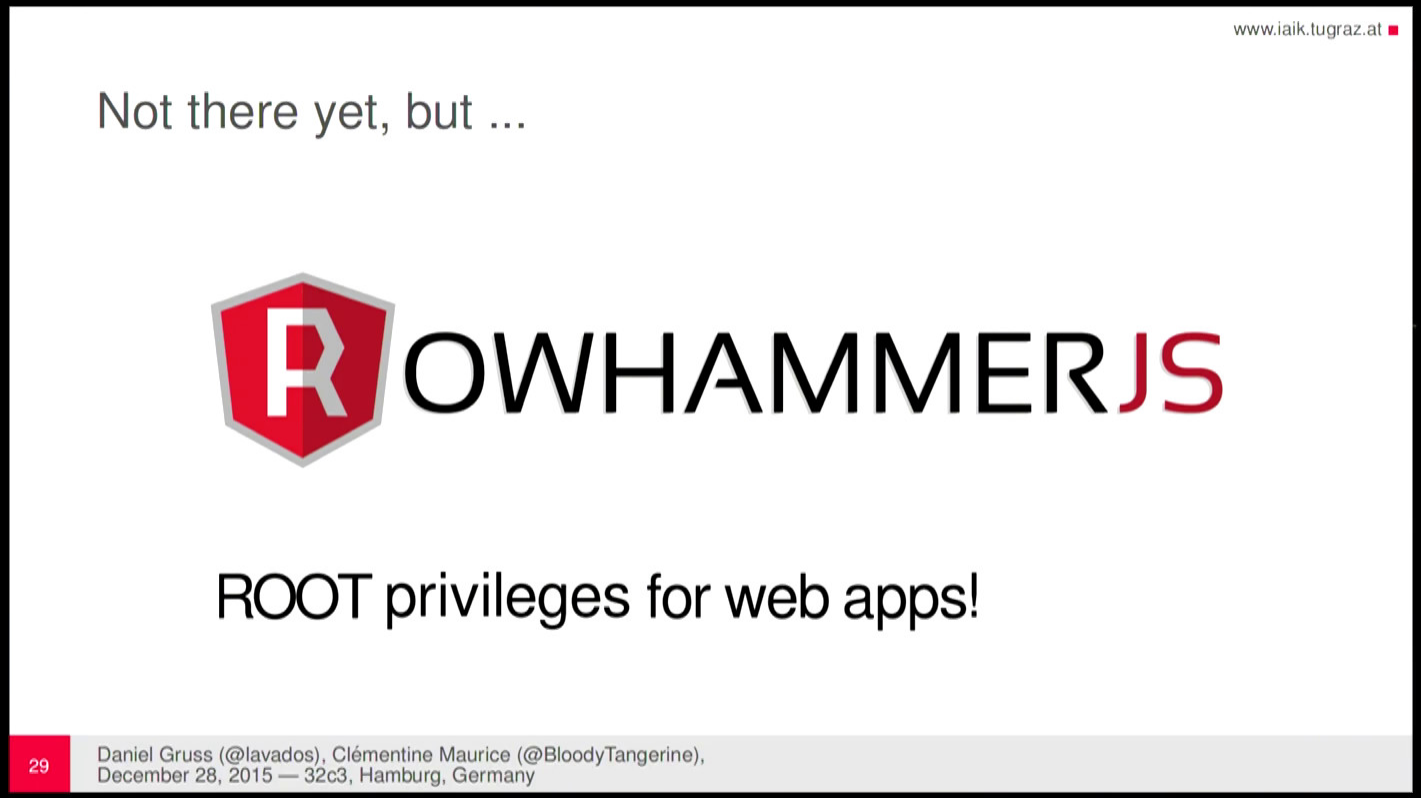
- "Rowhammer" is a problem with some recent DRAM devices in which repeatedly accessing a row of memory can cause bit flips in adjacent rows (Kim et al., ISCA 2014).
  - Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors (Kim et al., ISCA 2014)
- We tested a selection of laptops and found that a subset of them exhibited the problem.
- We built two working privilege escalation exploits that use this effect.
  - Exploiting the DRAM rowhammer bug to gain kernel privileges (Seaborn, 2015)
- One exploit uses rowhammer-induced bit flips to gain kernel privileges on x86-64 Linux when run as an unprivileged userland process.
- When run on a machine vulnerable to the rowhammer problem, the process was able to induce bit flips in page table entries (PTEs).
- It was able to use this to gain write access to its own page table, and hence gain read-write access to all of physical memory.

Security Implications

It's like breaking into an apartment by repeatedly slamming a neighbor's door until the vibrations open the door you were after

More Security Implications

"We can gain unrestricted access to systems of website visitors."



Rowhammer.js: A Remote Software-Induced Fault Attack in JavaScript (DIMVA'16)

Source: https://lab.dsst.io/32c3-slides/7197.html

More Security Implications

"Can gain control of a smart phone deterministically"

Drammer: Deterministic Rowhammer Attacks on Mobile Platforms, CCS'16

Source: https://fossbytes.com/drammer-rowhammer-attack-android-root-devices/

More Security Implications?

More on RowHammer Analysis

- Yoongu Kim, Ross Daly, Jeremie Kim, Chris Fallin, Ji Hye Lee, Donghyuk Lee, Chris Wilkerson, Konrad Lai, and Onur Mutlu,
  "Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors"
  Proceedings of the
  41st International Symposium on Computer Architecture (***ISCA***),
  Minneapolis, MN, June 2014.
  [Slides (pptx) (pdf)] [Lightning Session Slides (pptx) (pdf)] [Source Code and Data]

Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors

Yoongu Kim[1] Ross Daly* Jeremie Kim[1] Chris Fallin* Ji Hye Lee[1]
Donghyuk Lee[1] Chris Wilkerson[2] Konrad Lai Onur Mutlu[1]
[1]Carnegie Mellon University [2]Intel Labs

RowHammer Characterization Results

1. Most Modules Are at Risk
2. Errors vs. Vintage
3. Error = Charge Loss
4. Adjacency: Aggressor & Victim
5. Sensitivity Studies
6. Other Results in Paper
7. Solution Space

Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors, (Kim et al., ISCA 2014)

Apple's Patch for RowHammer

- https://support.apple.com/en-gb/HT204934

Available for: OS X Mountain Lion v10.8.5, OS X Mavericks v10.9.5

Impact: A malicious application may induce memory corruption to escalate privileges

Description: A disturbance error, also known as Rowhammer, exists with some DDR3 RAM that could have led to memory corruption. This issue was mitigated by increasing memory refresh rates.

CVE-ID

CVE-2015-3693 : Mark Seaborn and Thomas Dullien of Google, working from original research by Yoongu Kim et al (2014)

HP, Lenovo, and other vendors released similar patches

Our Solution

- PARA: *Probabilistic Adjacent Row Activation*
- Key Idea
  - After closing a row, we activate (i.e., refresh) one of its neighbors with a low probability: $p = 0.005$
- Reliability Guarantee
  - When $p=0.005$, errors in one year: 9.4×10^{-14}
  - By adjusting the value of p, we can vary the strength of protection against errors

Kim+, "Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors," ISCA 2014.

Advantages of PARA

- *PARA refreshes rows infrequently*
  - Low power
  - Low performance-overhead
    - Average slowdown: 0.20% (for 29 benchmarks)
    - Maximum slowdown: 0.75%
- *PARA is stateless*
  - Low cost
  - Low complexity

- *PARA is an effective and low-overhead solution to prevent disturbance errors*

Kim+, "Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors," ISCA 2014.

Requirements for PARA

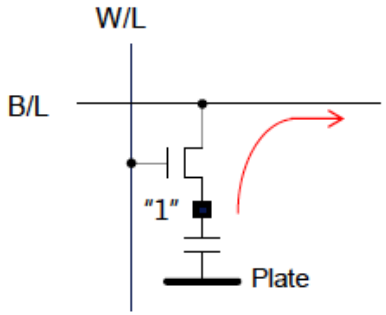
- If implemented in DRAM chip
  - Enough slack in timing/refresh parameters
  - Plenty of slack today:
    - Lee et al., "Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common Case," HPCA 2015.
    - Chang et al., "Understanding Latency Variation in Modern DRAM Chips," SIGMETRICS 2016.

- If implemented in memory controller
  - Better coordination between memory controller and DRAM
  - Memory controller should know which rows are physically adjacent

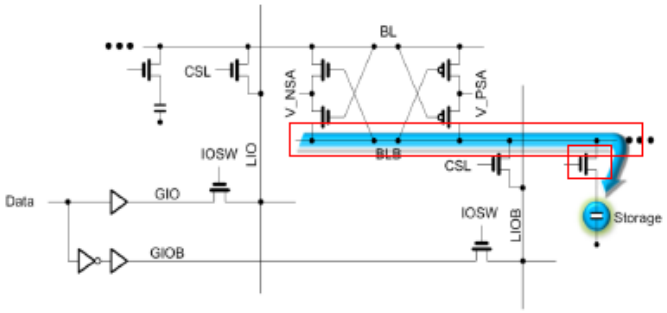
Industry Is Writing Papers About It, Too

DRAM Process Scaling Challenges

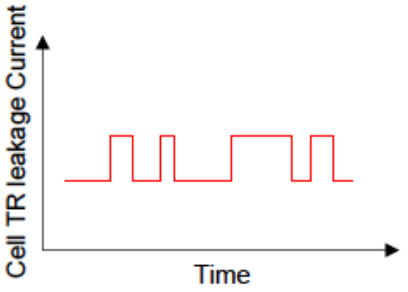
- **Refresh**
  - Difficult to build high-aspect ratio cell capacitors decreasing cell capacitance
  - Leakage current of cell access transistors increasing
- **tWR**
  - Contact resistance between the cell capacitor and access transistor increasing
  - On-current of the cell access transistor decreasing
  - Bit-line resistance increasing
- **VRT**
  - Occurring more frequently with cell capacitance decreasing



Refresh



tWR



VRT

Industry Is Writing Papers About It, Too

DRAM Process Scaling Challenges

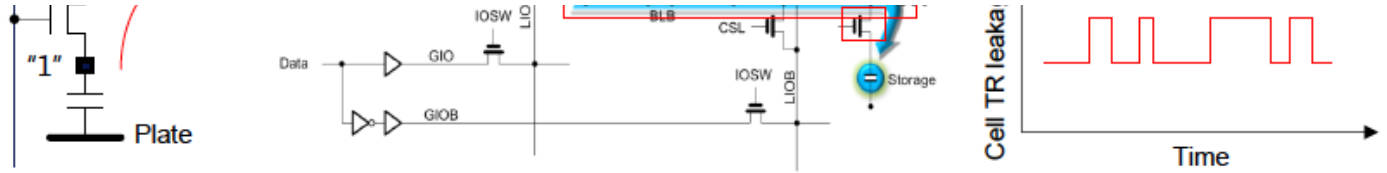
- **Refresh**
  - Difficult to build high-aspect ratio cell capacitors decreasing cell capacitance

THE MEMORY FORUM 2014

Co-Architecting Controllers and DRAM to Enhance DRAM Process Scaling

Uksong Kang, Hak-soo Yu, Churoo Park, *Hongzhong Zheng,
**John Halbert, **Kuljit Bains, SeongJin Jang, and Joo Sun Choi

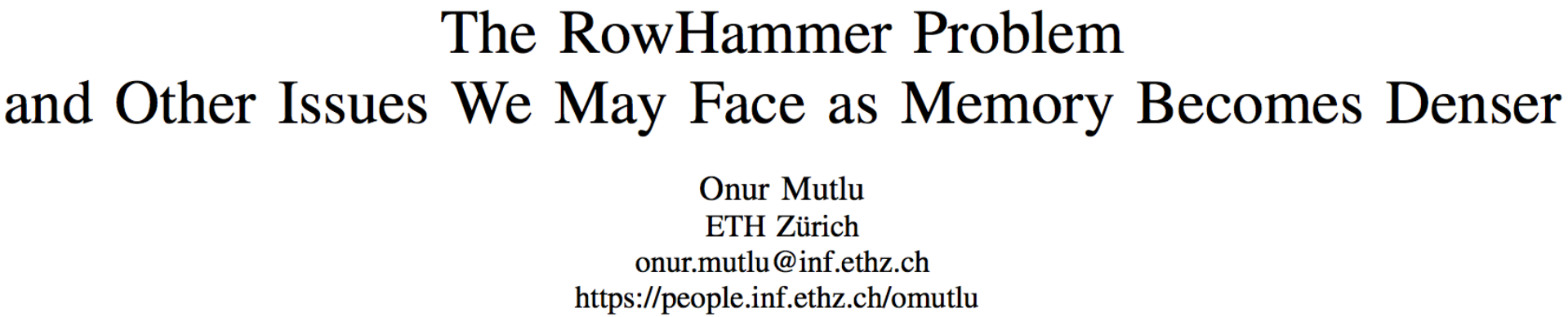
*Samsung Electronics, Hwasung, Korea / *Samsung Electronics, San Jose / **Intel*



Refresh **tWR** **VRT**

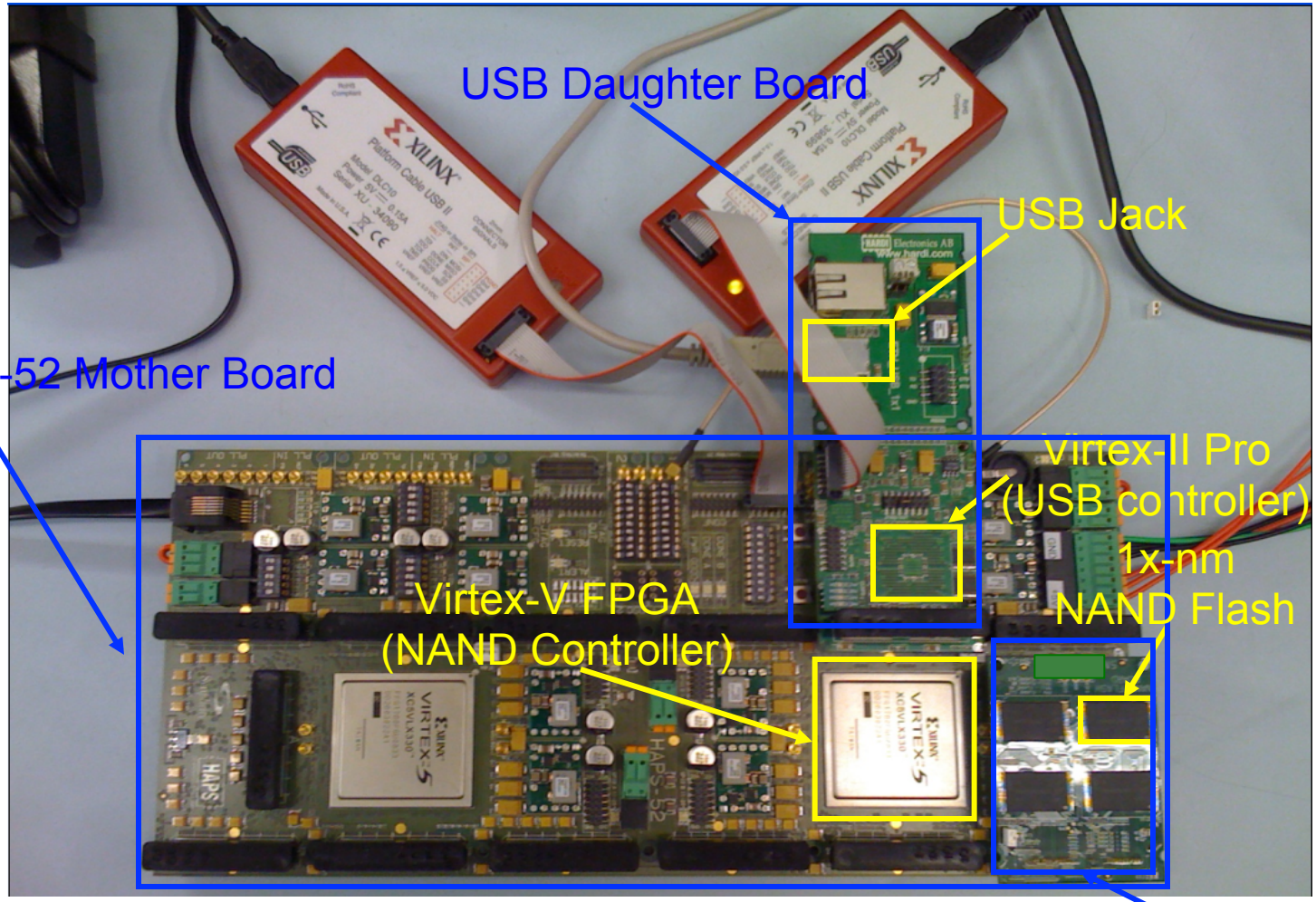
Future of Memory Reliability

- Onur Mutlu,
  "The RowHammer Problem and Other Issues We May Face as Memory Becomes Denser"
  Invited Paper in Proceedings of the
  Design, Automation, and Test in Europe Conference (***DATE***), Lausanne, Switzerland, March 2017.
  [Slides (pptx) (pdf)]


The RowHammer Problem
and Other Issues We May Face as Memory Becomes Denser

Onur Mutlu
ETH Zürich
onur.mutlu@inf.ethz.ch
https://people.inf.ethz.ch/omutlu

Aside: NAND Flash & SSD Scaling Issues



[DATE 2012, ICCD 2012, DATE 2013, ITJ 2013, ICCD 2013, SIGMETRICS 2014, HPCA 2015, DSN 2015, MSST 2015, JSAC 2016, HPCA 2017, DFRWS 2017, PIEEE'17]

Cai+, "Error Characterization, Mitigation, and Recovery in Flash Memory Based Solid State Drives," Proc. IEEE 2017.

Aside: NAND Flash & SSD Scaling Issues

- Yu Cai, Saugata Ghose, Erich F. Haratsch, Yixin Luo, and Onur Mutlu,
  "Error Characterization, Mitigation, and Recovery in Flash Memory Based Solid State Drives"
  to appear in Proceedings of the IEEE, 2017.

Cai+, "Error Patterns in MLC NAND Flash Memory: Measurement, Characterization, and Analysis," DATE 2012.

Cai+, "Flash Correct-and-Refresh: Retention-Aware Error Management for Increased Flash Memory Lifetime," ICCD 2012.

Cai+, "Threshold Voltage Distribution in MLC NAND Flash Memory: Characterization, Analysis and Modeling," DATE 2013.

Cai+, "Error Analysis and Retention-Aware Error Management for NAND Flash Memory," Intel Technology Journal 2013.

Cai+, "Program Interference in MLC NAND Flash Memory: Characterization, Modeling, and Mitigation," ICCD 2013.

Cai+, "Neighbor-Cell Assisted Error Correction for MLC NAND Flash Memories," SIGMETRICS 2014.

Cai+,"Data Retention in MLC NAND Flash Memory: Characterization, Optimization and Recovery," HPCA 2015.

Cai+, "Read Disturb Errors in MLC NAND Flash Memory: Characterization and Mitigation," DSN 2015.

Luo+, "WARM: Improving NAND Flash Memory Lifetime with Write-hotness Aware Retention Management," MSST 2015.

Meza+, "A Large-Scale Study of Flash Memory Errors in the Field," SIGMETRICS 2015.

Luo+, "Enabling Accurate and Practical Online Flash Channel Modeling for Modern MLC NAND Flash Memory," IEEE JSAC 2016.

Cai+, "Vulnerabilities in MLC NAND Flash Memory Programming: Experimental Analysis, Exploits, and Mitigation Techniques," HPCA 2017.

Fukami+, "Improving the Reliability of Chip-Off Forensic Analysis of NAND Flash Memory Devices," DFRWS EU 2017.

Aside: NAND Flash Errors and Mitigation

Proceedings of the IEEE, Sept. 2017

Error Characterization, Mitigation, and Recovery in Flash-Memory-Based Solid-State Drives

This paper reviews the most recent advances in solid-state drive (SSD) error characterization, mitigation, and data recovery techniques to improve both SSD's reliability and lifetime.

By Yu Cai, Saugata Ghose, Erich F. Haratsch, Yixin Luo, and Onur Mutlu

https://arxiv.org/pdf/1706.08642

Aside: NAND Flash Vulnerabilities

HPCA, Feb. 2017

Vulnerabilities in MLC NAND Flash Memory Programming: Experimental Analysis, Exploits, and Mitigation Techniques

Yu Cai[†] Saugata Ghose[†] Yixin Luo[‡†] Ken Mai[†] Onur Mutlu[§†] Erich F. Haratsch[‡]
[†]*Carnegie Mellon University* [‡]*Seagate Technology* [§]*ETH Zürich*

Modern NAND flash memory chips provide high density by storing two bits of data in each flash cell, called a multi-level cell *(MLC). An MLC partitions the threshold voltage range of a flash cell into four* voltage states. *When a flash cell is programmed, a high voltage is applied to the cell. Due to parasitic capacitance coupling between flash cells that are physically close to each other, flash cell programming can lead to* cell-to-cell program interference, *which introduces errors into* neighboring *flash cells. In order to reduce the impact of cell-to-cell interference on the reliability of MLC NAND flash memory, flash manufacturers adopt a* two-step programming method, *which programs the MLC in two separate steps. First, the flash memory partially programs the least significant bit of the MLC to some intermediate threshold voltage. Second, it programs the most significant bit to bring the MLC up to its full voltage state.*

In this paper, we demonstrate that two-step programming exposes new reliability and security vulnerabilities. We expe-

belongs to a different flash memory *page* (the unit of data programmed and read at the same time), which we refer to, respectively, as the least significant bit (LSB) page and the most significant bit (MSB) page [5].

A flash cell is programmed by applying a large voltage on the control gate of the transistor, which triggers charge transfer into the floating gate, thereby increasing the threshold voltage. To precisely control the threshold voltage of the cell, the flash memory uses *incremental step pulse programming* (ISPP) [12, 21, 25, 41]. ISPP applies multiple short pulses of the programming voltage to the control gate, in order to increase the cell threshold voltage by some small voltage amount (V_{step}) after each step. Initial MLC designs programmed the threshold voltage in *one shot*, issuing all of the pulses back-to-back to program *both* bits of data at the same time. However, as flash memory scales down, the distance between neighboring flash cells decreases, which

https://people.inf.ethz.ch/omutlu/pub/flash-memory-programming-vulnerabilities_hpca17.pdf

Challenge and Opportunity for Future

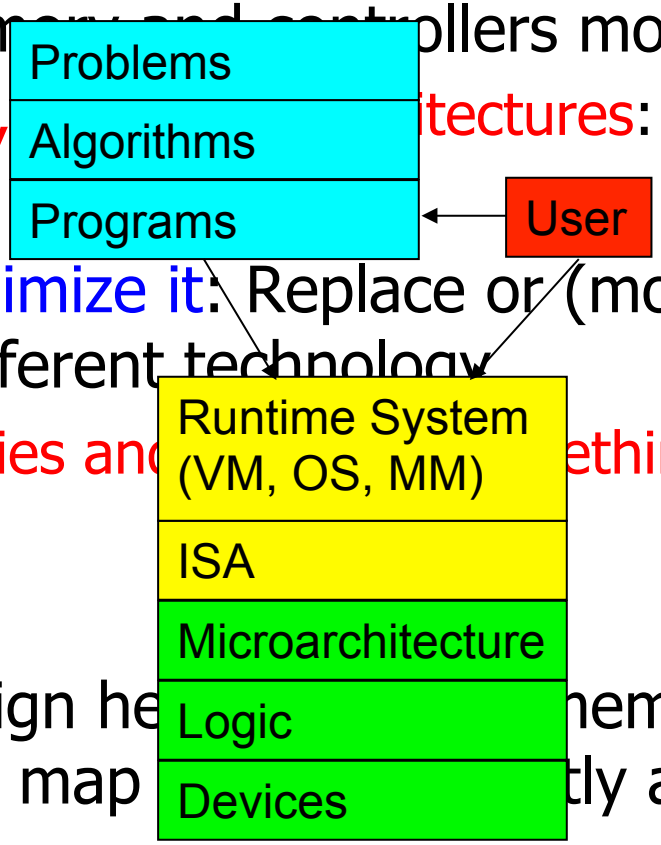
Fundamentally

Secure, Reliable, Safe

Memory Architectures

How Do We Solve The Memory Problem?

- Fix it: Make mem[illegible]llers more intelligent
  - New interfaces, [illegible]itectures: system-mem codesign
- Eliminate or minimize it: Replace or (more likely) augment DRAM with a different technology
  - New technologies an[illegible]ethinking of memory & storage
- Embrace it: Design he[illegible]nemories (none of which are perfect) and map [illegible]tly across them
  - New models for data management and maybe usage



Solutions (to memory scaling) require software/hardware/device cooperation

Solution 1: New Memory Architectures

- Overcome memory shortcomings with
  - Memory-centric system design
  - Novel memory architectures, interfaces, functions
  - Better waste management (efficient utilization)

- Key issues to tackle
  - Enable reliability at low cost → high capacity
  - Reduce energy
  - Reduce latency
  - Improve bandwidth
  - Reduce waste (capacity, bandwidth, latency)
  - Enable computation close to data

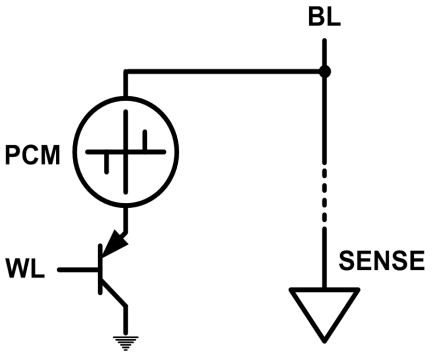
Solution 1: New Memory Architectures

- Liu+, "RAIDR: Retention-Aware Intelligent DRAM Refresh," ISCA 2012.
- Kim+, "A Case for Exploiting Subarray-Level Parallelism in DRAM," ISCA 2012.
- Lee+, "Tiered-Latency DRAM: A Low Latency and Low Cost DRAM Architecture," HPCA 2013.
- Liu+, "An Experimental Study of Data Retention Behavior in Modern DRAM Devices," ISCA 2013.
- Seshadri+, "RowClone: Fast and Efficient In-DRAM Copy and Initialization of Bulk Data," MICRO 2013.
- Pekhimenko+, "Linearly Compressed Pages: A Main Memory Compression Framework," MICRO 2013.
- Chang+, "Improving DRAM Performance by Parallelizing Refreshes with Accesses," HPCA 2014.
- Khan+, "The Efficacy of Error Mitigation Techniques for DRAM Retention Failures: A Comparative Experimental Study," SIGMETRICS 2014.
- Luo+, "Characterizing Application Memory Error Vulnerability to Optimize Data Center Cost," DSN 2014.
- Kim+, "Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors," ISCA 2014.
- Lee+, "Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common-Case," HPCA 2015.
- Qureshi+, "AVATAR: A Variable-Retention-Time (VRT) Aware Refresh for DRAM Systems," DSN 2015.
- Meza+, "Revisiting Memory Errors in Large-Scale Production Data Centers: Analysis and Modeling of New Trends from the Field," DSN 2015.
- Kim+, "Ramulator: A Fast and Extensible DRAM Simulator," IEEE CAL 2015.
- Seshadri+, "Fast Bulk Bitwise AND and OR in DRAM," IEEE CAL 2015.
- Ahn+, "A Scalable Processing-in-Memory Accelerator for Parallel Graph Processing," ISCA 2015.
- Ahn+, "PIM-Enabled Instructions: A Low-Overhead, Locality-Aware Processing-in-Memory Architecture," ISCA 2015.
- Lee+, "Decoupled Direct Memory Access: Isolating CPU and IO Traffic by Leveraging a Dual-Data-Port DRAM," PACT 2015.
- Seshadri+, "Gather-Scatter DRAM: In-DRAM Address Translation to Improve the Spatial Locality of Non-unit Strided Accesses," MICRO 2015.
- Lee+, "Simultaneous Multi-Layer Access: Improving 3D-Stacked Memory Bandwidth at Low Cost," TACO 2016.
- Hassan+, "ChargeCache: Reducing DRAM Latency by Exploiting Row Access Locality," HPCA 2016.
- Chang+, "Low-Cost Inter-Linked Subarrays (LISA): Enabling Fast Inter-Subarray Data Migration in DRAM," HPCA 2016.
- Chang+, "Understanding Latency Variation in Modern DRAM Chips Experimental Characterization, Analysis, and Optimization," SIGMETRICS 2016.
- Khan+, "PARBOR: An Efficient System-Level Technique to Detect Data Dependent Failures in DRAM," DSN 2016.
- Hsieh+, "Transparent Offloading and Mapping (TOM): Enabling Programmer-Transparent Near-Data Processing in GPU Systems," ISCA 2016.
- Hashemi+, "Accelerating Dependent Cache Misses with an Enhanced Memory Controller," ISCA 2016.
- Boroumand+, "LazyPIM: An Efficient Cache Coherence Mechanism for Processing-in-Memory," IEEE CAL 2016.
- Pattnaik+, "Scheduling Techniques for GPU Architectures with Processing-In-Memory Capabilities," PACT 2016.
- Hsieh+, "Accelerating Pointer Chasing in 3D-Stacked Memory: Challenges, Mechanisms, Evaluation," ICCD 2016.
- Hashemi+, "Continuous Runahead: Transparent Hardware Acceleration for Memory Intensive Workloads," MICRO 2016.
- Khan+, "A Case for Memory Content-Based Detection and Mitigation of Data-Dependent Failures in DRAM"," IEEE CAL 2016.
- Hassan+, "SoftMC: A Flexible and Practical Open-Source Infrastructure for Enabling Experimental DRAM Studies," HPCA 2017.
- Mutlu, "The RowHammer Problem and Other Issues We May Face as Memory Becomes Denser," DATE 2017.
- Lee+, "Design-Induced Latency Variation in Modern DRAM Chips: Characterization, Analysis, and Latency Reduction Mechanisms," SIGMETRICS 2017.
- Chang+, "Understanding Reduced-Voltage Operation in Modern DRAM Devices: Experimental Characterization, Analysis, and Mechanisms," SIGMETRICS 2017.
- Patel+, "The Reach Profiler (REAPER): Enabling the Mitigation of DRAM Retention Failures via Profiling at Aggressive Conditions," ISCA 2017.
- Seshadri and Mutlu, "Simple Operations in Memory to Reduce Data Movement," ADCOM 2017.
- Liu+, "Concurrent Data Structures for Near-Memory Computing," SPAA 2017.
- Khan+, "Detecting and Mitigating Data-Dependent DRAM Failures by Exploiting Current Memory Content," MICRO 2017.
- Seshadri+, "Ambit: In-Memory Accelerator for Bulk Bitwise Operations Using Commodity DRAM Technology," MICRO 2017.
- Avoid DRAM:
  - Seshadri+, "The Evicted-Address Filter: A Unified Mechanism to Address Both Cache Pollution and Thrashing," PACT 2012.
  - Pekhimenko+, "Base-Delta-Immediate Compression: Practical Data Compression for On-Chip Caches," PACT 2012.
  - Seshadri+, "The Dirty-Block Index," ISCA 2014.
  - Pekhimenko+, "Exploiting Compressed Block Size as an Indicator of Future Reuse," HPCA 2015.
  - Vijaykumar+, "A Case for Core-Assisted Bottleneck Acceleration in GPUs: Enabling Flexible Data Compression with Assist Warps," ISCA 2015.
  - Pekhimenko+, "Toggle-Aware Bandwidth Compression for GPUs," HPCA 2016.

Solution 2: Emerging Memory Technologies

- Some emerging **resistive** memory technologies seem more scalable than DRAM (and they are non-volatile)

- Example: Phase Change Memory
  - Data stored by changing phase of material
  - Data read by detecting material's resistance
  - Expected to scale to 9nm (2022 [ITRS 2009])
  - Prototyped at 20nm (Raoux+, IBM JRD 2008)
  - Expected to be denser than DRAM: can store multiple bits/cell

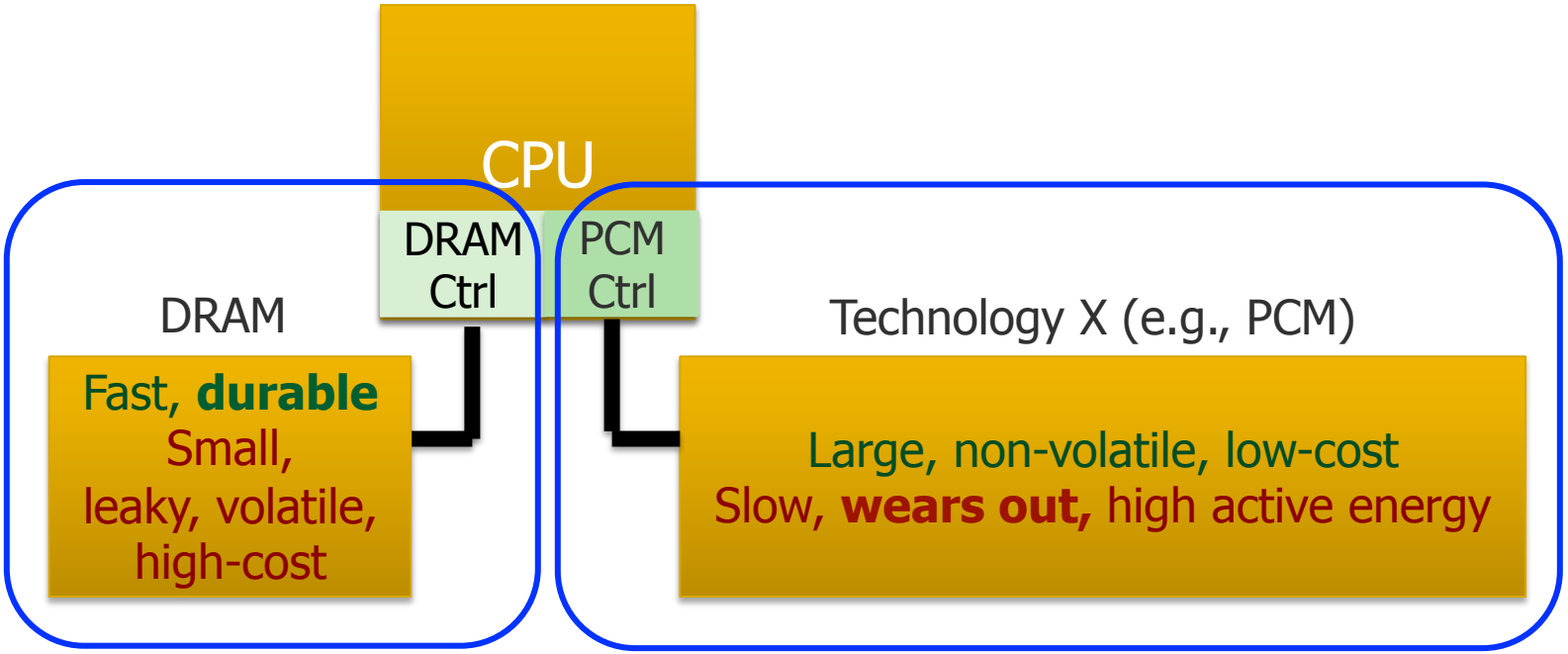


- But, emerging technologies have (many) shortcomings
  - Can they be enabled to replace/augment/surpass DRAM?

Solution 2: Emerging Memory Technologies

- Lee+, "Architecting Phase Change Memory as a Scalable DRAM Alternative," ISCA'09, CACM'10, IEEE Micro'10.
- Meza+, "Enabling Efficient and Scalable Hybrid Memories," IEEE Comp. Arch. Letters 2012.
- Yoon, Meza+, "Row Buffer Locality Aware Caching Policies for Hybrid Memories," ICCD 2012.
- Kultursay+, "Evaluating STT-RAM as an Energy-Efficient Main Memory Alternative," ISPASS 2013.
- Meza+, "A Case for Efficient Hardware-Software Cooperative Management of Storage and Memory," WEED 2013.
- Lu+, "Loose Ordering Consistency for Persistent Memory," ICCD 2014.
- Zhao+, "FIRM: Fair and High-Performance Memory Control for Persistent Memory Systems," MICRO 2014.
- Yoon, Meza+, "Efficient Data Mapping and Buffering Techniques for Multi-Level Cell Phase-Change Memories," TACO 2014.
- Ren+, "ThyNVM: Enabling Software-Transparent Crash Consistency in Persistent Memory Systems," MICRO 2015.
- Chauhan+, "NVMove: Helping Programmers Move to Byte-Based Persistence," INFLOW 2016.
- Li+, "Utility-Based Hybrid Memory Management," CLUSTER 2017.
- Yu+, "Banshee: Bandwidth-Efficient DRAM Caching via Software/Hardware Cooperation," MICRO 2017.

Combination: Hybrid Memory Systems

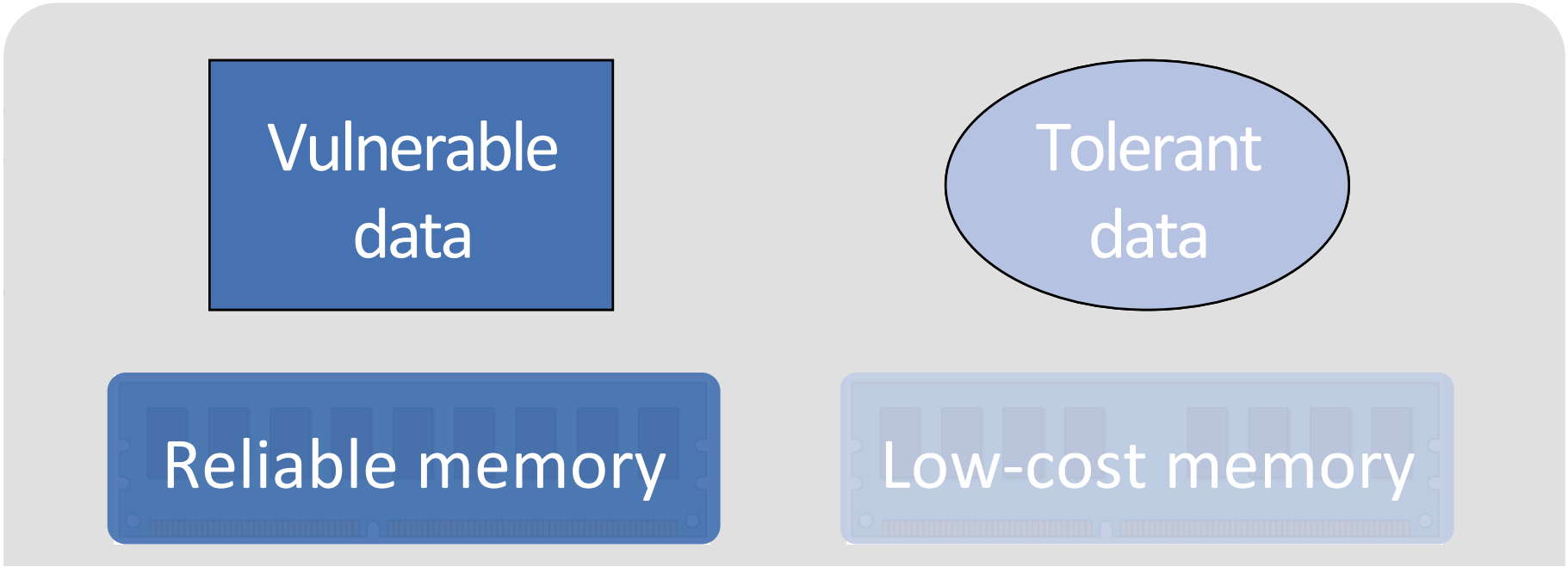


Hardware/software manage data allocation and movement
to achieve the best of multiple technologies

Meza+, "Enabling Efficient and Scalable Hybrid Memories," IEEE Comp. Arch. Letters, 2012.

Yoon, Meza et al., "Row Buffer Locality Aware Caching Policies for Hybrid Memories," ICCD 2012 Best Paper Award.

Exploiting Memory Error Tolerance with Hybrid Memory Systems



On Microsoft's Web Search workload

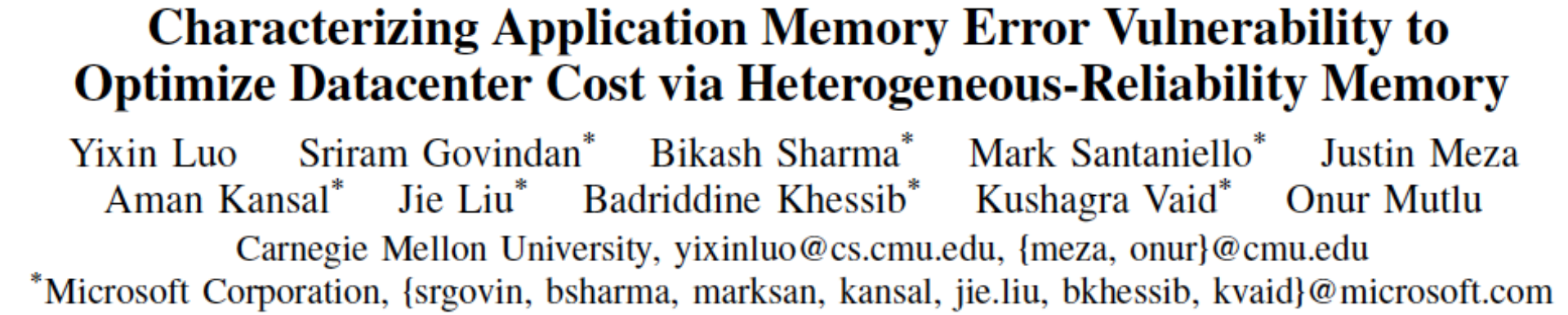
Reduces server hardware cost by 4.7 %

Achieves single server availability target of 99.90 %

Heterogeneous-**R**eliability **M**emory [DSN 2014]

More on Heterogeneous Reliability Memory

- Yixin Luo, Sriram Govindan, Bikash Sharma, Mark Santaniello, Justin Meza, Aman Kansal, Jie Liu, Badriddine Khessib, Kushagra Vaid, and Onur Mutlu, **"Characterizing Application Memory Error Vulnerability to Optimize Data Center Cost via Heterogeneous-Reliability Memory"** *Proceedings of the 44th Annual IEEE/IFIP International Conference on Dependable Systems and Networks (**DSN**)*, Atlanta, GA, June 2014. [Summary] [Slides (pptx) (pdf)] [Coverage on ZDNet]



Characterizing Application Memory Error Vulnerability to Optimize Datacenter Cost via Heterogeneous-Reliability Memory

Yixin Luo Sriram Govindan* Bikash Sharma* Mark Santaniello* Justin Meza
Aman Kansal* Jie Liu* Badriddine Khessib* Kushagra Vaid* Onur Mutlu

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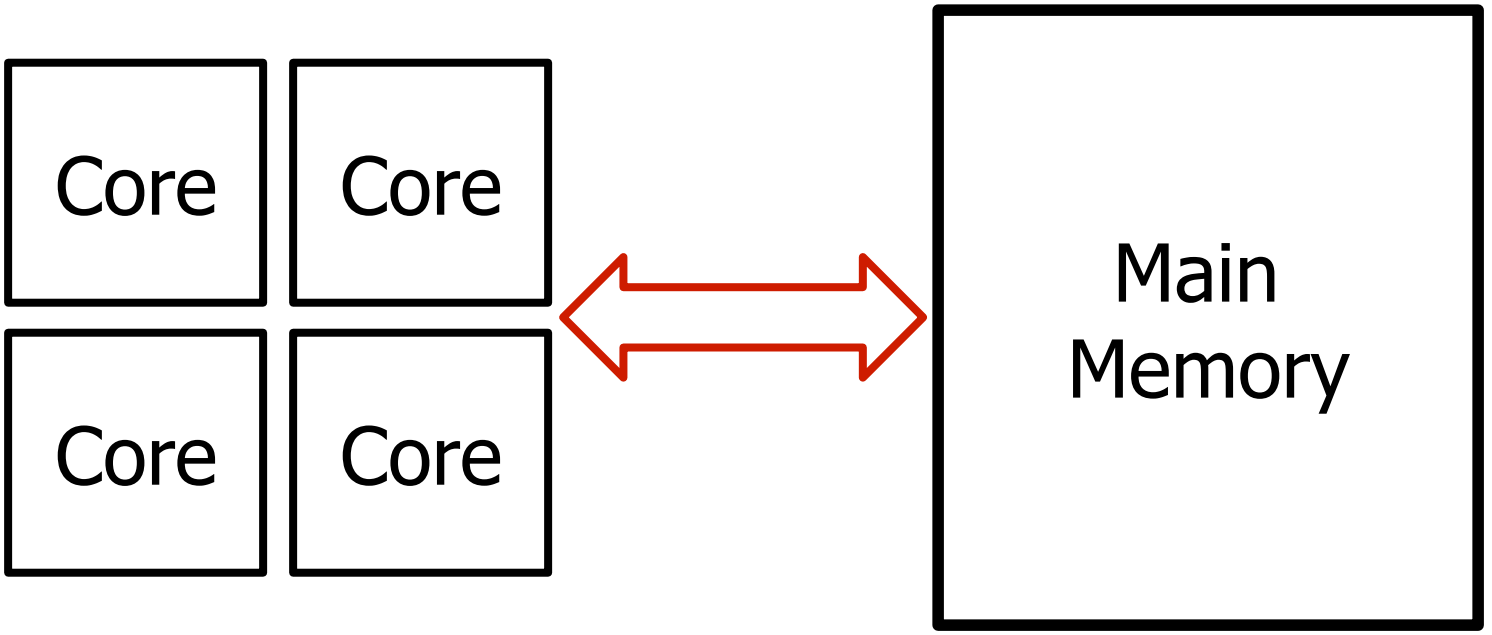
An Orthogonal Issue: Memory Interference



Cores' interfere with each other when accessing shared main memory
Uncontrolled interference leads to many problems (QoS, performance)

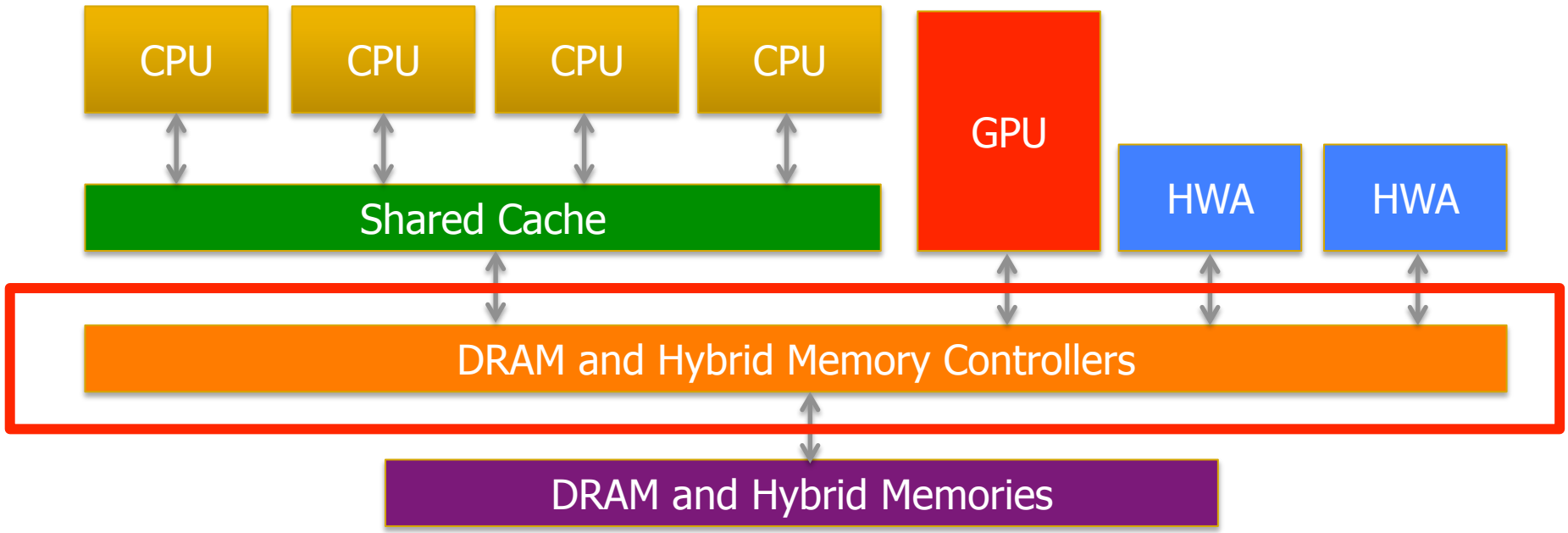
An Orthogonal Issue: Memory Interference

- Problem: Memory interference between cores is uncontrolled
  → unfairness, starvation, low performance
  → uncontrollable, unpredictable, vulnerable system

- Solution: QoS-Aware Memory Systems
  - Hardware designed to provide a configurable fairness substrate
    - Application-aware memory scheduling, partitioning, throttling
  - Software designed to configure the resources to satisfy different QoS goals

- QoS-aware memory systems can provide predictable performance and higher efficiency

Goal: Predictable Performance in Complex Systems



- Heterogeneous agents: CPUs, GPUs, and HWAs
- Main memory interference between CPUs, GPUs, HWAs

How to allocate resources to heterogeneous agents to mitigate interference and provide predictable performance?

Strong Memory Service Guarantees

- Goal: Satisfy performance/SLA requirements in the presence of shared main memory, heterogeneous agents, and hybrid memory/storage

- Approach:
  - Develop techniques/models to accurately estimate the performance loss of an application/agent in the presence of resource sharing
  - Develop mechanisms (hardware and software) to enable the resource partitioning/prioritization needed to achieve the required performance levels for all applications
  - All the while providing high system performance

- Subramanian et al., "MISE: Providing Performance Predictability and Improving Fairness in Shared Main Memory Systems," HPCA 2013.
- Subramanian et al., "The Application Slowdown Model," MICRO 2015.

How Can We Fix the Memory Problem & Design (Memory) Systems of the Future?

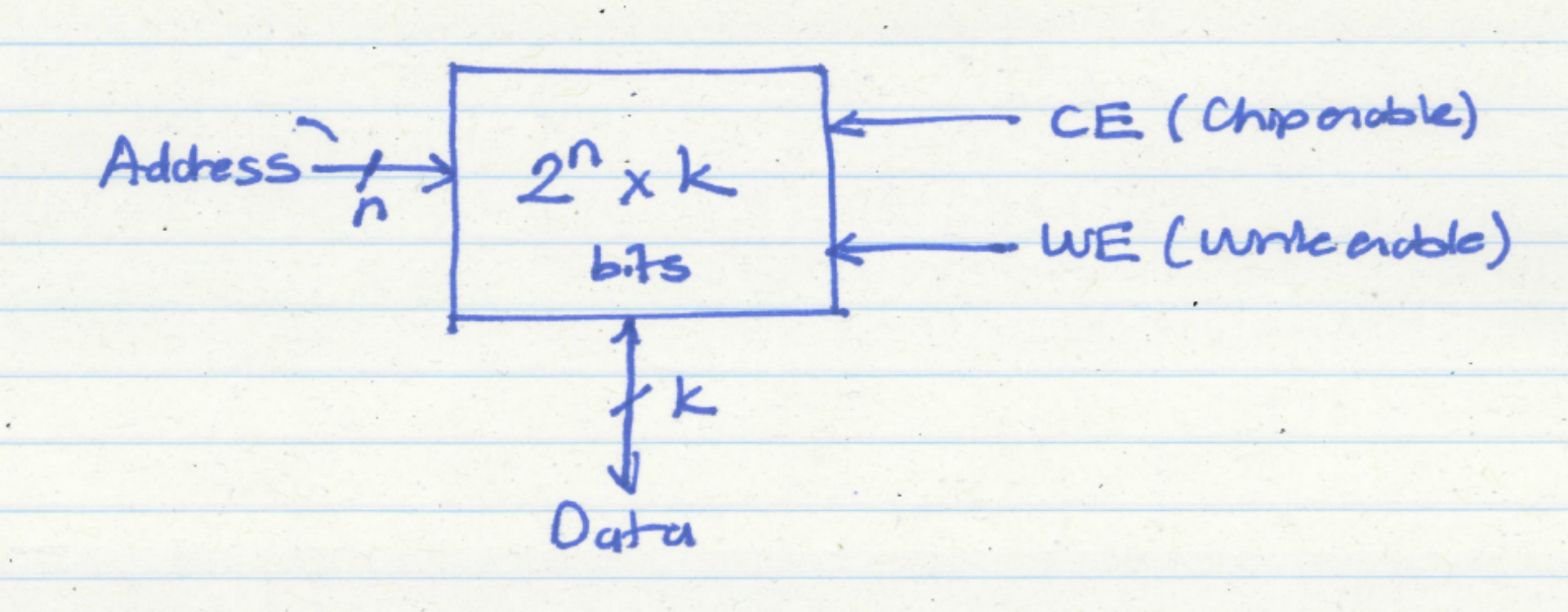
Look Backward to Look Forward

- We first need to understand the principles of:
  - Memory and DRAM
  - Memory controllers
  - Techniques for reducing and tolerating memory latency
  - Potential memory technologies that can compete with DRAM

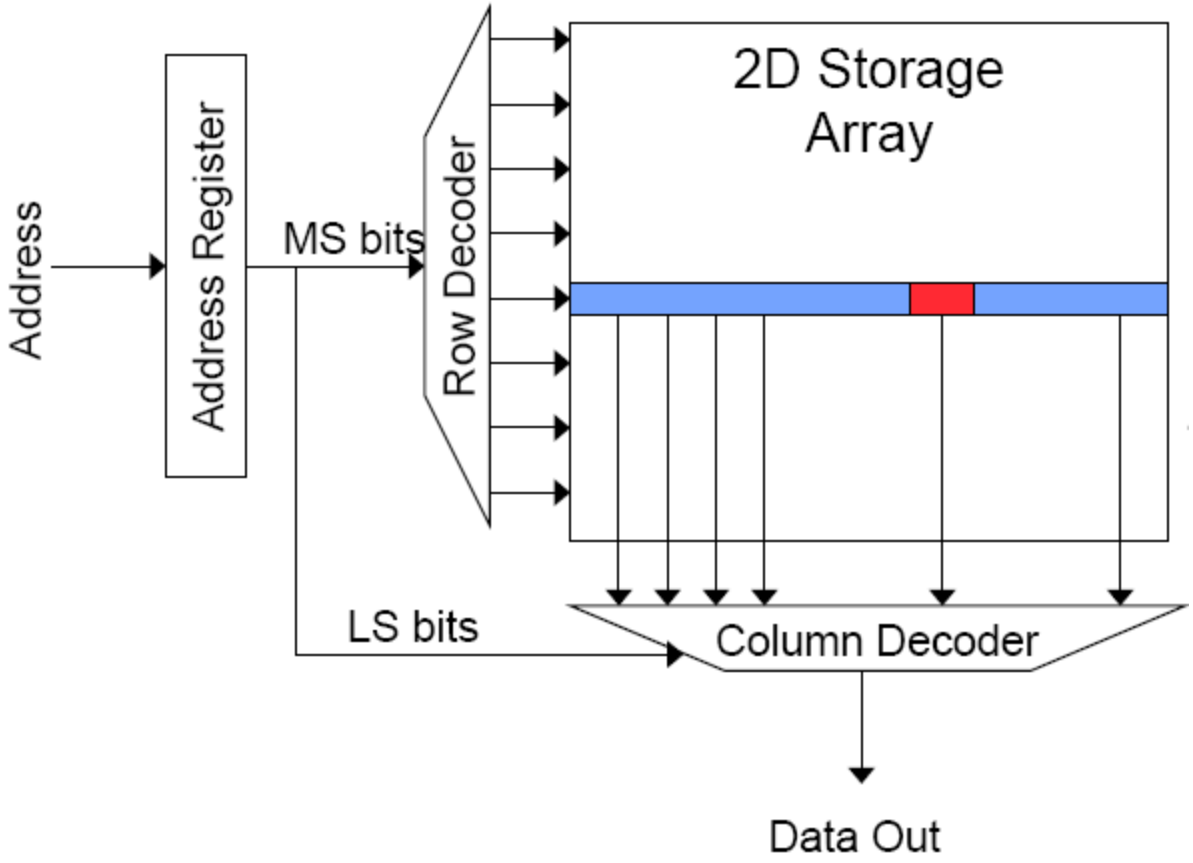
- This is what we will cover in the next lectures

Main Memory Fundamentals

The Memory Chip/System Abstraction



Review: Memory Bank Organization



- Read access sequence:

1. Decode row address & drive word-lines

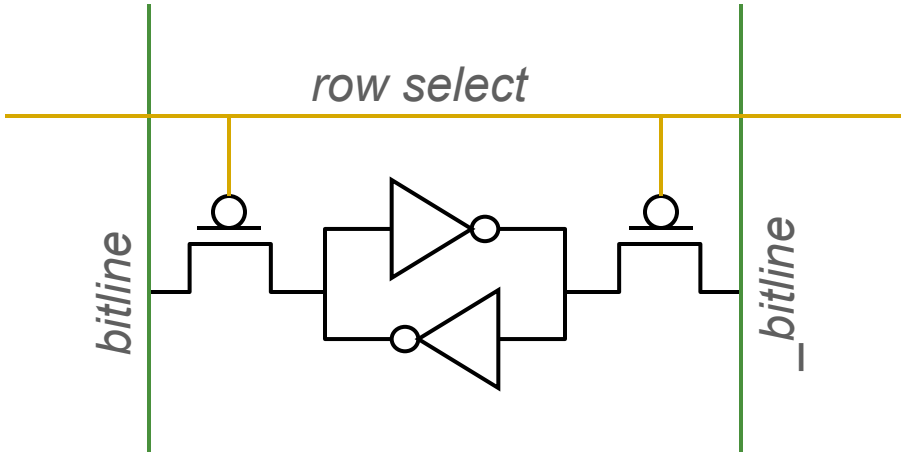
2. Selected bits drive bit-lines
   - Entire row read

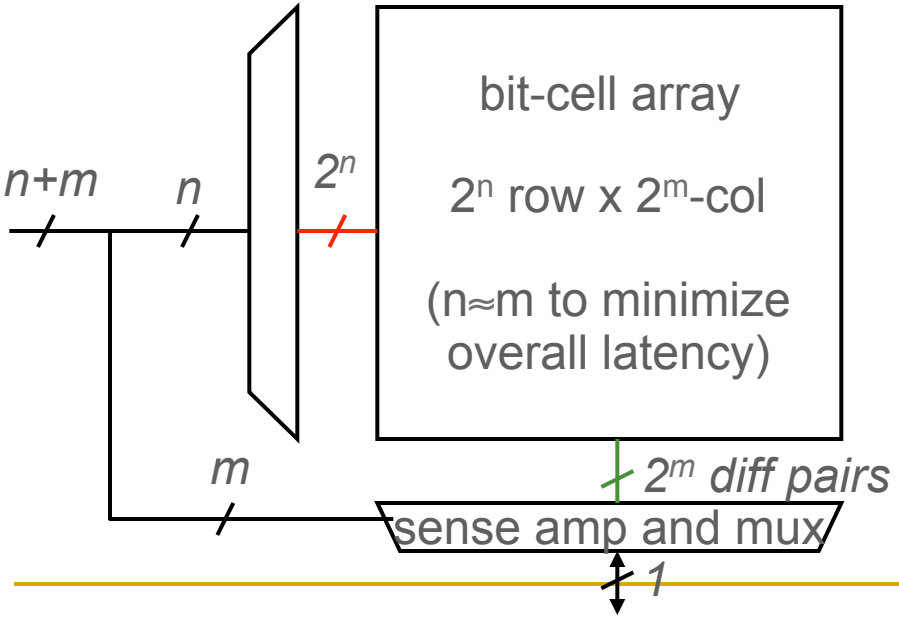
3. Amplify row data

4. Decode column address & select subset of row
   - Send to output

5. Precharge bit-lines
   - For next access

Review: SRAM (Static Random Access Memory)





Read Sequence

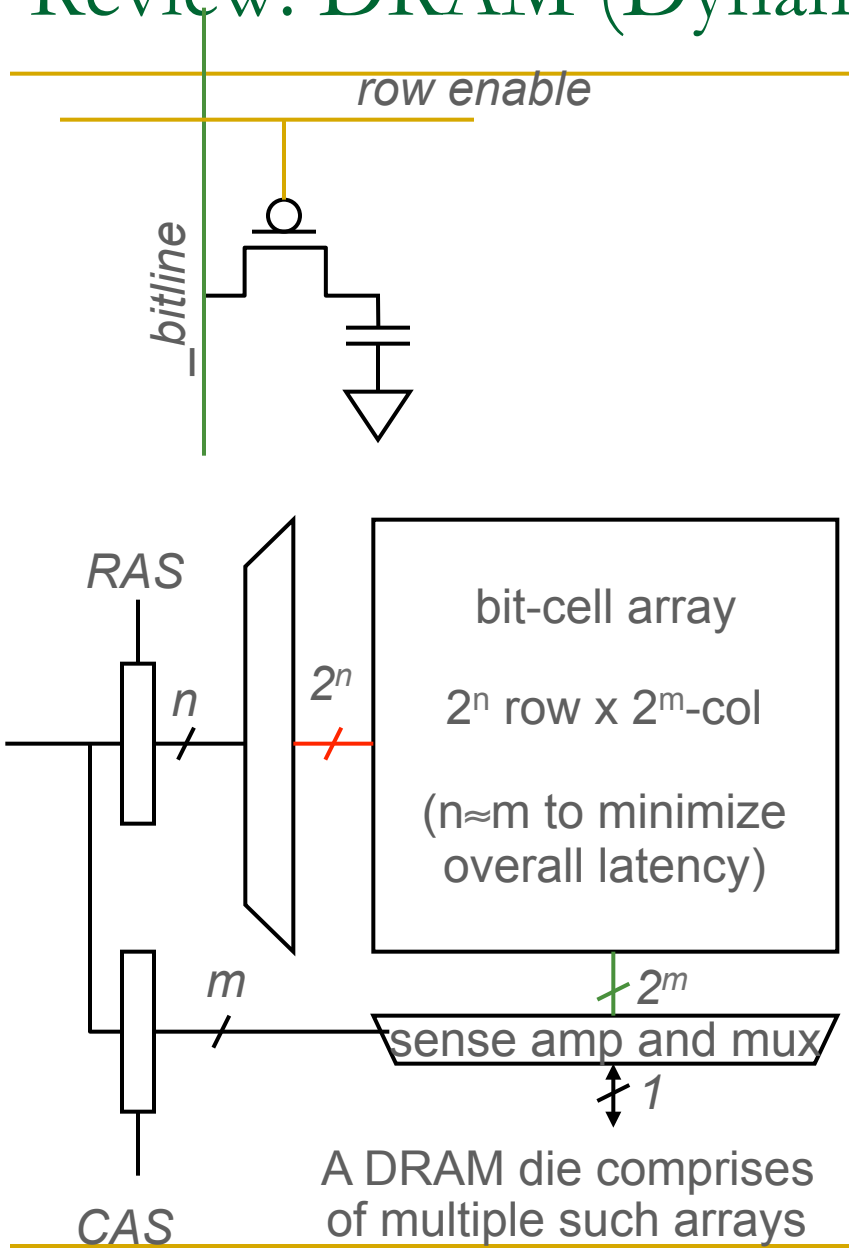
1. address decode
2. drive row select
3. selected bit-cells drive bitlines
   (entire row is read together)
4. differential sensing and column select
   (data is ready)
5. precharge all bitlines
   (for next read or write)

Access latency dominated by steps 2 and 3

Cycling time dominated by steps 2, 3 and 5

- step 2 proportional to 2^m
- step 3 and 5 proportional to 2^n

Review: DRAM (Dynamic Random Access Memory)



Bits stored as charges on node capacitance (non-restorative)

- bit cell loses charge when read
- bit cell loses charge over time

Read Sequence

1~3 same as SRAM

4. a "flip-flopping" sense amp amplifies and regenerates the bitline, data bit is mux'ed out

5. precharge all bitlines

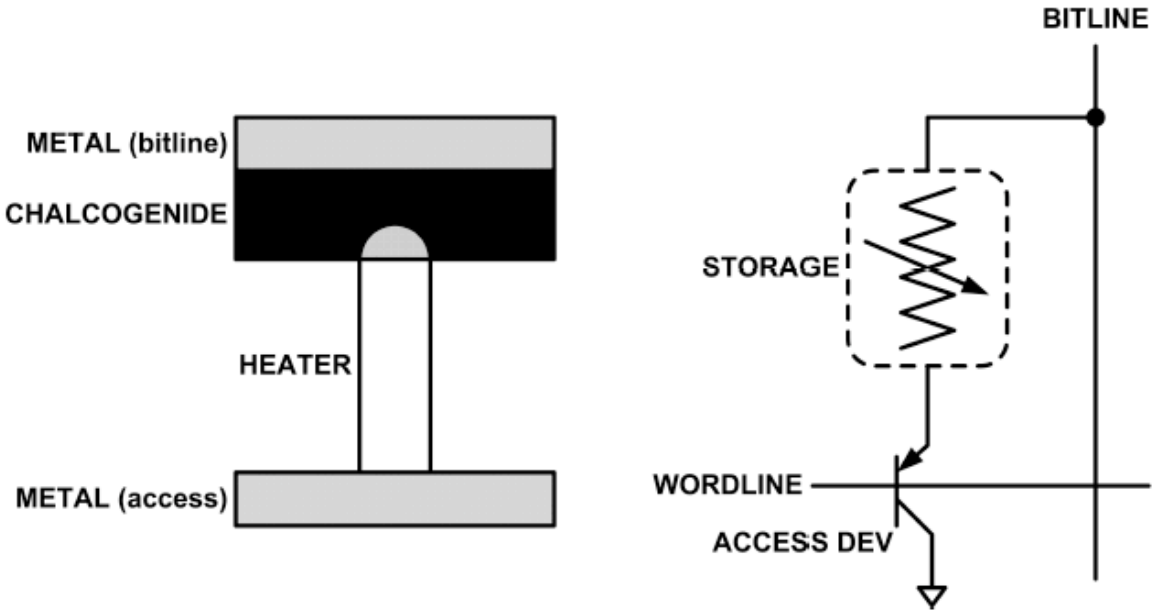
Destructive reads

Charge loss over time

Refresh: A DRAM controller must periodically read each row within the allowed refresh time (10s of ms) such that charge is restored

An Aside: Phase Change Memory

- Phase change material (chalcogenide glass) exists in two states:
  - Amorphous: Low optical reflexivity and high electrical resistivity
  - Crystalline: High optical reflexivity and low electrical resistivity



PCM is resistive memory: High resistance (0), Low resistance (1)

Lee, Ipek, Mutlu, Burger, "Architecting Phase Change Memory as a Scalable DRAM Alternative," ISCA 2009.

Review: DRAM vs. SRAM

- DRAM
  - Slower access (capacitor)
  - Higher density (1T 1C cell)
  - Lower cost
  - Requires refresh (power, performance, circuitry)
  - Manufacturing requires putting capacitor and logic together

- SRAM
  - Faster access (no capacitor)
  - Lower density (6T cell)
  - Higher cost
  - No need for refresh
  - Manufacturing compatible with logic process (no capacitor)

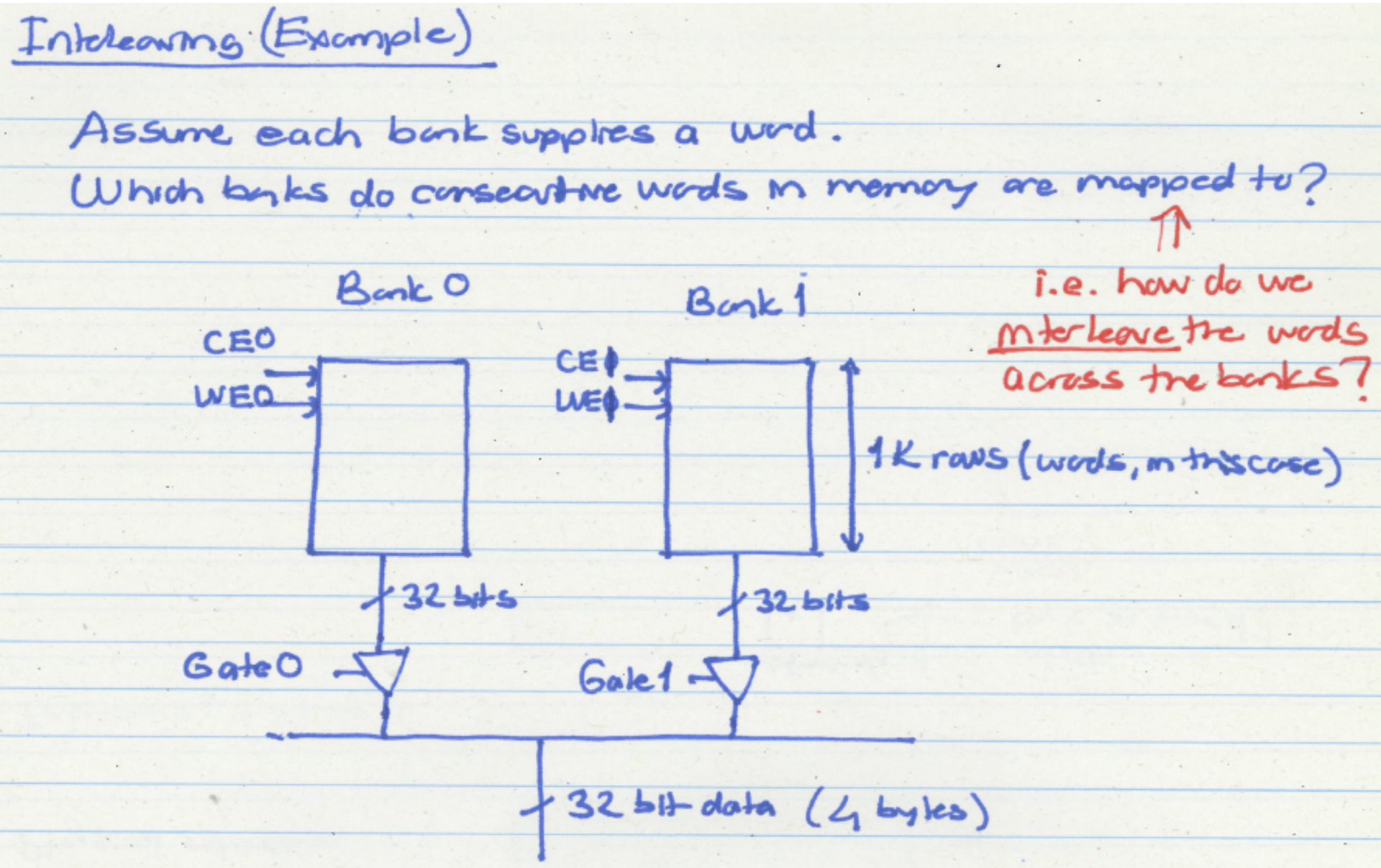
Some Fundamental Concepts (I)

- Physical address space
  - Maximum size of main memory: total number of uniquely identifiable locations
- Physical addressability
  - Minimum size of data in memory can be addressed
  - Byte-addressable, word-addressable, 64-bit-addressable
  - Microarchitectural addressability depends on the abstraction level of the implementation
- Alignment
  - Does the hardware support unaligned access transparently to software?
- Interleaving

Some Fundamental Concepts (II)

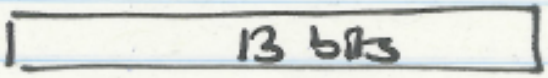
- Interleaving (banking)
  - Problem: a single monolithic memory array takes long to access and does not enable multiple accesses in parallel
  - Goal: Reduce the latency of memory array access and enable multiple accesses in parallel
  - Idea: Divide the array into multiple banks that can be accessed independently (in the same cycle or in consecutive cycles)
    - Each bank is smaller than the entire memory storage
    - Accesses to different banks can be overlapped
  - A Key Issue: How do you map data to different banks? (i.e., how do you interleave data across banks?)

Interleaving

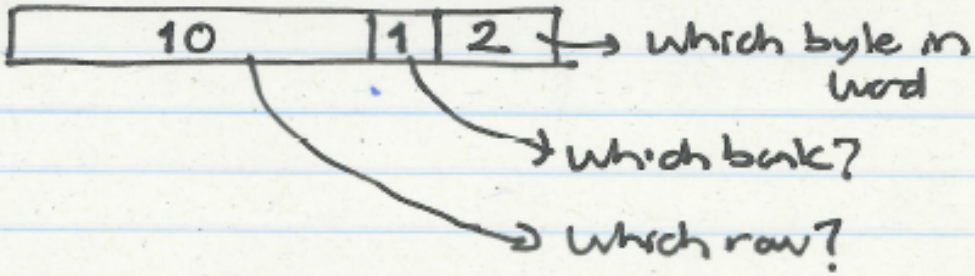


Interleaving Options

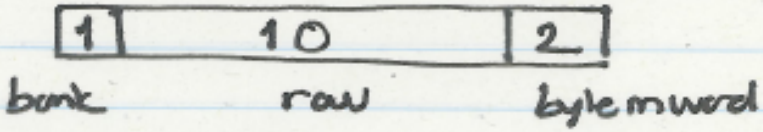
Physical address



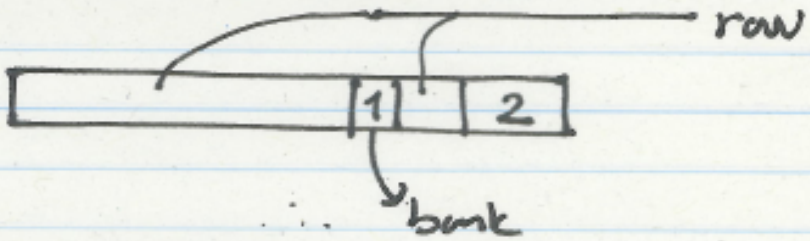
Interleaving scheme 1



Interleaving scheme 2



Interleaving scheme 3

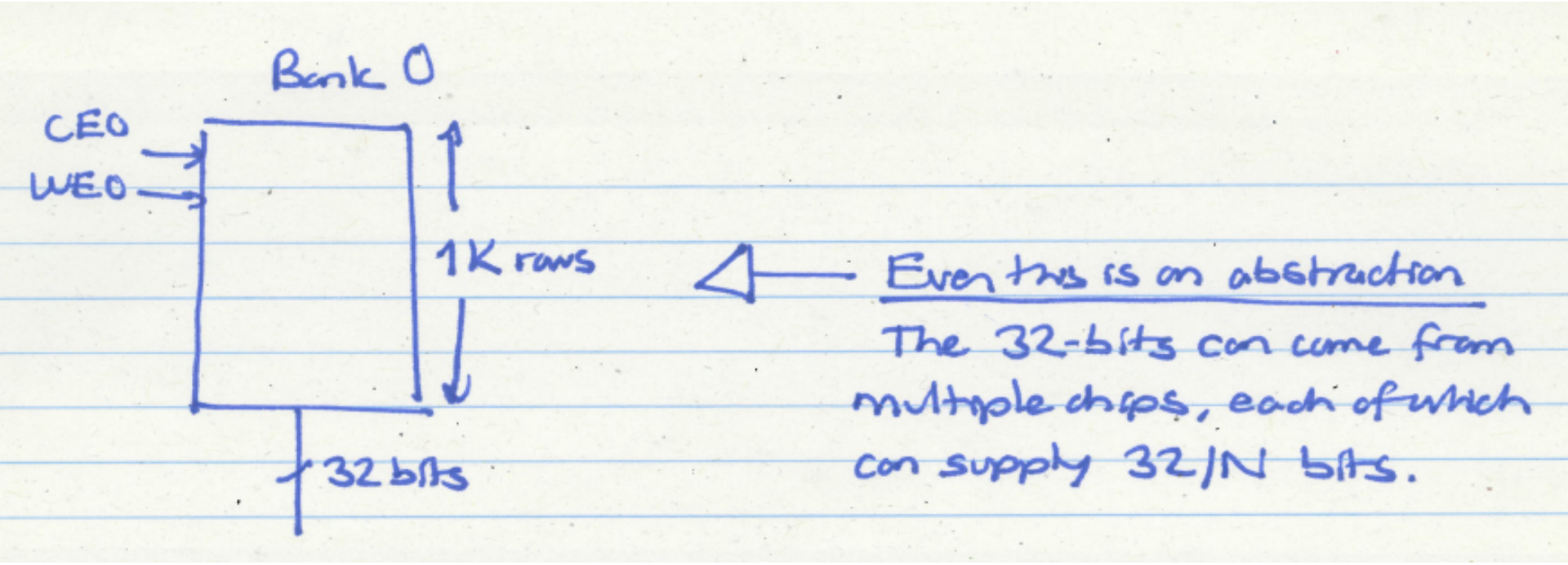


Where (which bank) do consecutive words in memory are mapped to?

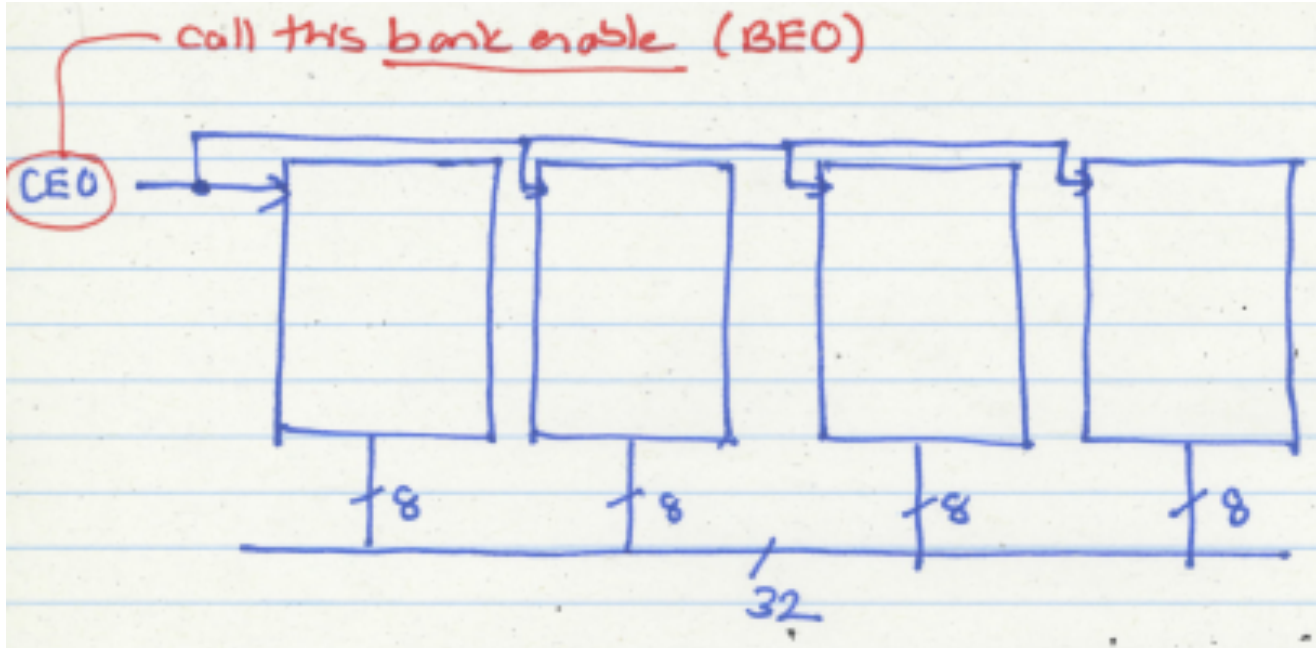
Some Questions/Concepts

- Remember CRAY-1 with 16 banks [From Digital Circuits]
  - 11 cycle bank latency; banks share address/data buses
  - Consecutive words in memory in consecutive banks (word interleaving)
  - 1 access can be started (and finished) per cycle
- Can banks be operated *fully* in parallel?
  - Multiple accesses started per cycle?
- What is the cost of this?
  - We have seen it earlier
- Modern superscalar processors have L1 data caches with multiple, fully-independent banks; DRAM banks share buses

The Bank Abstraction



Rank



This is called a "rank." (only bank 0 of the rank shown here)

Rank: A set of chips that respond to the same command & same address at the same time with different pieces of the requested data

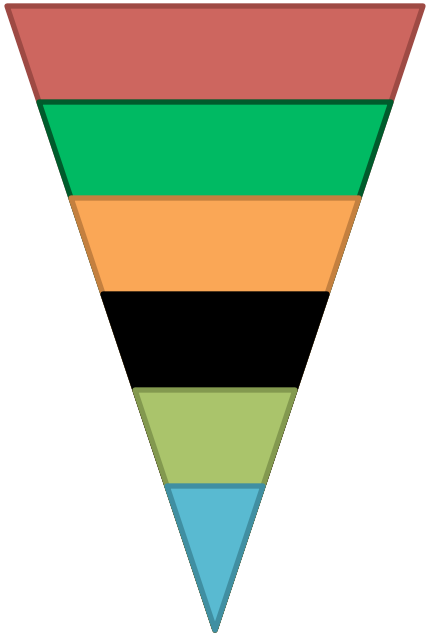
Why? Producing an 8-bit/pin chip cheaper than producing a 32-bit/pin chip

Idea: Produce an 8-bit/pin chip, but control/operate them as a rank so that we can get 32 bits in a single read.

The DRAM Subsystem

DRAM Subsystem Organization

- Channel
- DIMM
- Rank
- Chip
- Bank
- Row/Column

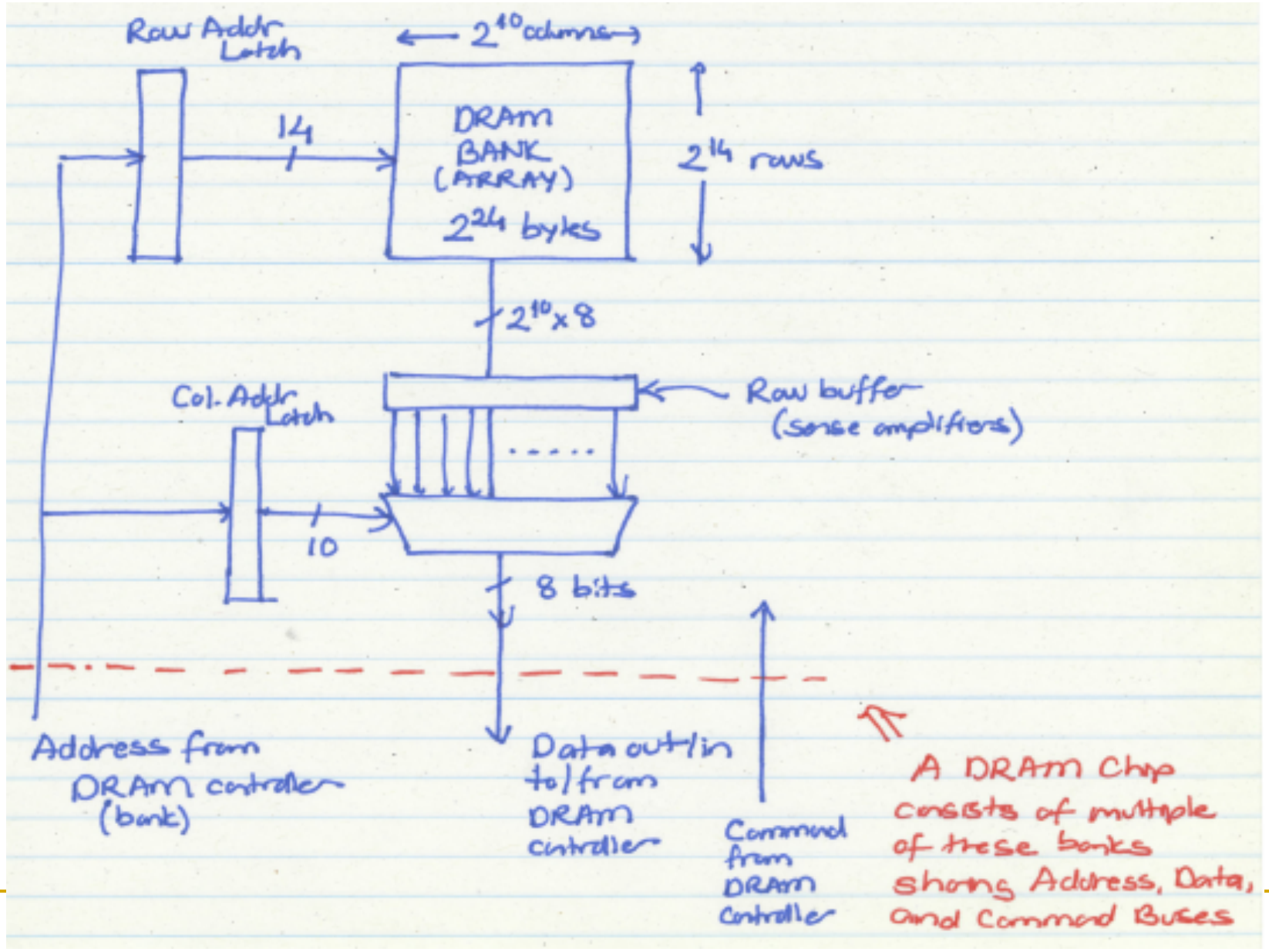


Page Mode DRAM

- A DRAM bank is a 2D array of cells: rows x columns
- A "DRAM row" is also called a "DRAM page"
- "Sense amplifiers" also called "row buffer"

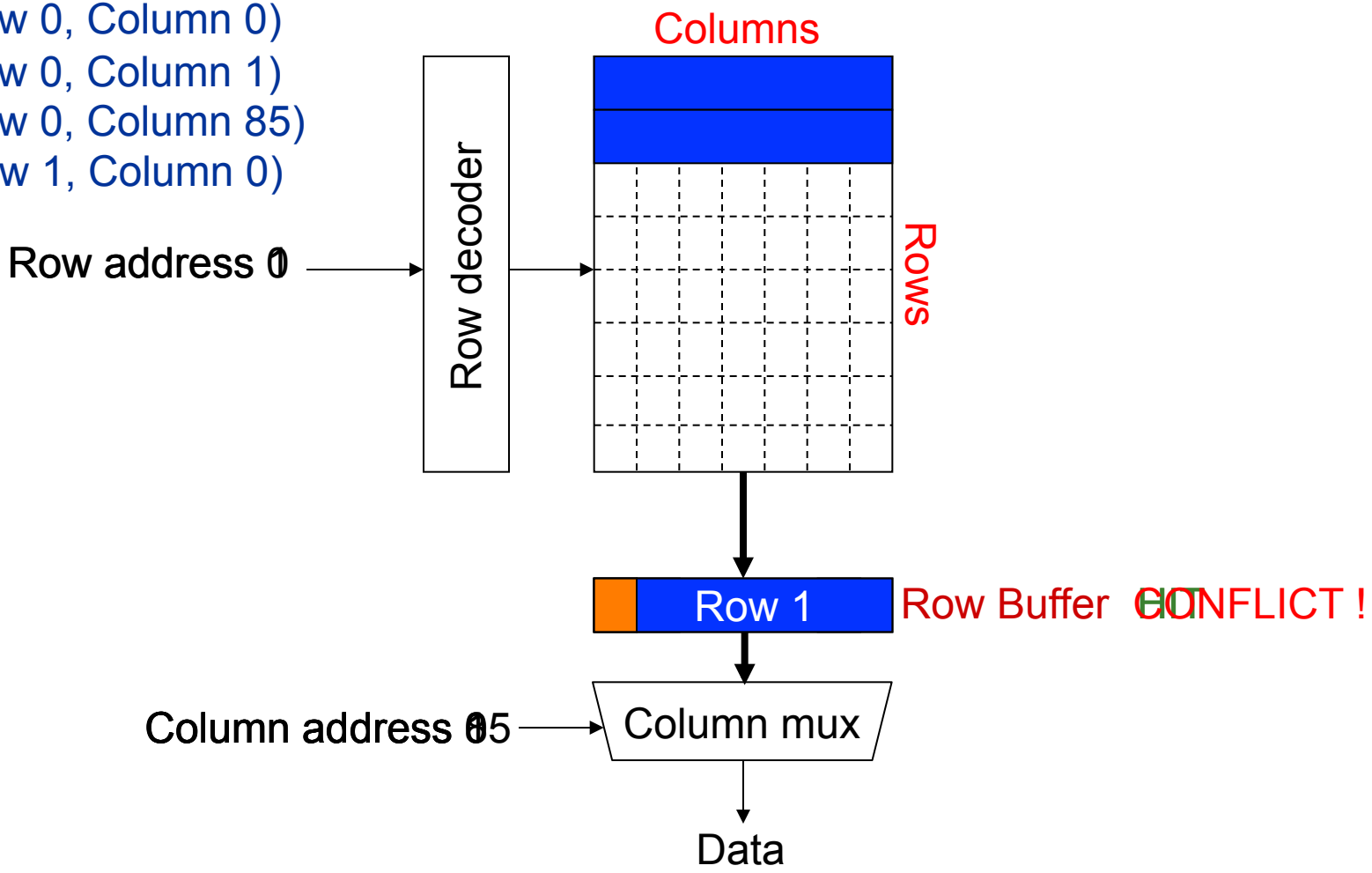
- Each address is a <row,column> pair
- Access to a "closed row"
  - Activate command opens row (placed into row buffer)
  - Read/write command reads/writes column in the row buffer
  - Precharge command closes the row and prepares the bank for next access
- Access to an "open row"
  - No need for activate command

The DRAM Bank Structure



DRAM Bank Operation

Access Address:
(Row 0, Column 0)
(Row 0, Column 1)
(Row 0, Column 85)
(Row 1, Column 0)

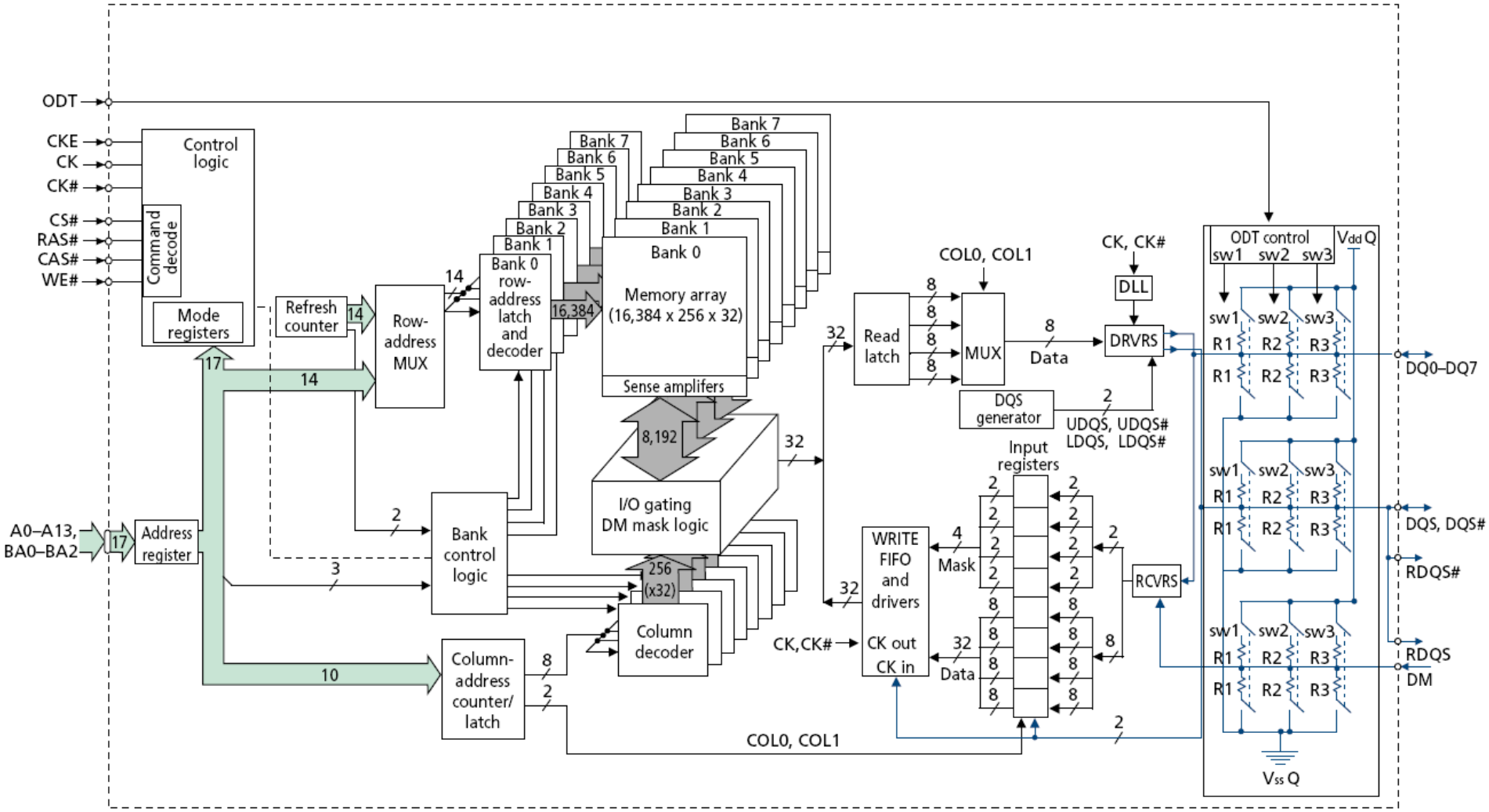


The DRAM Chip

- Consists of multiple banks (8 is a common number today)
- Banks share command/address/data buses
- The chip itself has a narrow interface (4-16 bits per read)

- Changing the number of banks, size of the interface (pins), whether or not command/address/data buses are shared has significant impact on DRAM system cost

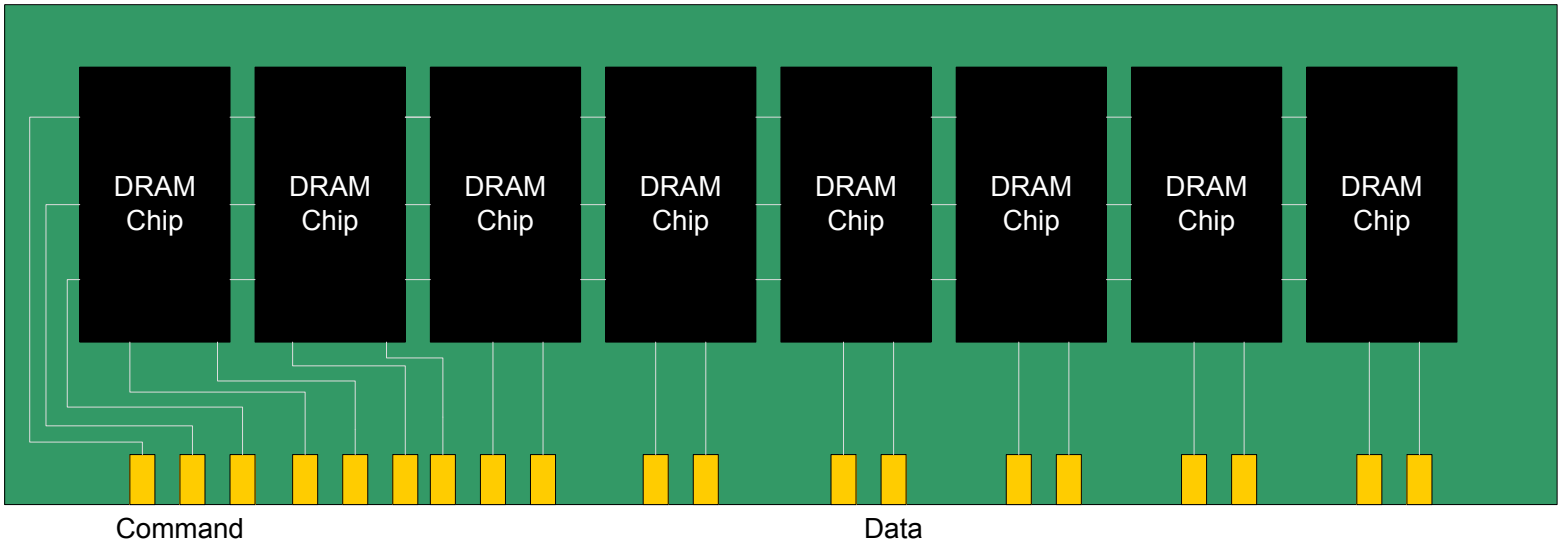
128M x 8-bit DRAM Chip



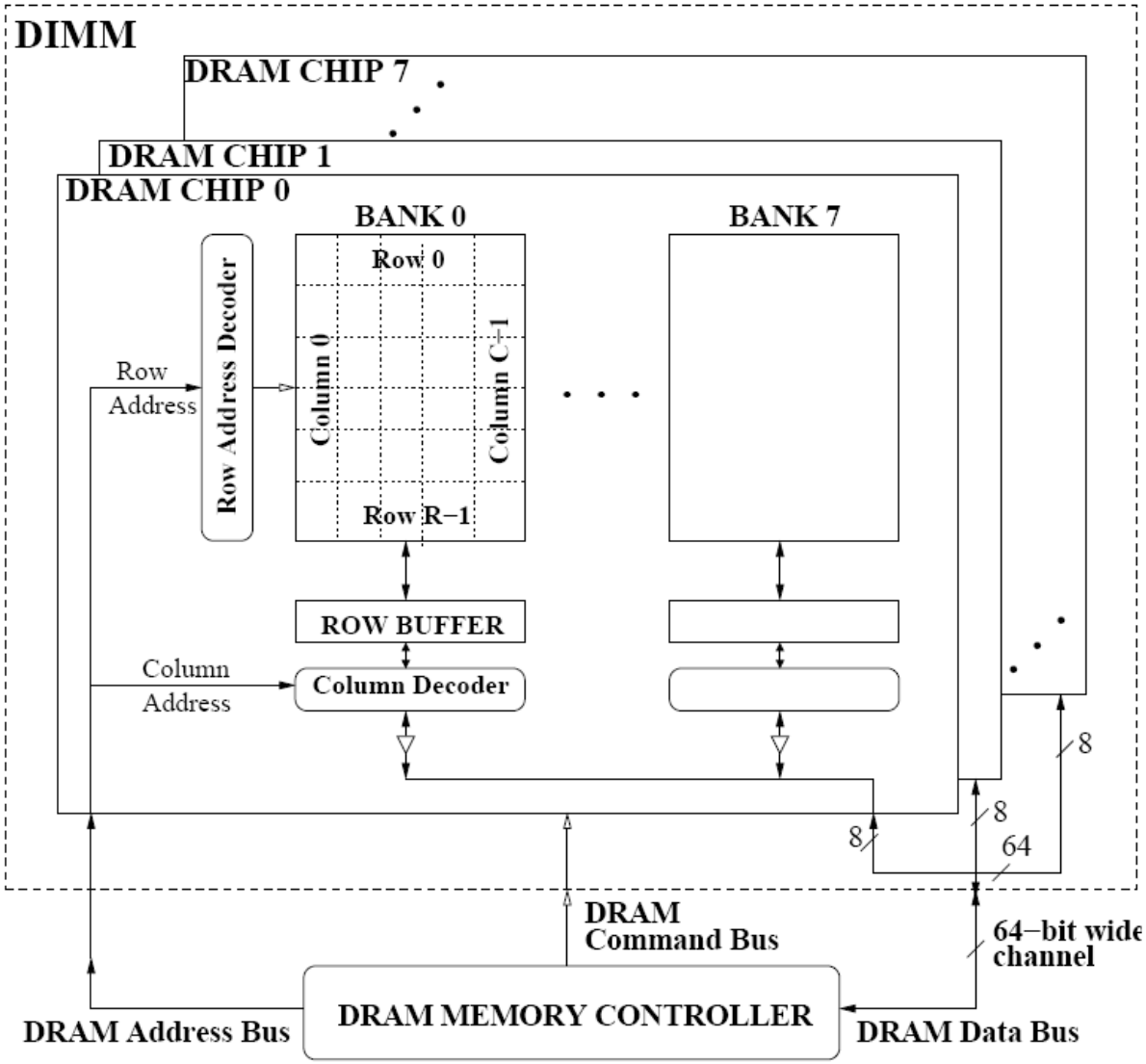
DRAM Rank and Module

- Rank: Multiple chips operated together to form a wide interface
- All chips comprising a rank are controlled at the same time
  - Respond to a single command
  - Share address and command buses, but provide different data
- A DRAM module consists of one or more ranks
  - E.g., DIMM (dual inline memory module)
  - This is what you plug into your motherboard
- If we have chips with 8-bit interface, to read 8 bytes in a single access, use 8 chips in a DIMM

A 64-bit Wide DIMM (One Rank)

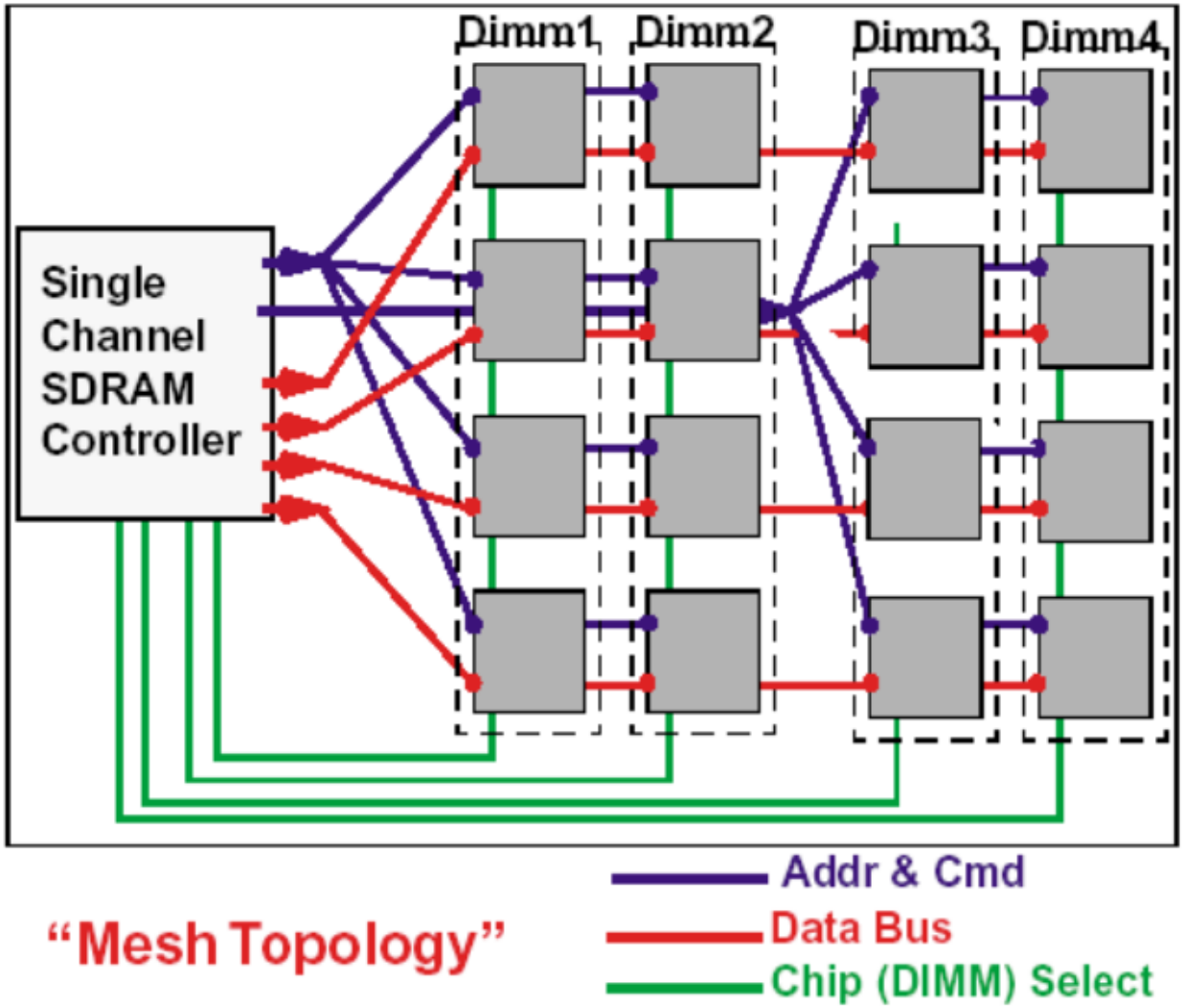


A 64-bit Wide DIMM (One Rank)



- Advantages:
  - Acts like a high-capacity DRAM chip with a wide interface
  - Flexibility: memory controller does not need to deal with individual chips
- Disadvantages:
  - Granularity: Accesses cannot be smaller than the interface width

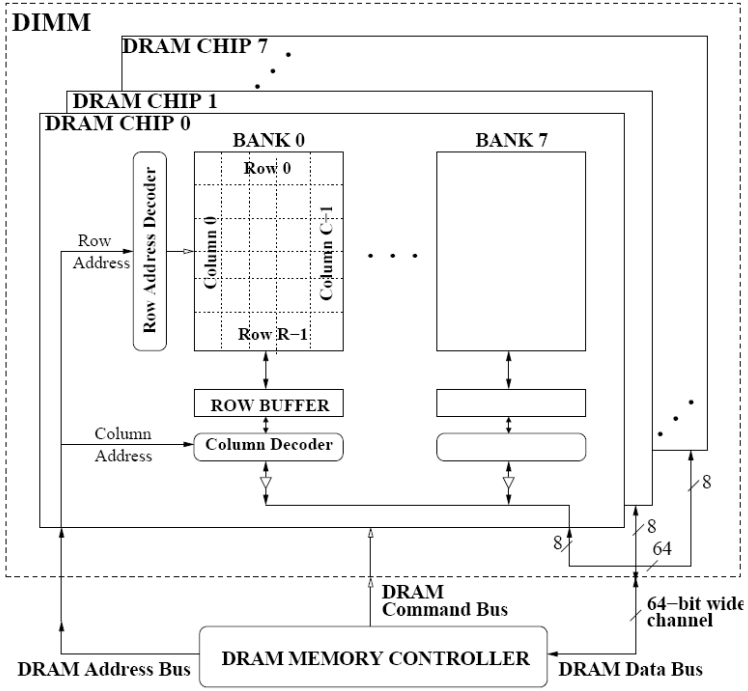
Multiple DIMMs

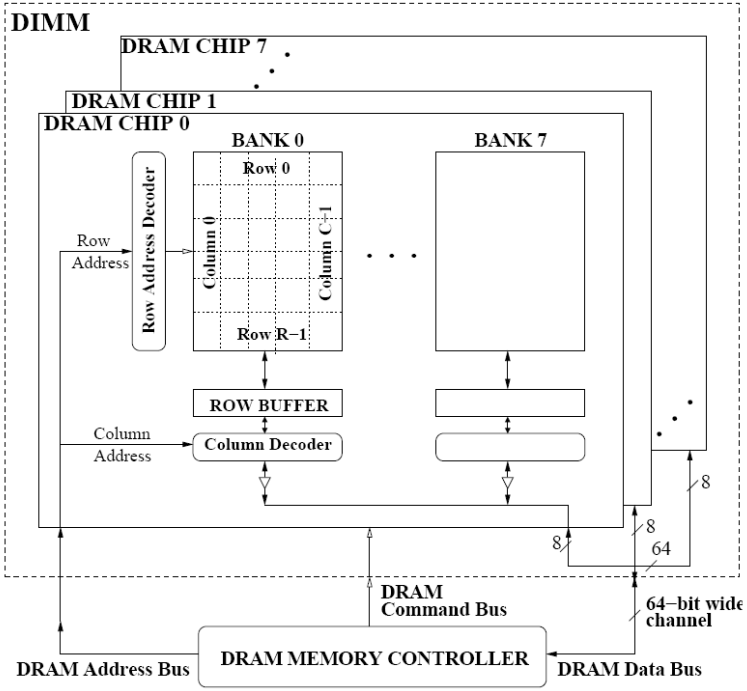


- Advantages:
  - Enables even higher capacity
- Disadvantages:
  - Interconnect complexity and energy consumption can be high

  → Scalability is limited by this

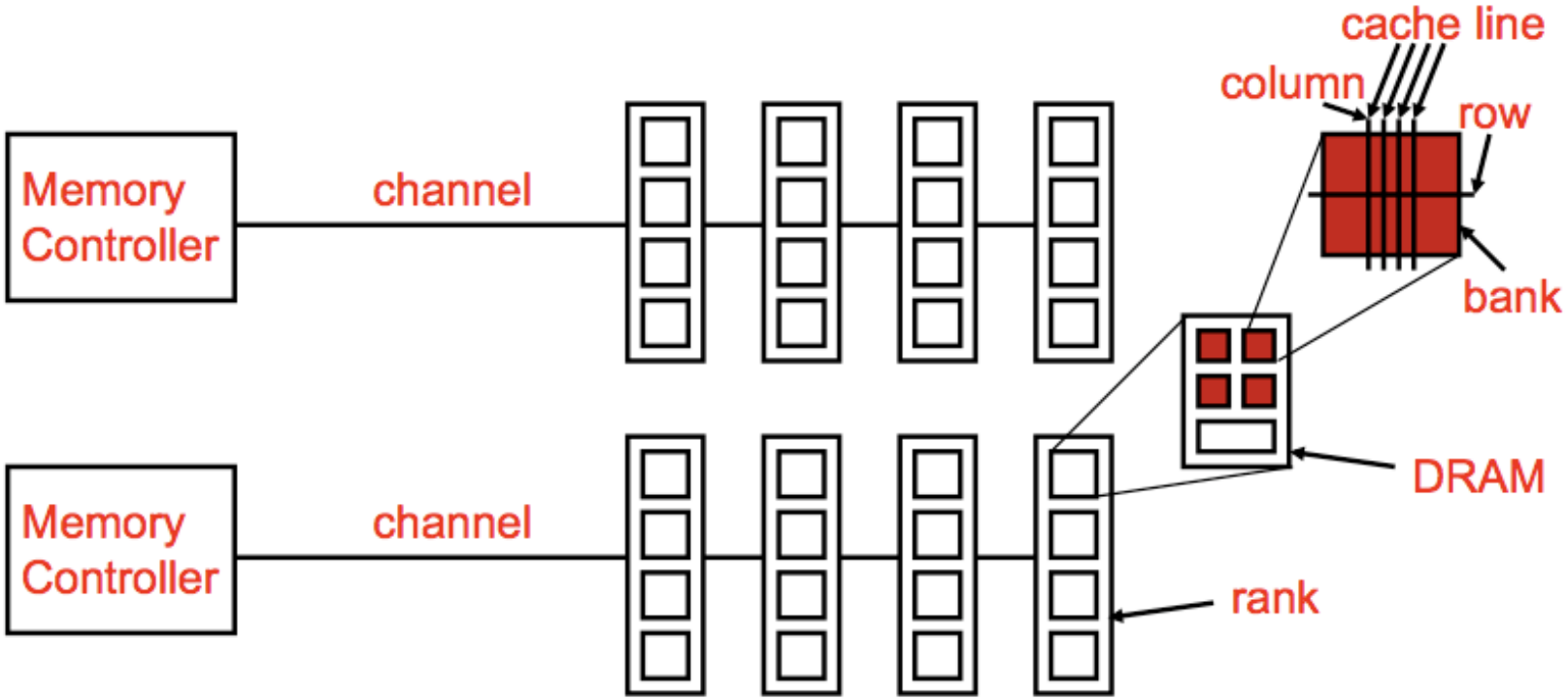
DRAM Channels



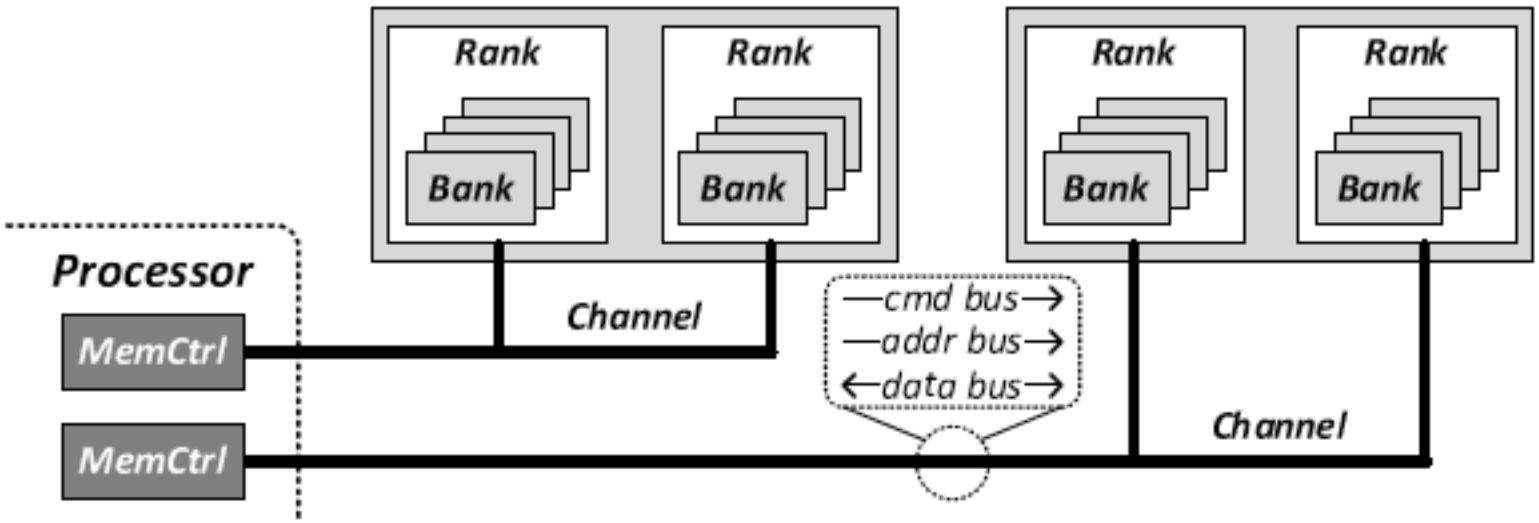


- 2 Independent Channels: 2 Memory Controllers (Above)
- 2 Dependent/Lockstep Channels: 1 Memory Controller with wide interface (Not shown above)

Generalized Memory Structure



Generalized Memory Structure



Kim+, "A Case for Exploiting Subarray-Level Parallelism in DRAM," ISCA 2012.

Computer Architecture

Lecture 4: Main Memory and DRAM Fundamentals

Prof. Onur Mutlu
ETH Zürich

Fall 2017

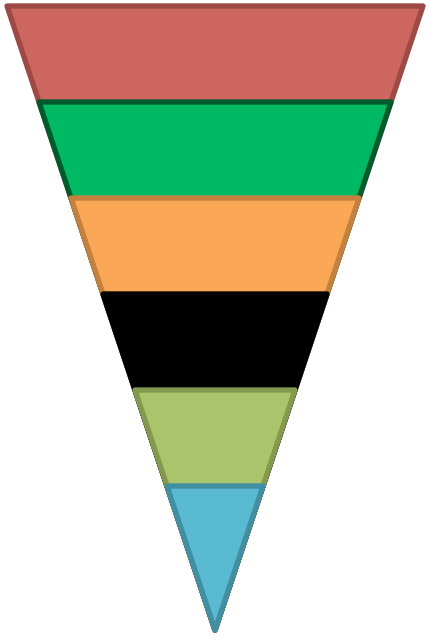
28 September 2017

We did not cover the following slides in lecture. These are for your preparation for the next lecture.

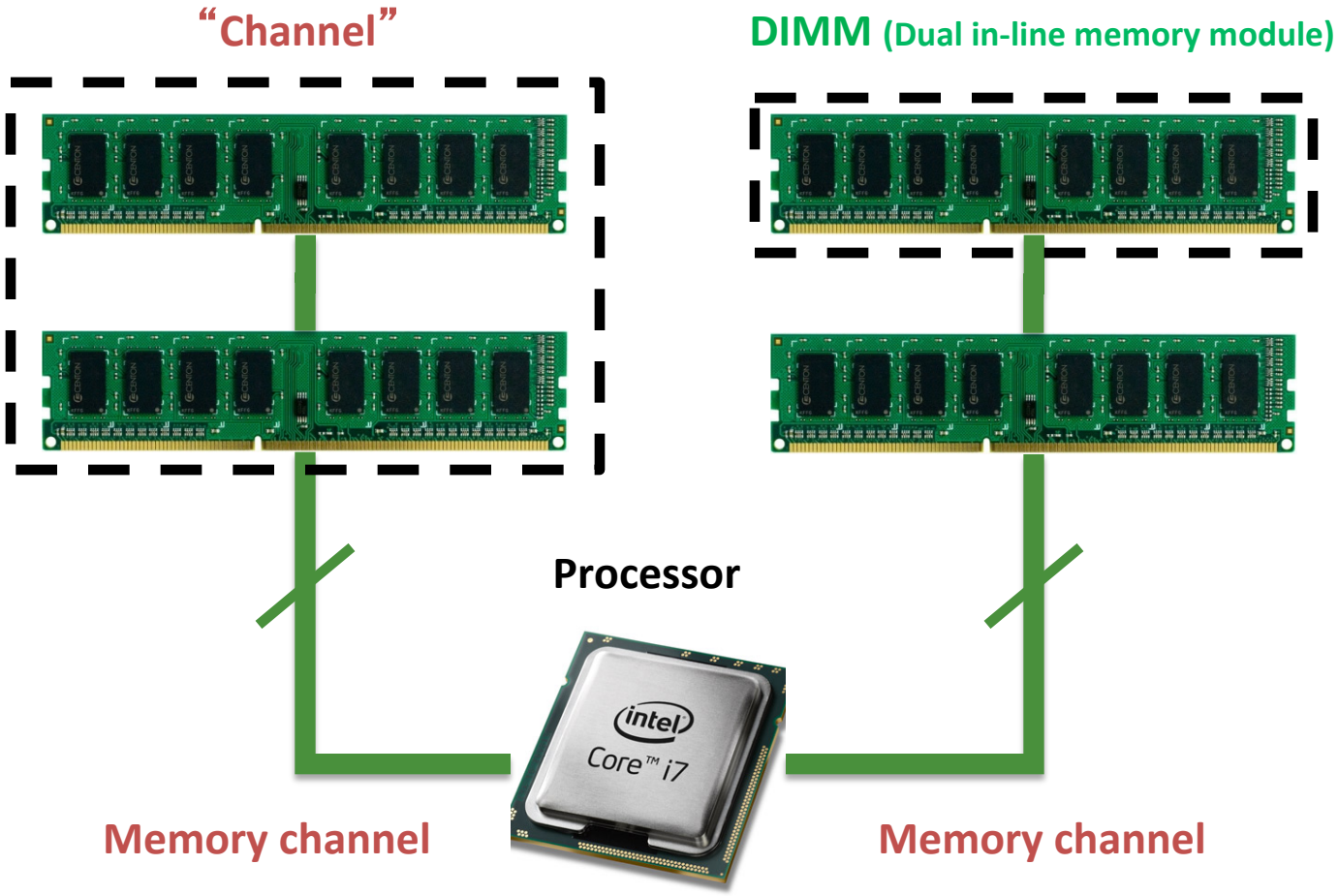
The DRAM Subsystem
The Top Down View

DRAM Subsystem Organization

- Channel
- DIMM
- Rank
- Chip
- Bank
- Row/Column
- Cell



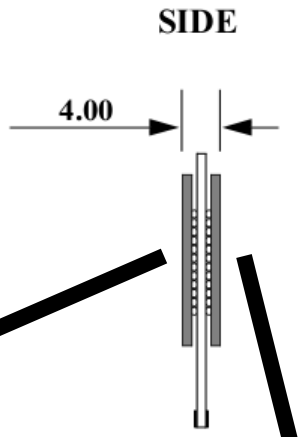
The DRAM subsystem



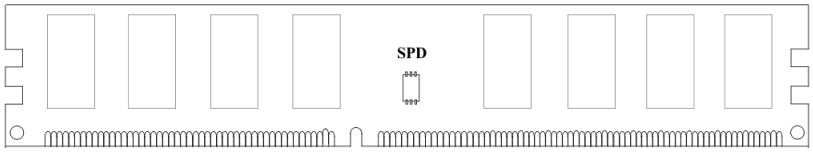
Breaking down a DIMM

DIMM (Dual in-line memory module)

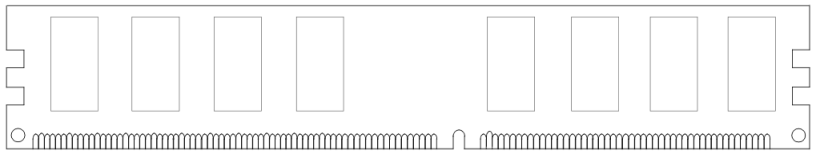
Side view



Front of DIMM



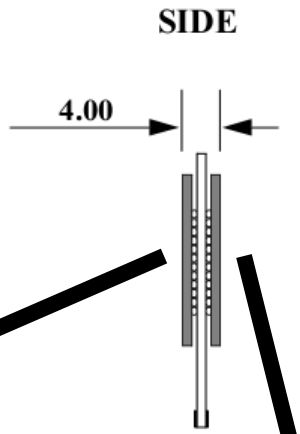
Back of DIMM



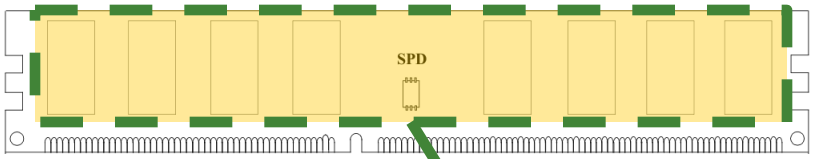
Breaking down a DIMM

DIMM (Dual in-line memory module)

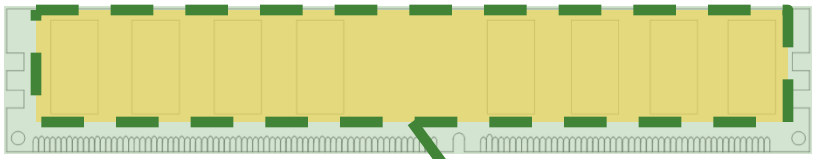
Side view



Front of DIMM



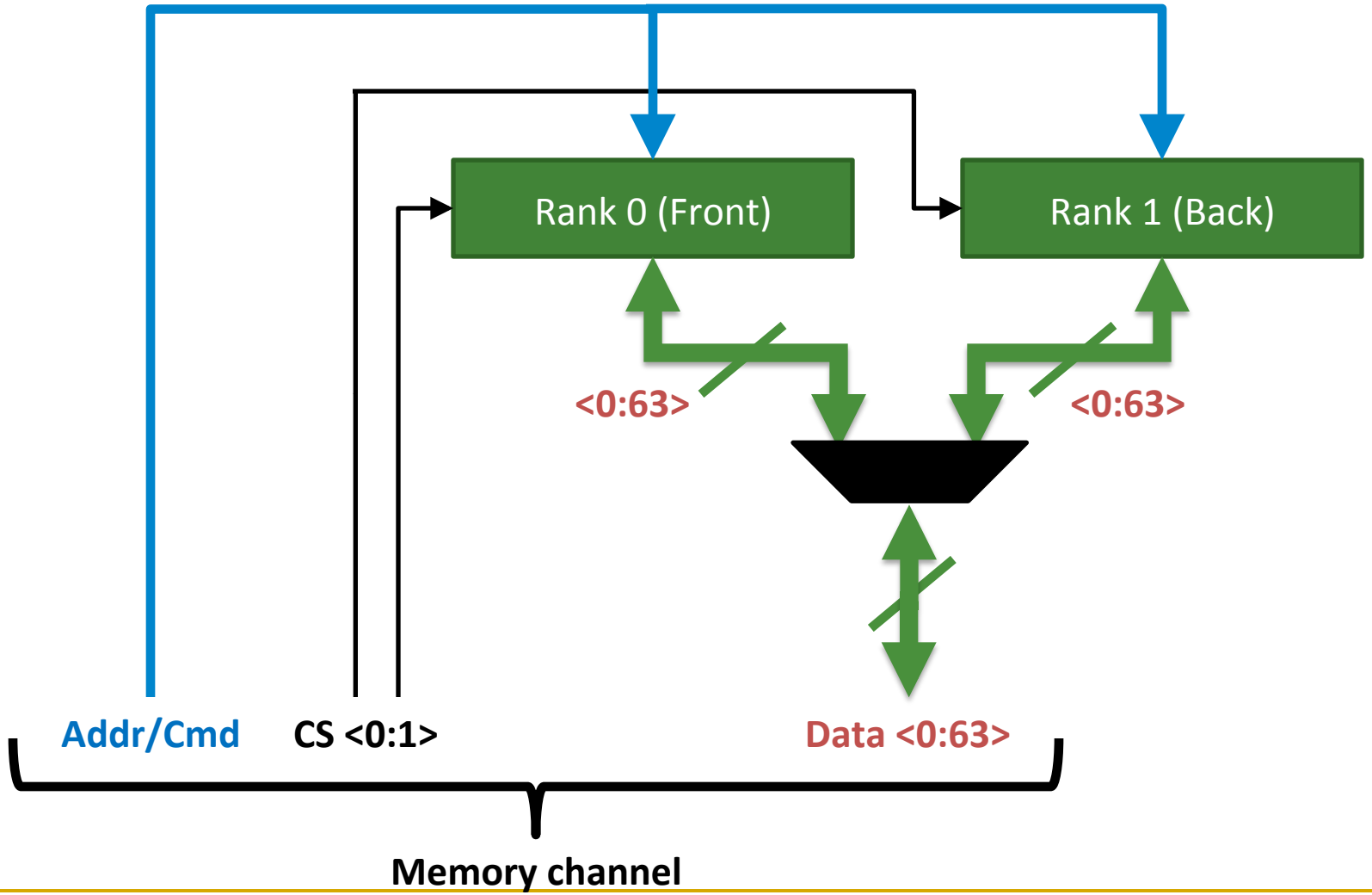
Back of DIMM



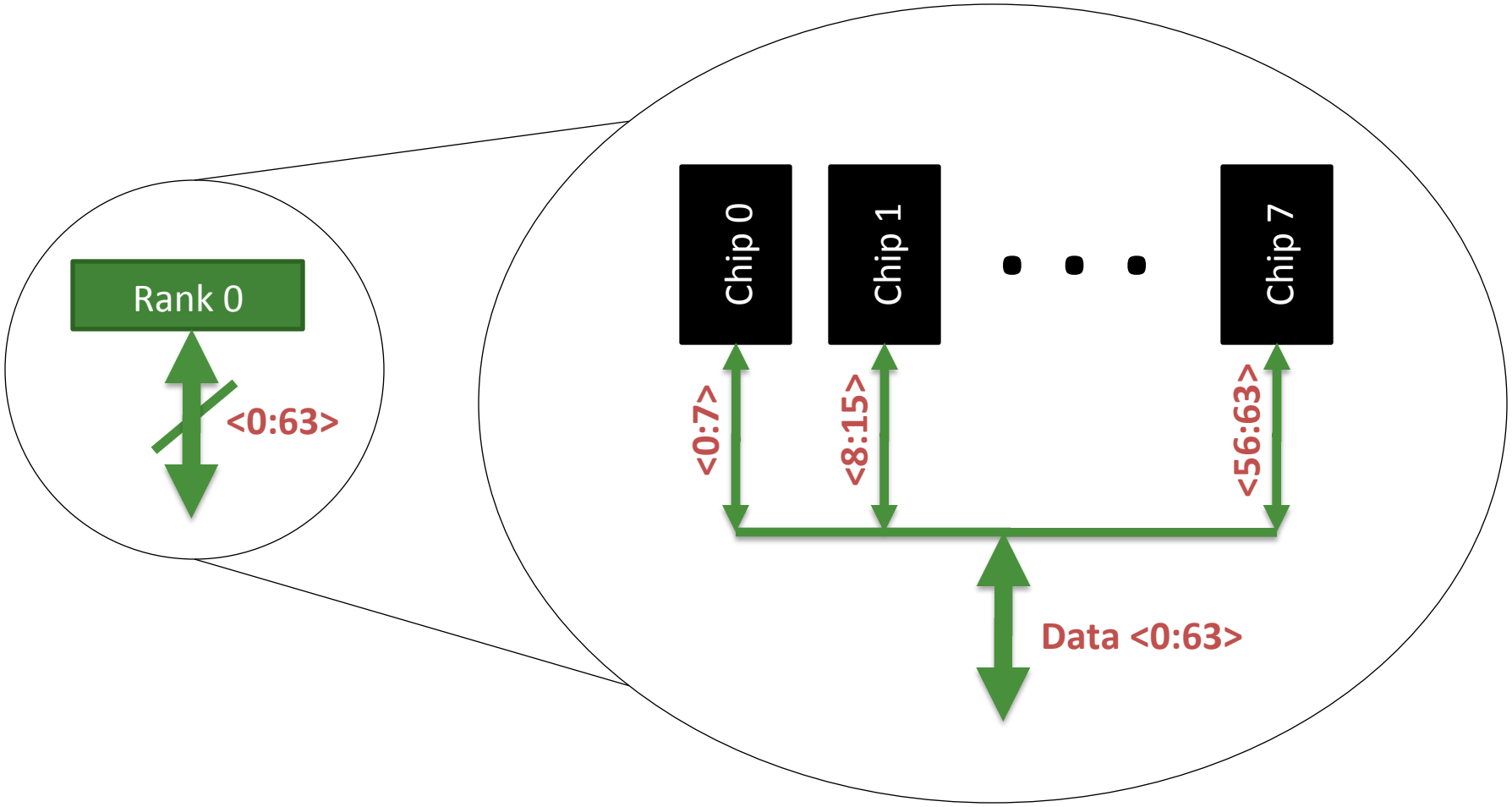
Rank 0: collection of 8 chips

Rank 1

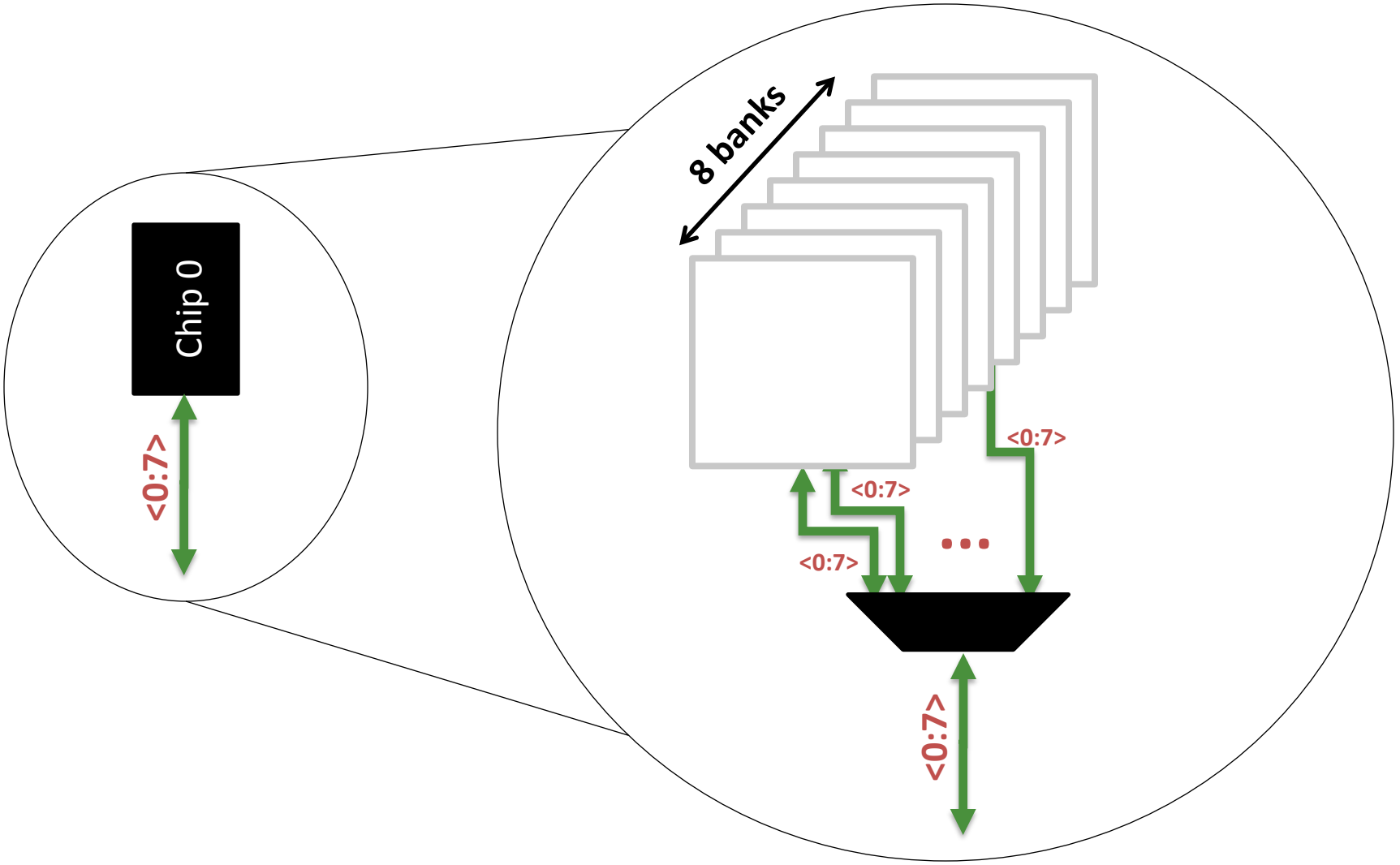
Rank


Rank 0 (Front)
Rank 1 (Back)
<0:63>
<0:63>
Addr/Cmd
CS <0:1>
Data <0:63>
Memory channel

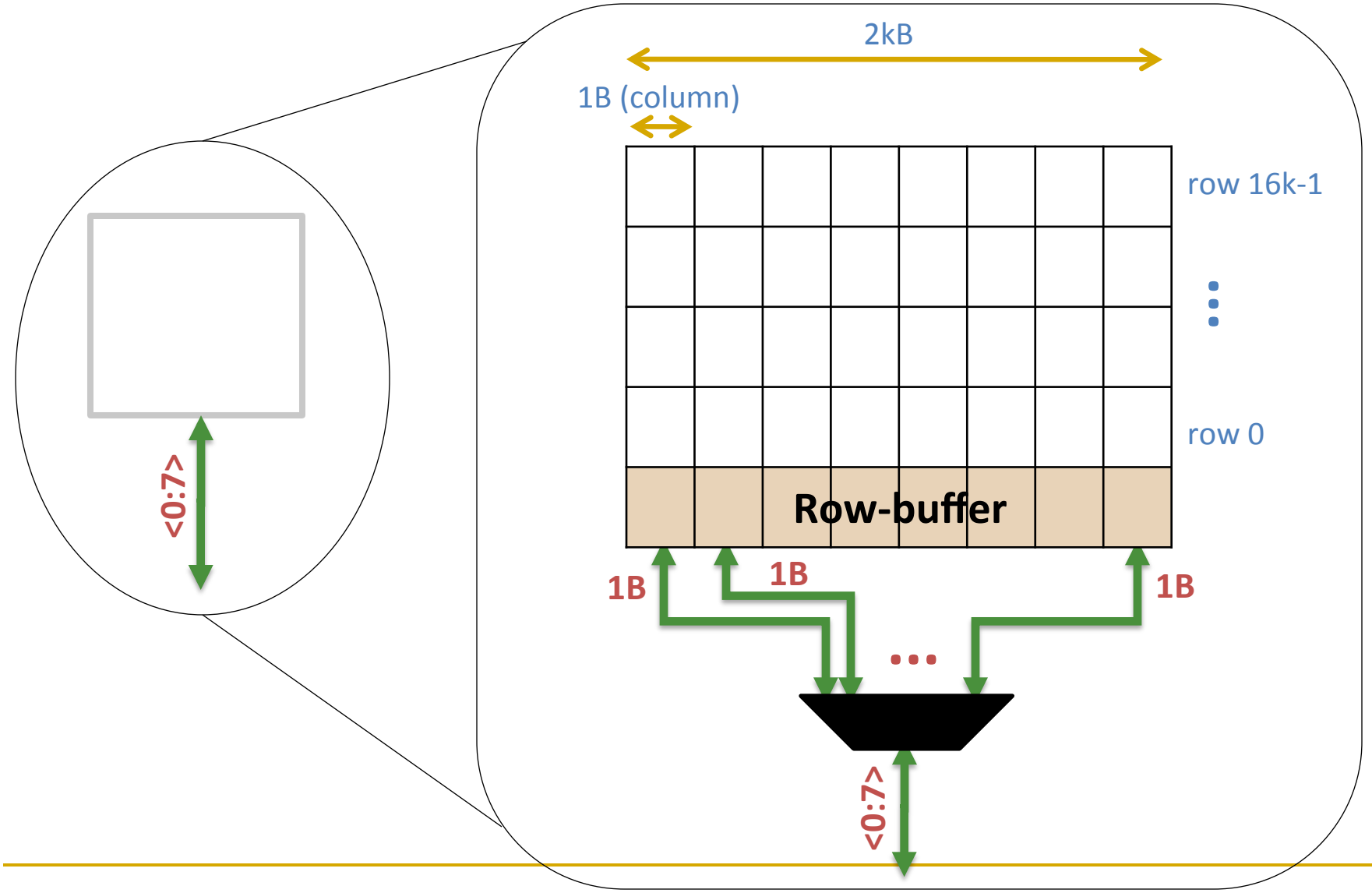
Breaking down a Rank



Breaking down a Chip

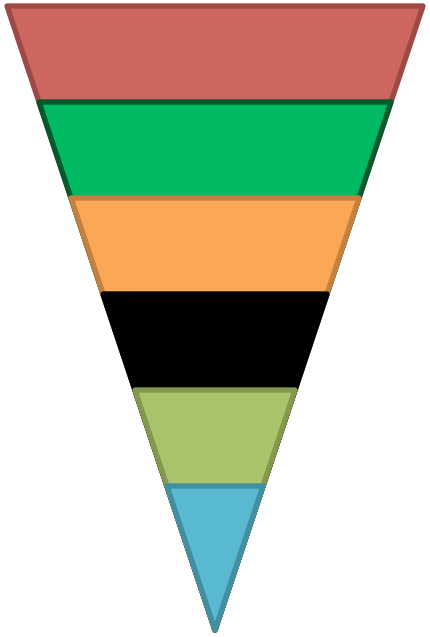


Breaking down a Bank

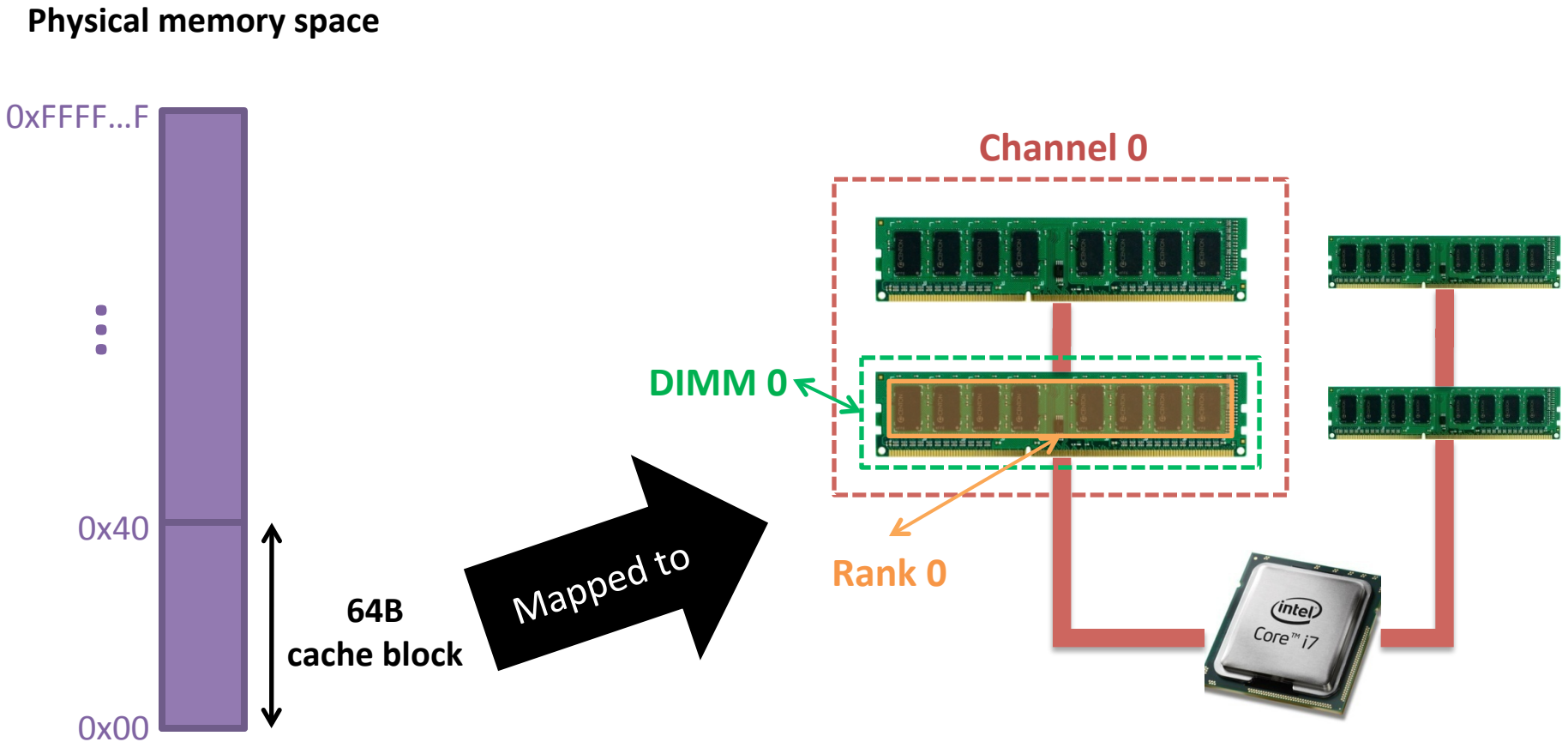


DRAM Subsystem Organization

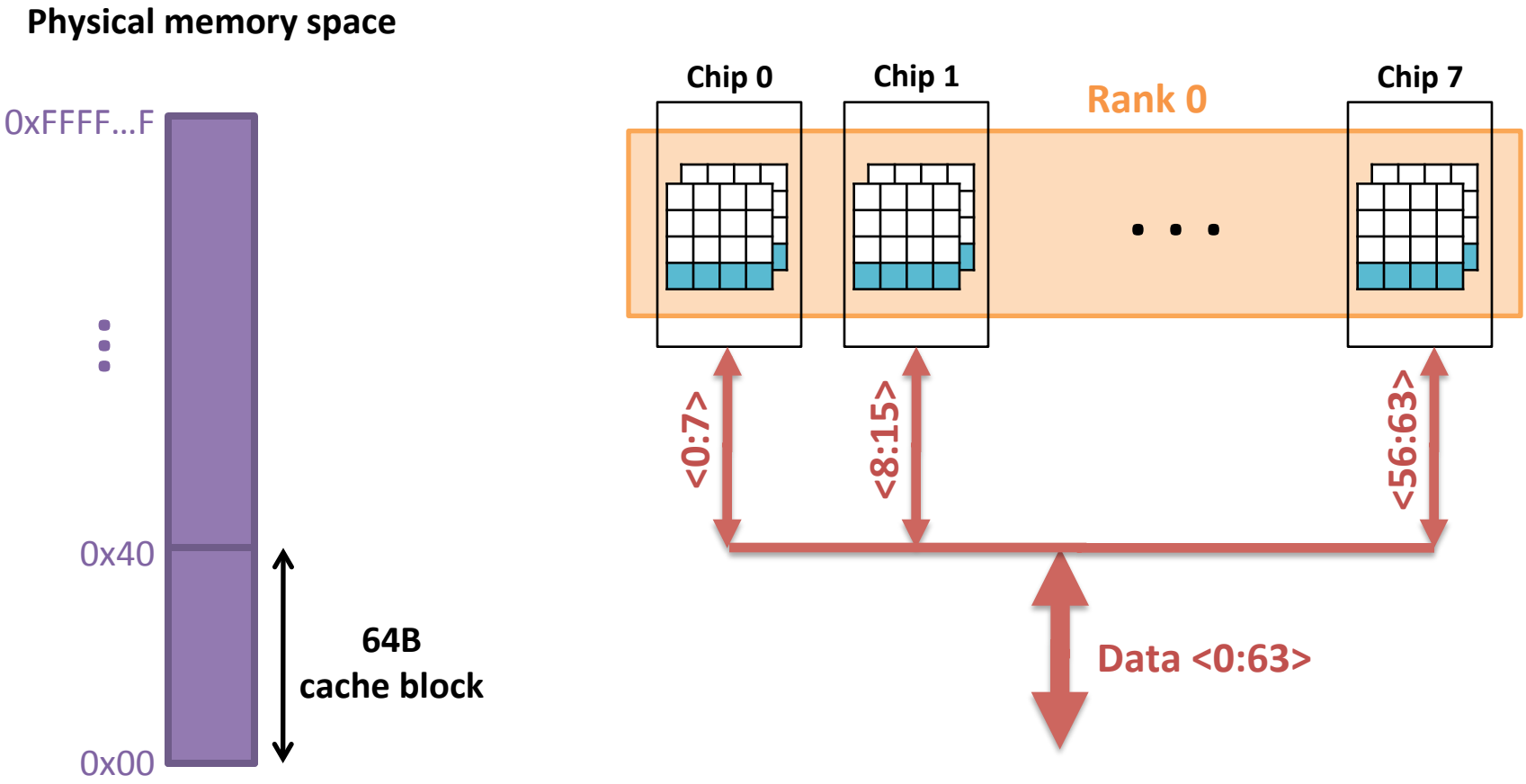
- Channel
- DIMM
- Rank
- Chip
- Bank
- Row/Column
- Cell



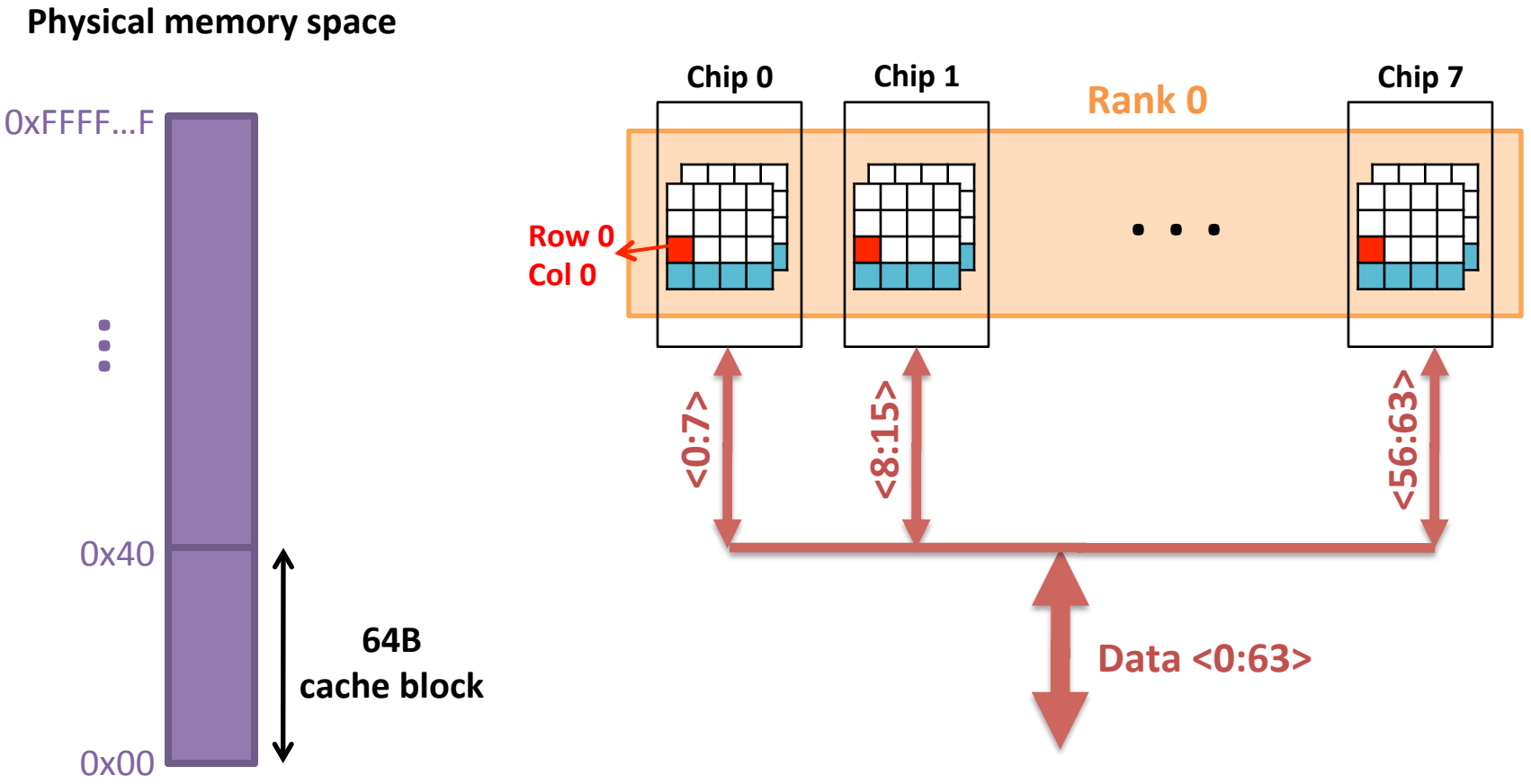
Example: Transferring a cache block



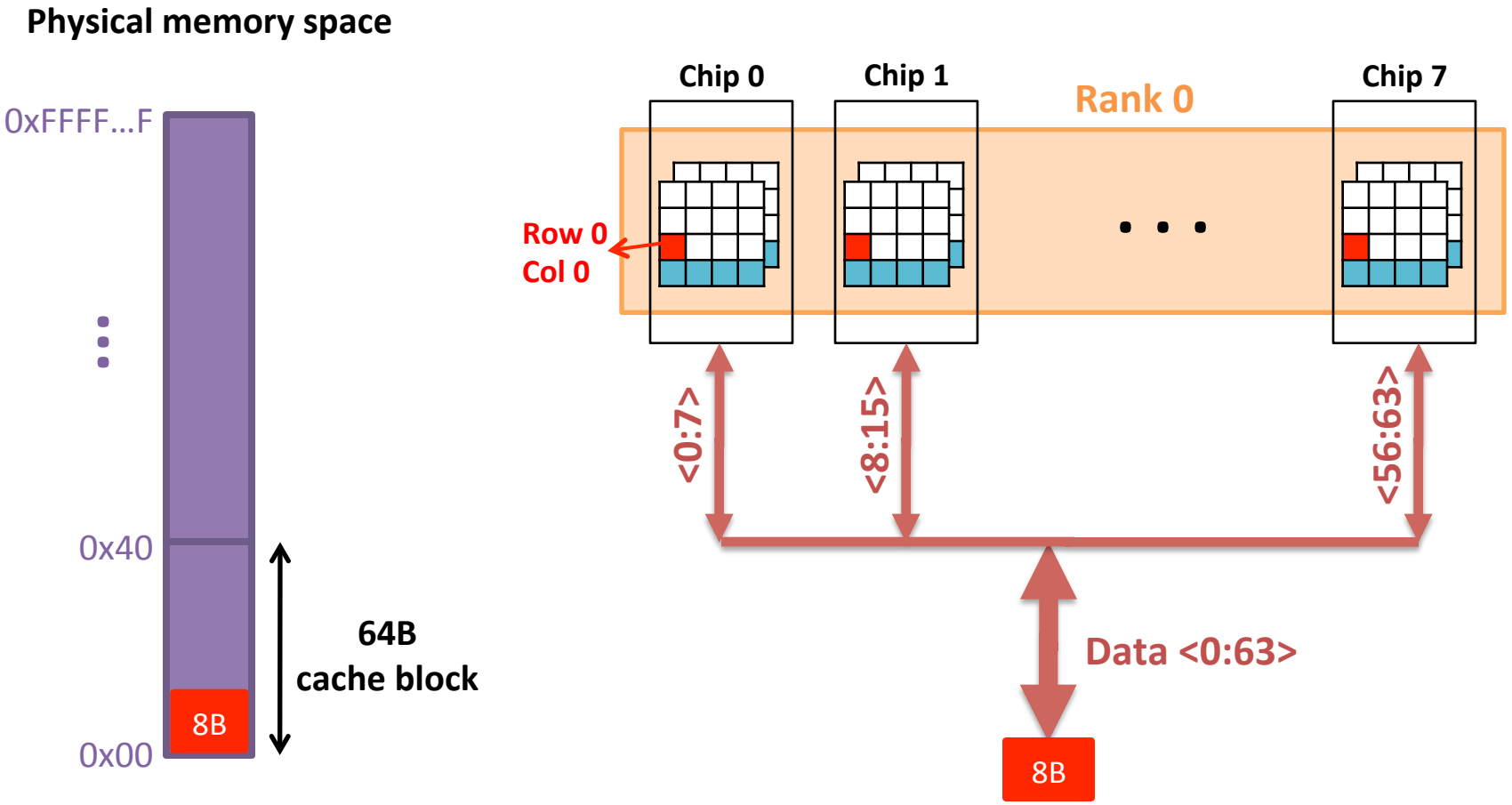
Example: Transferring a cache block



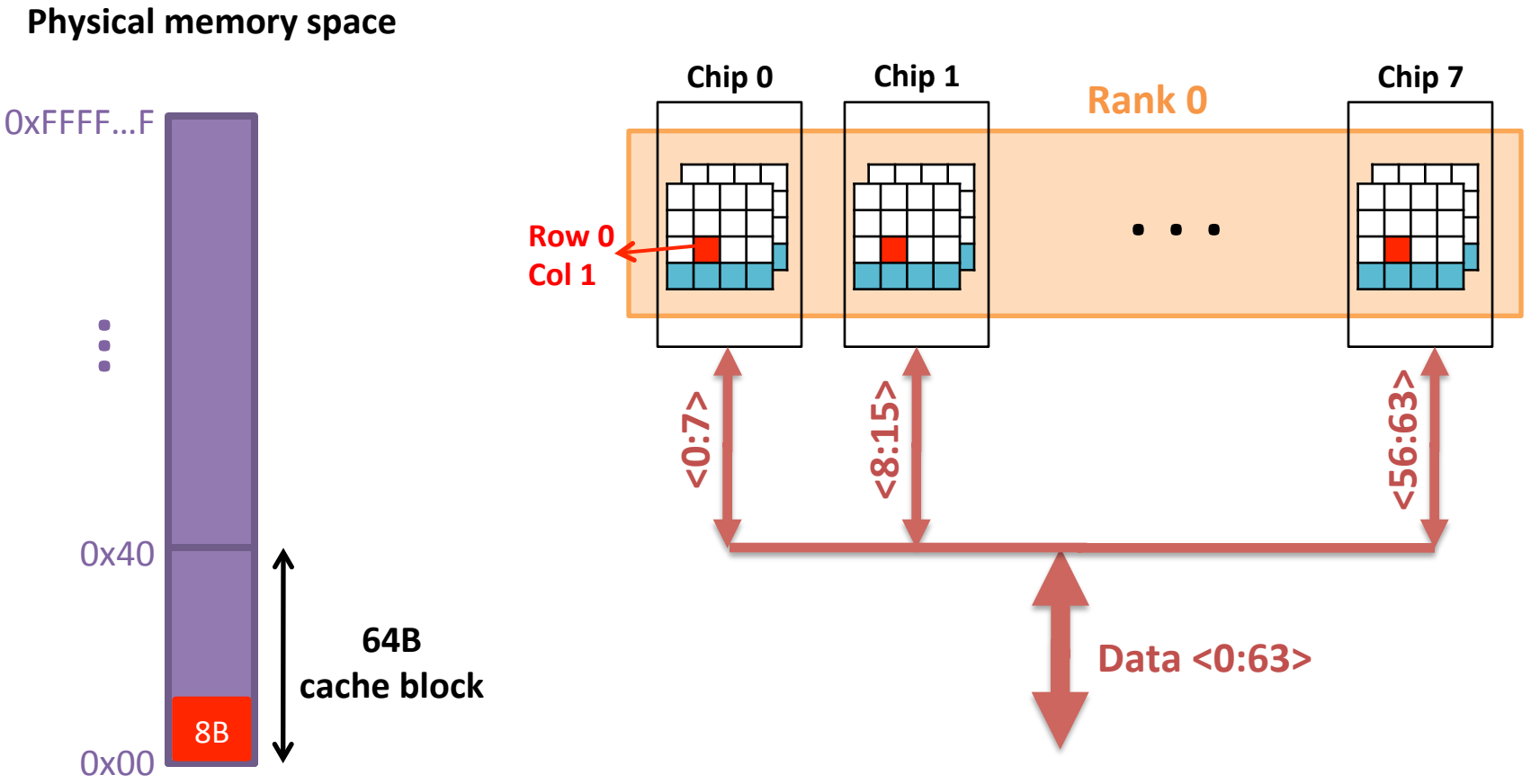
Example: Transferring a cache block



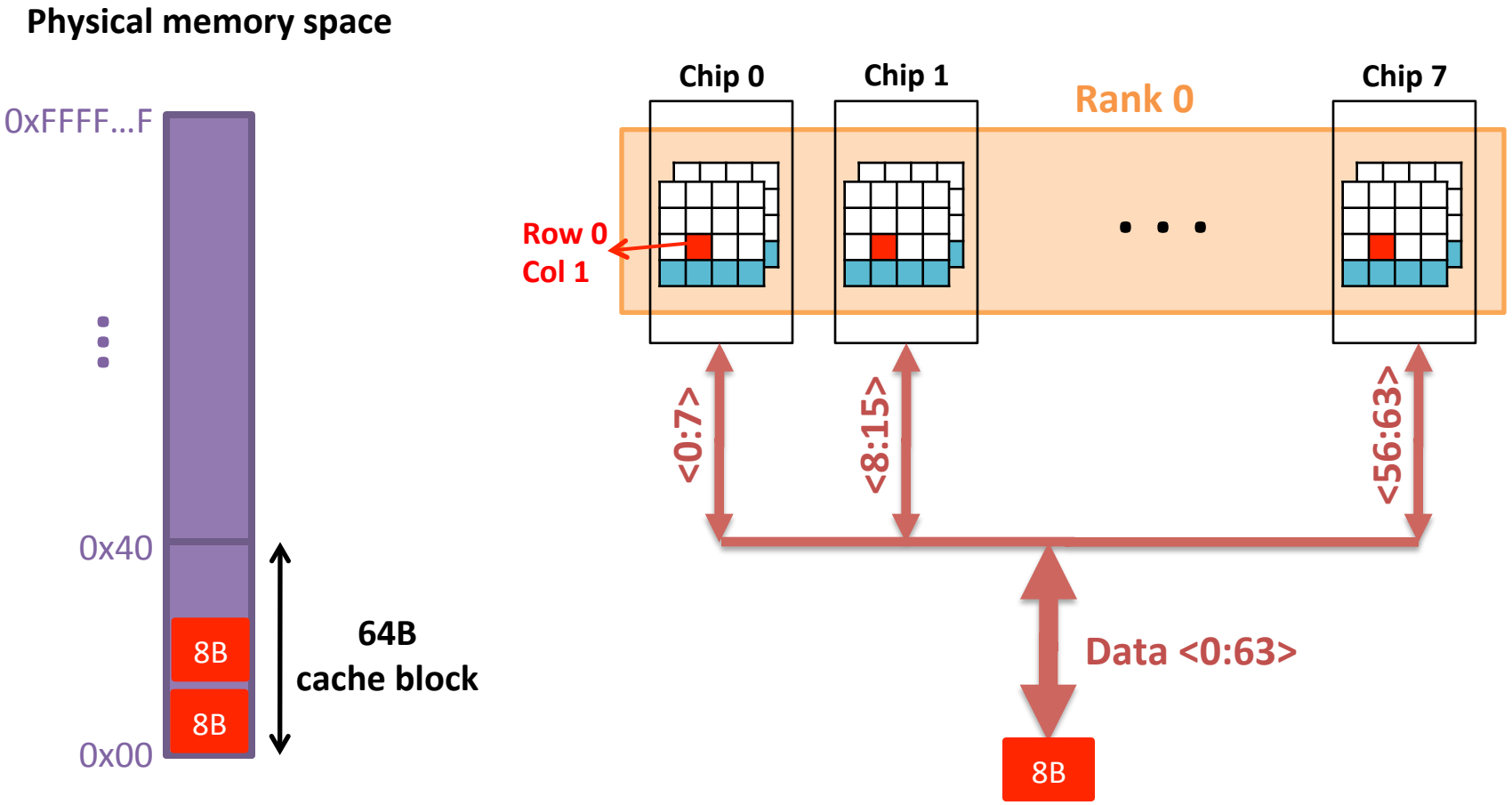
Example: Transferring a cache block



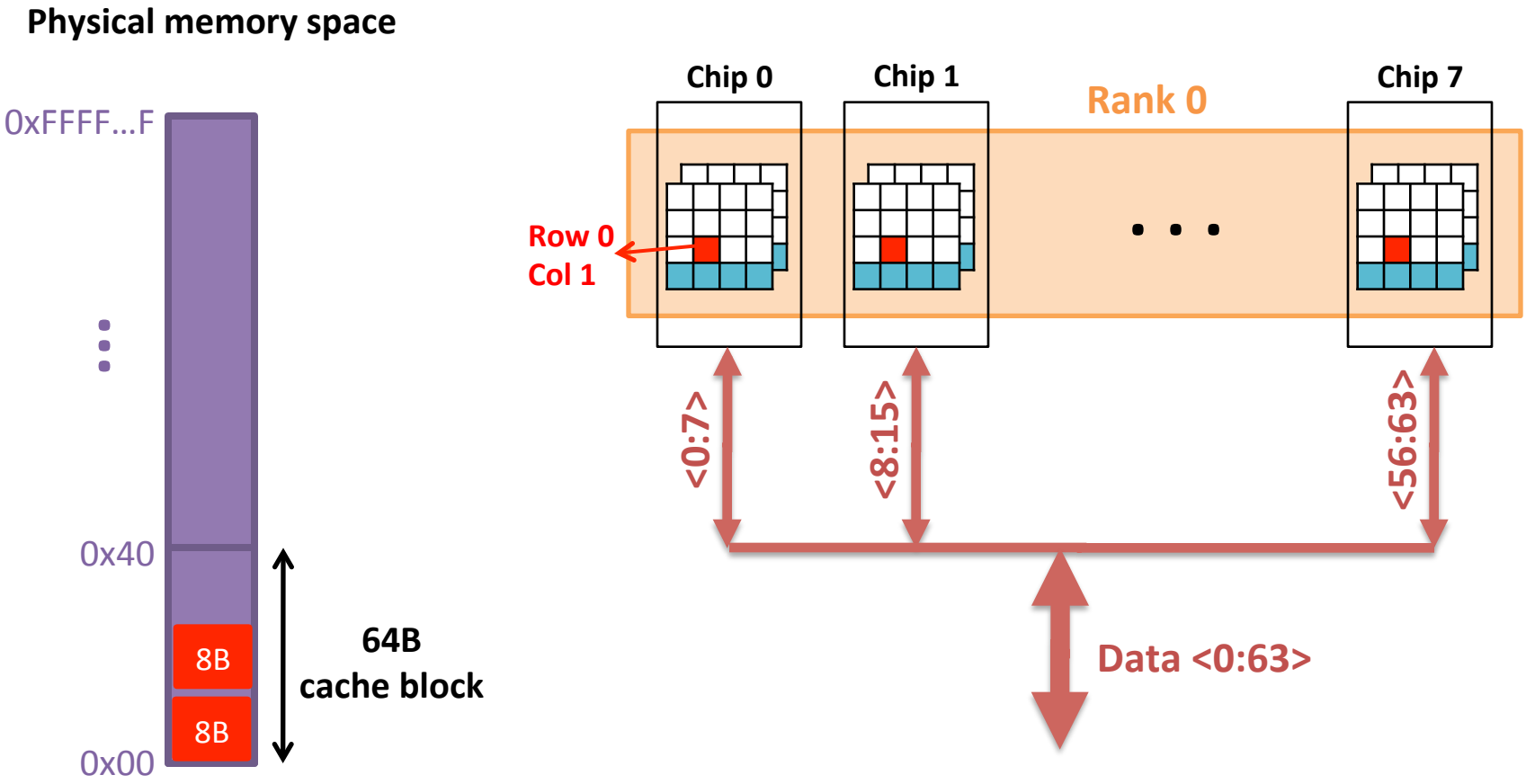
Example: Transferring a cache block



Example: Transferring a cache block



Example: Transferring a cache block



A 64B cache block takes 8 I/O cycles to transfer.

During the process, 8 columns are read sequentially.

Latency Components: Basic DRAM Operation

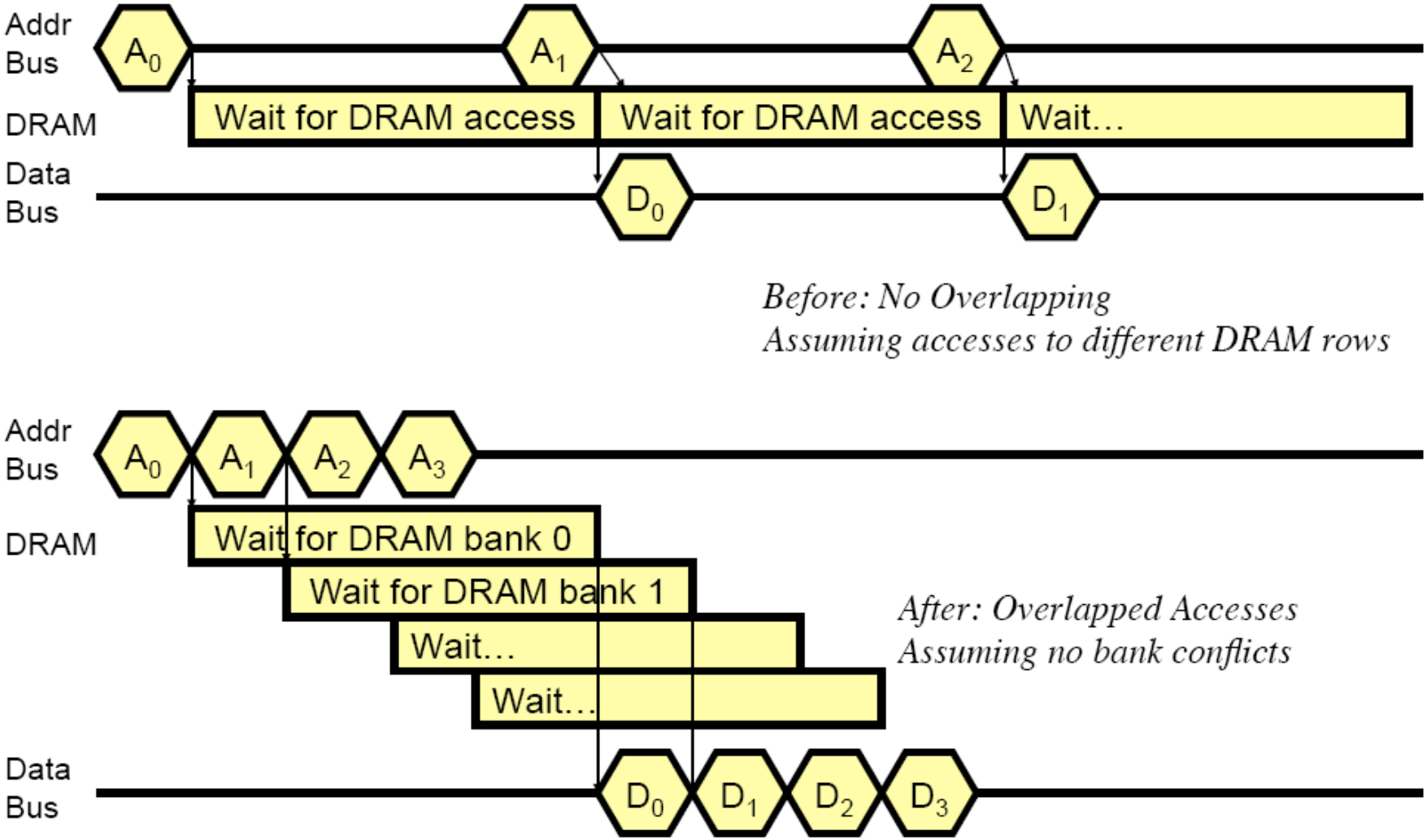
- CPU → controller transfer time
- Controller latency
  - Queuing & scheduling delay at the controller
  - Access converted to basic commands
- Controller → DRAM transfer time
- DRAM bank latency
  - Simple CAS (column address strobe) if row is "open" OR
  - RAS (row address strobe) + CAS if array precharged OR
  - PRE + RAS + CAS (worst case)
- DRAM → Controller transfer time
  - Bus latency (BL)
- Controller to CPU transfer time

Multiple Banks (Interleaving) and Channels

- Multiple banks
  - Enable concurrent DRAM accesses
  - Bits in address determine which bank an address resides in
- Multiple independent channels serve the same purpose
  - But they are even better because they have separate data buses
  - Increased bus bandwidth

- Enabling more concurrency requires reducing
  - Bank conflicts
  - Channel conflicts
- How to select/randomize bank/channel indices in address?
  - Lower order bits have more entropy
  - Randomizing hash functions (XOR of different address bits)

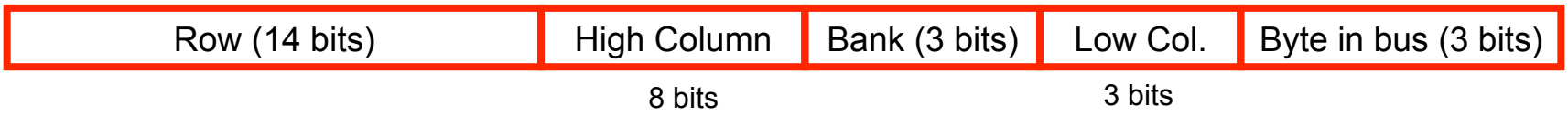
How Multiple Banks Help



Address Mapping (Single Channel)

- Single-channel system with 8-byte memory bus
  - 2GB memory, 8 banks, 16K rows & 2K columns per bank
- Row interleaving
  - Consecutive rows of memory in consecutive banks

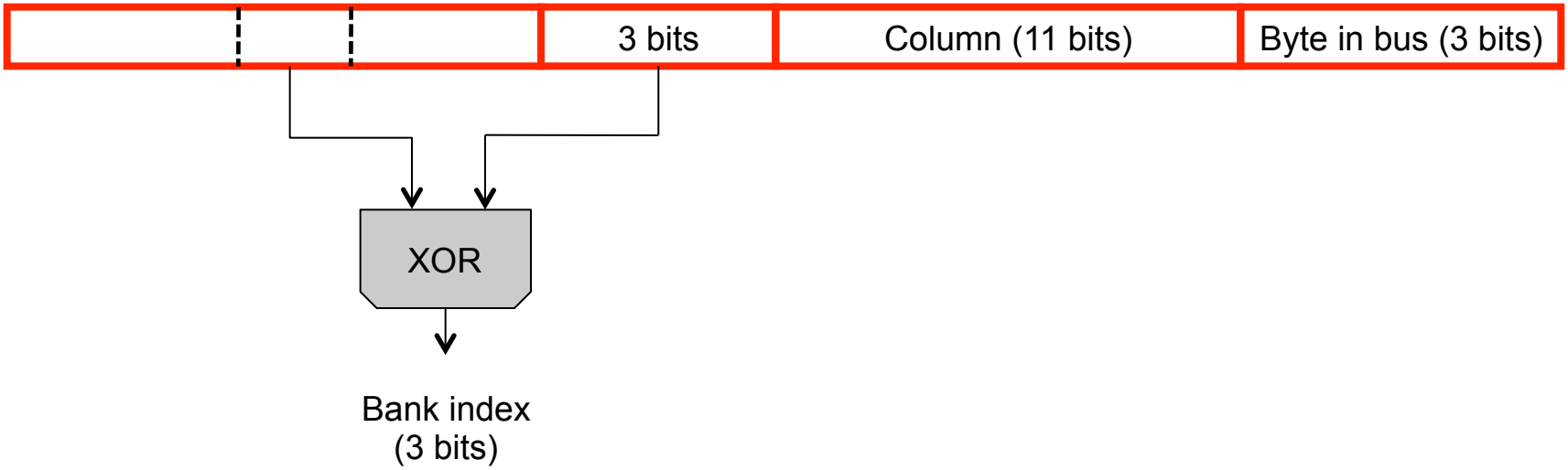
  - Accesses to consecutive cache blocks serviced in a pipelined manner
- Cache block interleaving
  - Consecutive cache block addresses in consecutive banks
  - 64 byte cache blocks



  - Accesses to consecutive cache blocks can be serviced in parallel

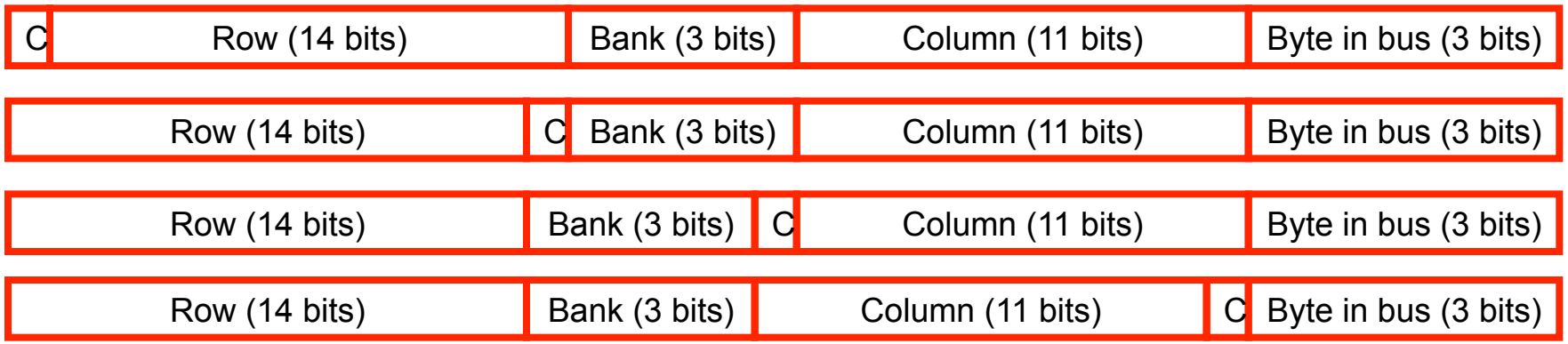
Bank Mapping Randomization

- DRAM controller can randomize the address mapping to banks so that bank conflicts are less likely

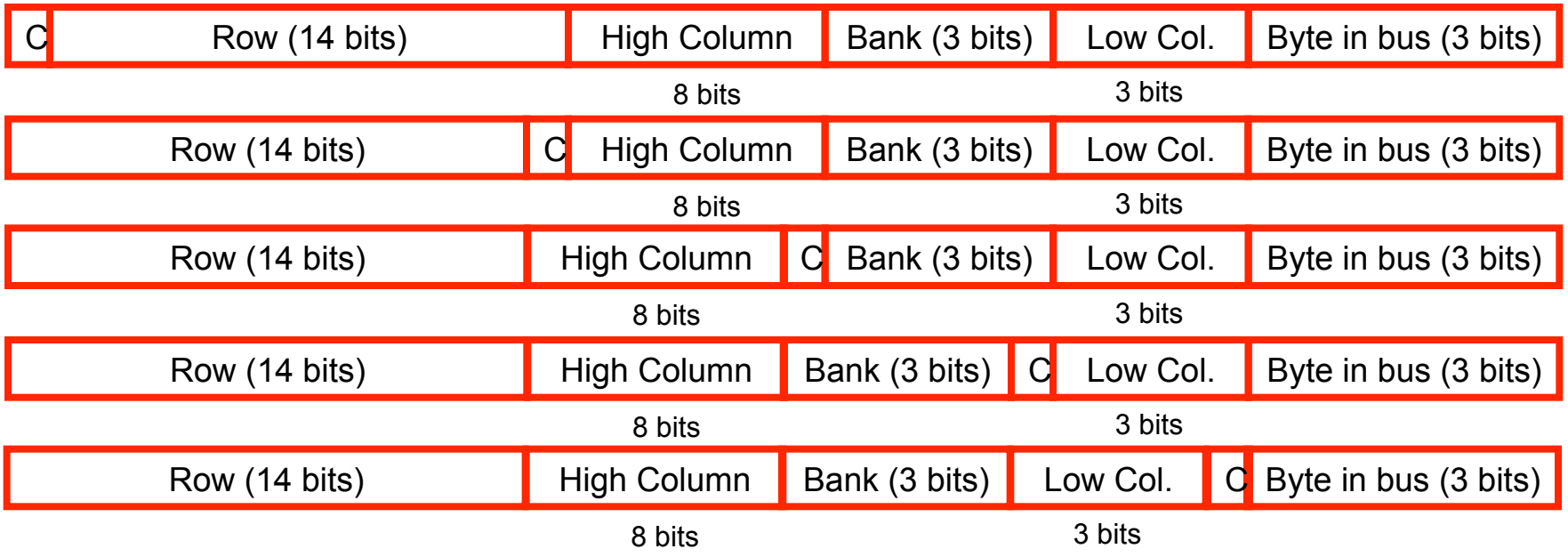


- Reading:
  - Rau, "Pseudo-randomly Interleaved Memory," ISCA 1991.

Address Mapping (Multiple Channels)

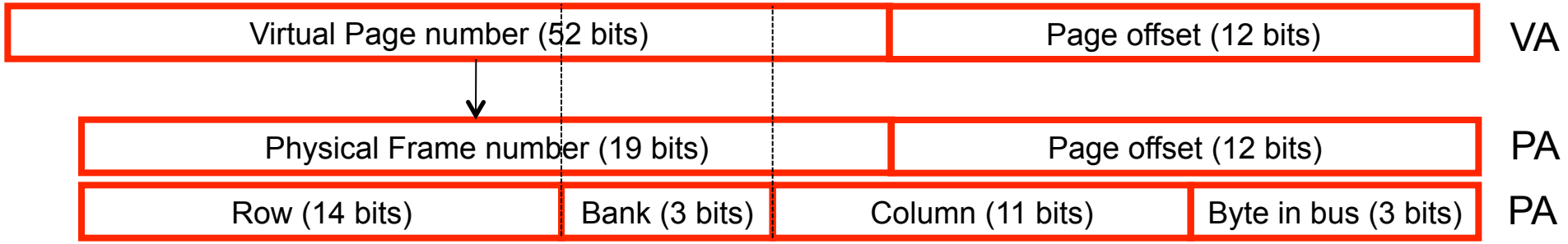


- Where are consecutive cache blocks?



Interaction with Virtual→Physical Mapping

- Operating System influences where an address maps to in DRAM



- Operating system can influence which bank/channel/rank a virtual page is mapped to.

- It can perform page coloring to
  - Minimize bank conflicts
  - Minimize inter-application interference **[Muralidhara+ MICRO'11]**
  - Minimize latency in the network **[Das+ HPCA'13]**

More on Reducing Bank Conflicts

- Read Sections 1 through 4 of:
  - Kim et al., "A Case for Exploiting Subarray-Level Parallelism in DRAM," ISCA 2012.

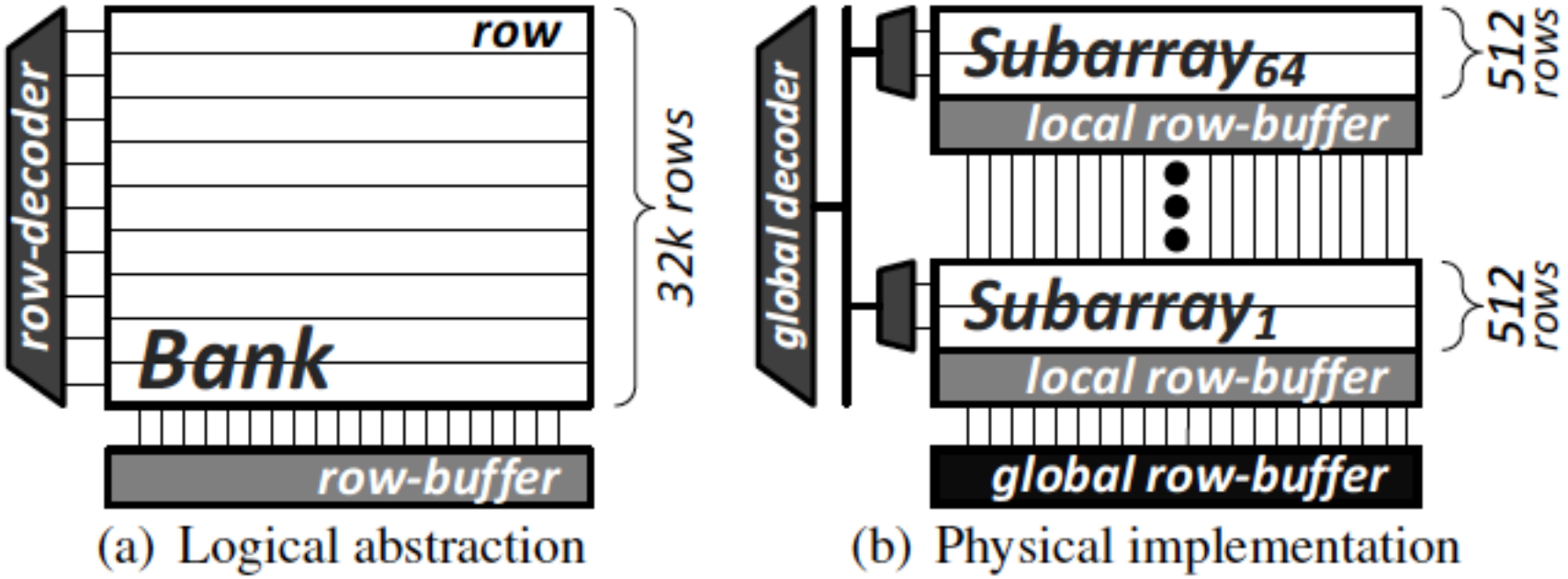
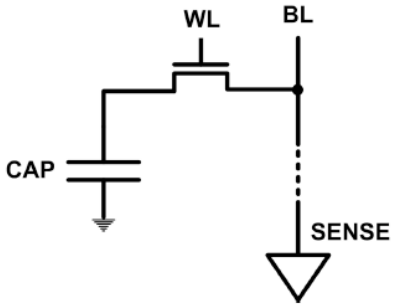


Figure 1. DRAM bank organization

DRAM Refresh (I)

- DRAM capacitor charge leaks over time
- The memory controller needs to read each row periodically to restore the charge
  - Activate + precharge each row every N ms
  - Typical N = 64 ms



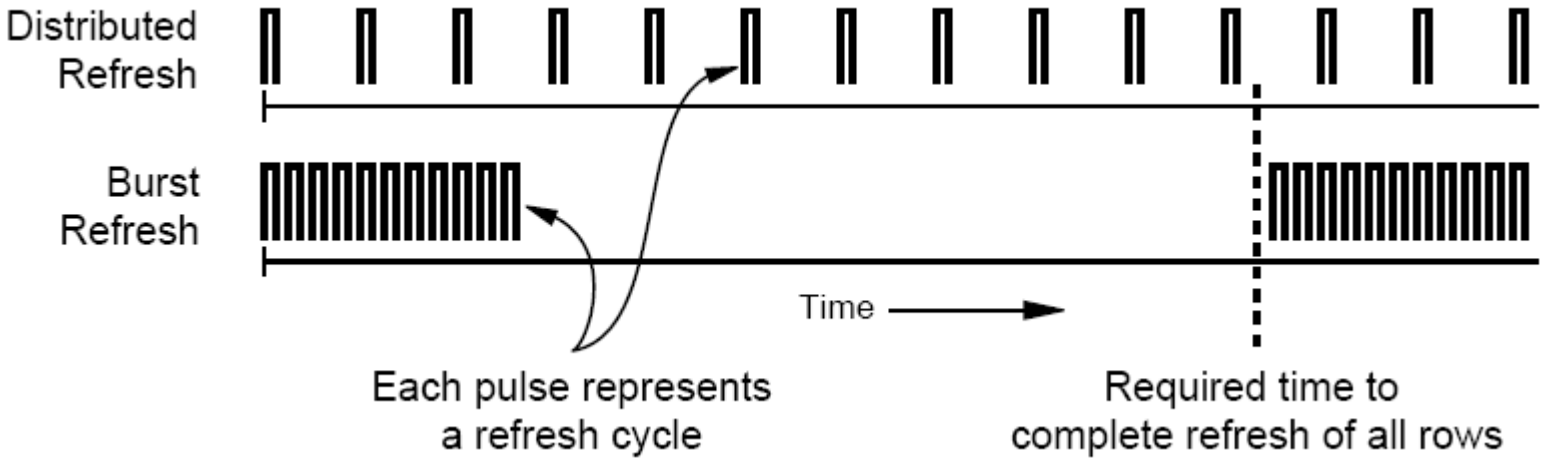
- Implications on performance?

  -- DRAM bank unavailable while refreshed

  -- Long pause times: If we refresh all rows in burst, every 64ms the DRAM will be unavailable until refresh ends

- Burst refresh: All rows refreshed immediately after one another
- Distributed refresh: Each row refreshed at a different time, at regular intervals

DRAM Refresh (II)



- Distributed refresh eliminates long pause times
- How else we can reduce the effect of refresh on performance?
  - Can we reduce the number of refreshes?

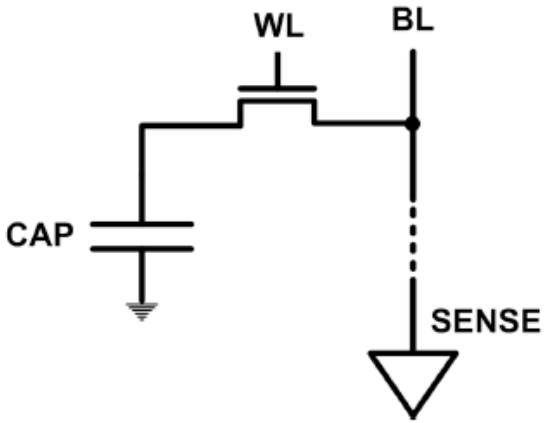
Downsides of DRAM Refresh

-- Energy consumption: Each refresh consumes energy

-- Performance degradation: DRAM rank/bank unavailable while refreshed

-- QoS/predictability impact: (Long) pause times during refresh

-- Refresh rate limits DRAM density scaling



Liu et al., "RAIDR: Retention-aware Intelligent DRAM Refresh," ISCA 2012.

Memory Controllers

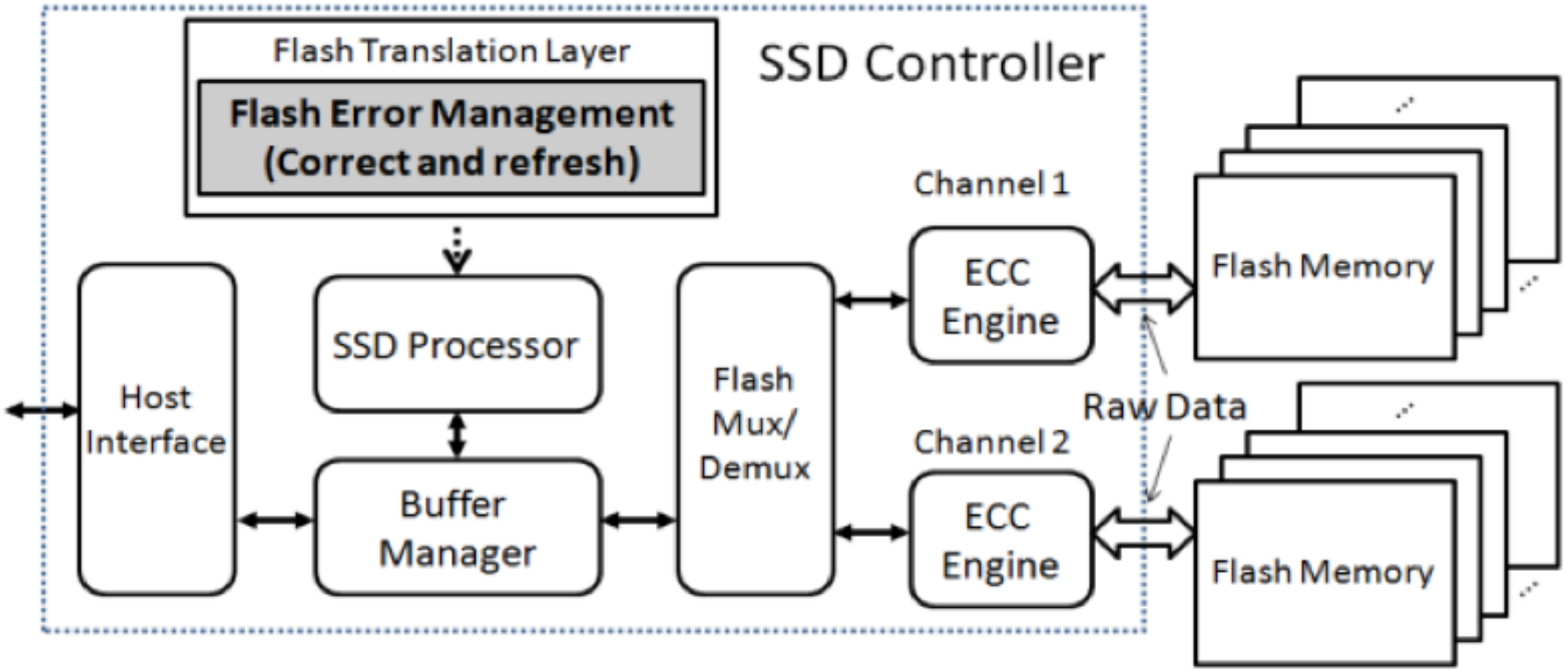
DRAM versus Other Types of Memories

- Long latency memories have similar characteristics that need to be controlled.

- The following discussion will use DRAM as an example, but many scheduling and control issues are similar in the design of controllers for other types of memories
  - Flash memory
  - Other emerging memory technologies
    - Phase Change Memory
    - Spin-Transfer Torque Magnetic Memory
  - These other technologies can place other demands on the controller

Flash Memory (SSD) Controllers

- Similar to DRAM memory controllers, except:
  - They are flash memory specific
  - They do much more: error correction, garbage collection, page remapping, …



Cai+, "Flash Correct-and-Refresh: Retention-Aware Error Management for Increased Flash Memory Lifetime", ICCD 2012.

DRAM Types

- DRAM has different types with different interfaces optimized for different purposes
  - Commodity: DDR, DDR2, DDR3, DDR4, …
  - Low power (for mobile): LPDDR1, …, LPDDR5, …
  - High bandwidth (for graphics): GDDR2, …, GDDR5, …
  - Low latency: eDRAM, RLDRAM, …
  - 3D stacked: WIO, HBM, HMC, …
  - …
- Underlying microarchitecture is fundamentally the same
- A flexible memory controller can support various DRAM types
- This complicates the memory controller
  - Difficult to support all types (and upgrades)

DRAM Types (circa 2015)

Segment	*DRAM Standards & Architectures*
Commodity	DDR3 (2007) [14]; DDR4 (2012) [18]
Low-Power	LPDDR3 (2012) [17]; LPDDR4 (2014) [20]
Graphics	GDDR5 (2009) [15]
Performance	eDRAM [28], [32]; RLDRAM3 (2011) [29]
3D-Stacked	WIO (2011) [16]; WIO2 (2014) [21]; MCDRAM (2015) [13]; HBM (2013) [19]; HMC1.0 (2013) [10]; HMC1.1 (2014) [11]
Academic	SBA/SSA (2010) [38]; Staged Reads (2012) [8]; RAIDR (2012) [27]; SALP (2012) [24]; TL-DRAM (2013) [26]; RowClone (2013) [37]; Half-DRAM (2014) [39]; Row-Buffer Decoupling (2014) [33]; SARP (2014) [6]; AL-DRAM (2015) [25]

Table 1. Landscape of DRAM-based memory

Kim et al., "Ramulator: A Fast and Extensible DRAM Simulator," IEEE Comp Arch Letters 2015.

DRAM Controller: Functions

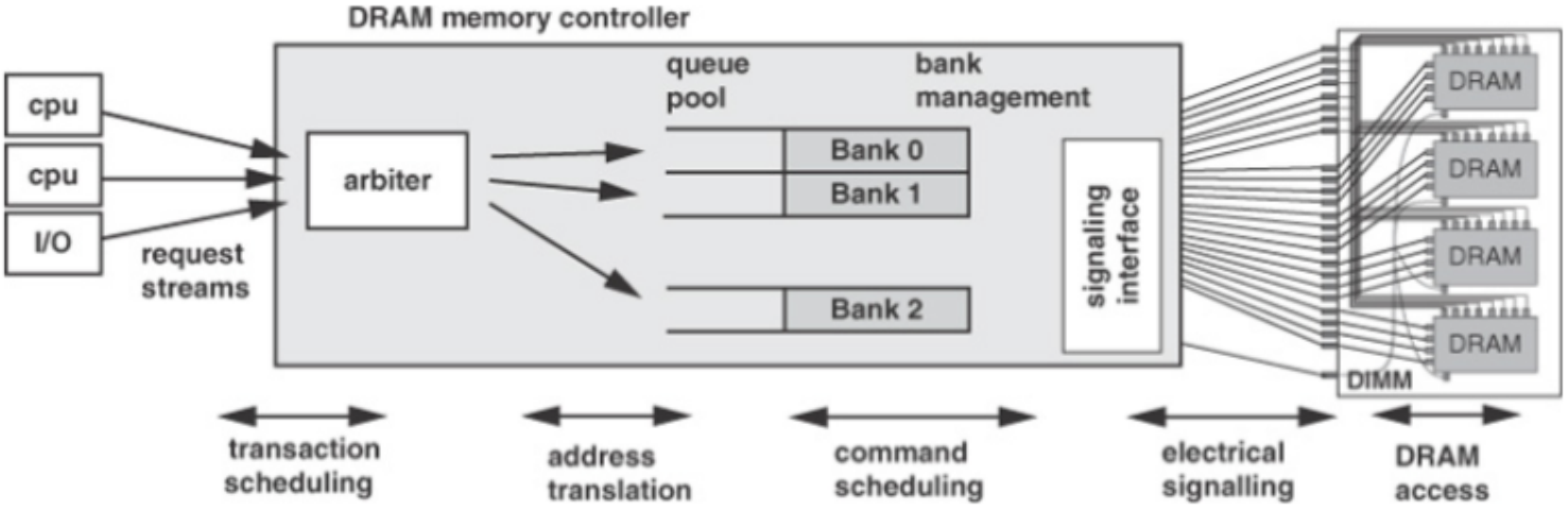
- Ensure correct operation of DRAM (refresh and timing)
- Service DRAM requests while obeying timing constraints of DRAM chips
  - Constraints: resource conflicts (bank, bus, channel), minimum write-to-read delays
  - Translate requests to DRAM command sequences
- Buffer and schedule requests to for high performance + QoS
  - Reordering, row-buffer, bank, rank, bus management
- Manage power consumption and thermals in DRAM
  - Turn on/off DRAM chips, manage power modes

DRAM Controller: Where to Place

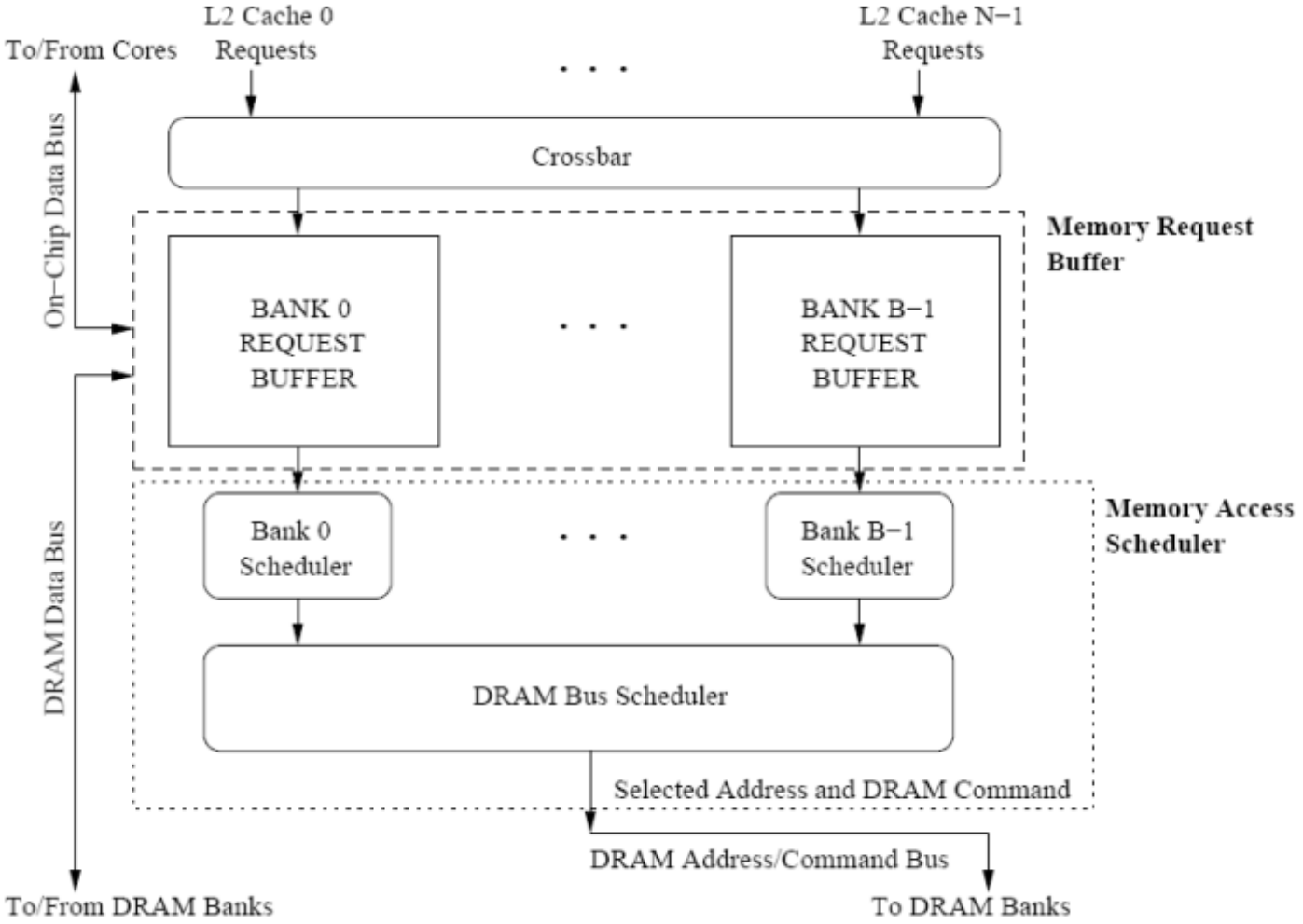
- In chipset
  - + More flexibility to plug different DRAM types into the system
  - + Less power density in the CPU chip

- On CPU chip
  - + Reduced latency for main memory access
  - + Higher bandwidth between cores and controller
    - More information can be communicated (e.g. request's importance in the processing core)

A Modern DRAM Controller (I)



A Modern DRAM Controller



DRAM Scheduling Policies (I)

- FCFS (first come first served)
  - Oldest request first

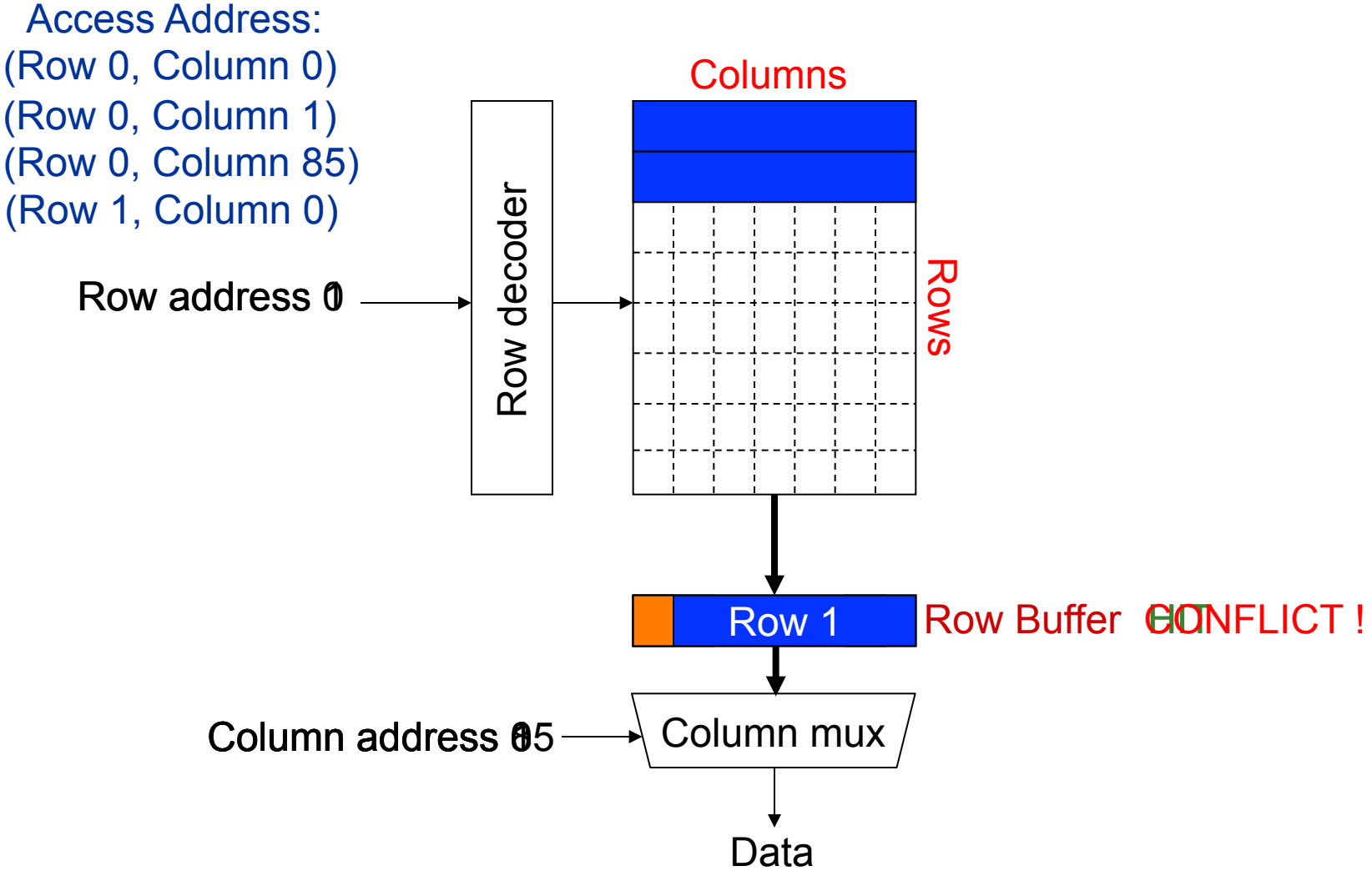
- FR-FCFS (first ready, first come first served)

  1. Row-hit first
  2. Oldest first

  Goal: Maximize row buffer hit rate → maximize DRAM throughput

  - Actually, scheduling is done at the command level
    - Column commands (read/write) prioritized over row commands (activate/precharge)
    - Within each group, older commands prioritized over younger ones

Review: DRAM Bank Operation



DRAM Scheduling Policies (II)

- A scheduling policy is a request prioritization order

- Prioritization can be based on
  - Request age
  - Row buffer hit/miss status
  - Request type (prefetch, read, write)
  - Requestor type (load miss or store miss)
  - Request criticality
    - Oldest miss in the core?
    - How many instructions in core are dependent on it?
    - Will it stall the processor?
  - Interference caused to other cores
  - ...

Row Buffer Management Policies

- Open row
  - Keep the row open after an access

  + Next access might need the same row → row hit

  -- Next access might need a different row → row conflict, wasted energy

- Closed row
  - Close the row after an access (if no other requests already in the request buffer need the same row)

  + Next access might need a different row → avoid a row conflict

  -- Next access might need the same row → extra activate latency

- Adaptive policies
  - Predict whether or not the next access to the bank will be to the same row

Open vs. Closed Row Policies

Policy	First access	Next access	Commands needed for next access
Open row	Row 0	Row 0 (row hit)	Read
Open row	Row 0	Row 1 (row conflict)	Precharge + Activate Row 1 + Read
Closed row	Row 0	Row 0 – access in request buffer (row hit)	Read
Closed row	Row 0	Row 0 – access not in request buffer (row closed)	Activate Row 0 + Read + Precharge
Closed row	Row 0	Row 1 (row closed)	Activate Row 1 + Read + Precharge

DRAM Power Management

- DRAM chips have power modes
- Idea: When not accessing a chip power it down

- Power states
  - Active (highest power)
  - All banks idle
  - Power-down
  - Self-refresh (lowest power)

- Tradeoff: State transitions incur latency during which the chip cannot be accessed

Difficulty of DRAM Control

Why are DRAM Controllers Difficult to Design?

- Need to obey DRAM timing constraints for correctness
  - There are many (50+) timing constraints in DRAM
  - tWTR: Minimum number of cycles to wait before issuing a read command after a write command is issued
  - tRC: Minimum number of cycles between the issuing of two consecutive activate commands to the same bank
  - …
- Need to keep track of many resources to prevent conflicts
  - Channels, banks, ranks, data bus, address bus, row buffers
- Need to handle DRAM refresh
- Need to manage power consumption
- Need to optimize performance & QoS (in the presence of constraints)
  - Reordering is not simple
  - Fairness and QoS needs complicates the scheduling problem

Many DRAM Timing Constraints

Latency	Symbol	DRAM cycles	Latency	Symbol	DRAM cycles
Precharge	${}^tRP$	11	Activate to read/write	${}^tRCD$	11
Read column address strobe	CL	11	Write column address strobe	CWL	8
Additive	AL	0	Activate to activate	${}^tRC$	39
Activate to precharge	${}^tRAS$	28	Read to precharge	${}^tRTP$	6
Burst length	${}^tBL$	4	Column address strobe to column address strobe	${}^tCCD$	4
Activate to activate (different bank)	${}^tRRD$	6	Four activate windows	${}^tFAW$	24
Write to read	${}^tWTR$	6	Write recovery	${}^tWR$	12

Table 4. DDR3 1600 DRAM timing specifications

- From Lee et al., "DRAM-Aware Last-Level Cache Writeback: Reducing Write-Caused Interference in Memory Systems," HPS Technical Report, April 2010.

More on DRAM Operation

- Kim et al., "A Case for Exploiting Subarray-Level Parallelism (SALP) in DRAM," ISCA 2012.
- Lee et al., "Tiered-Latency DRAM: A Low Latency and Low Cost DRAM Architecture," HPCA 2013.

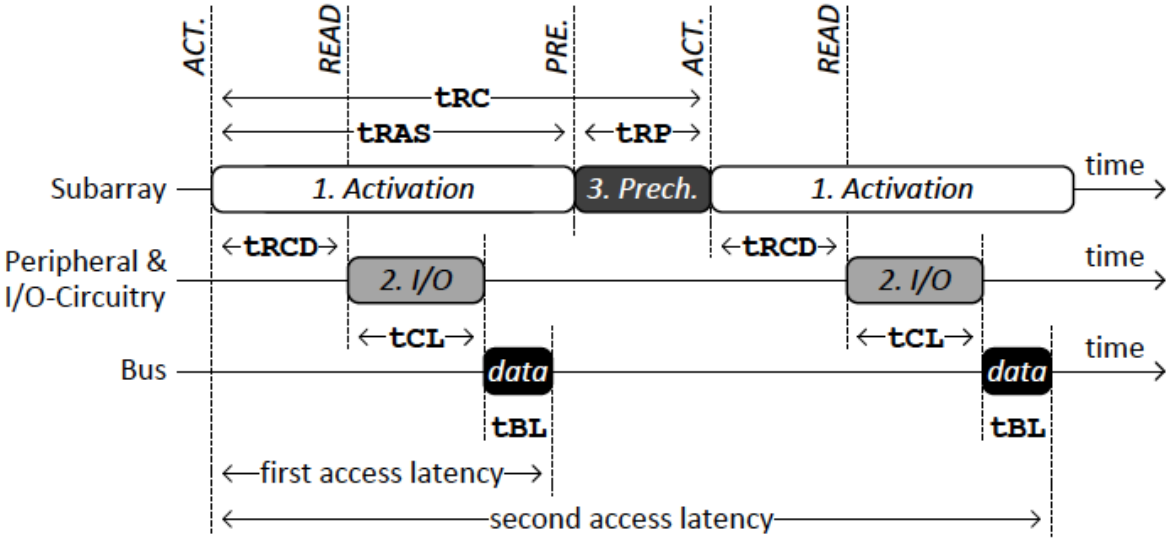
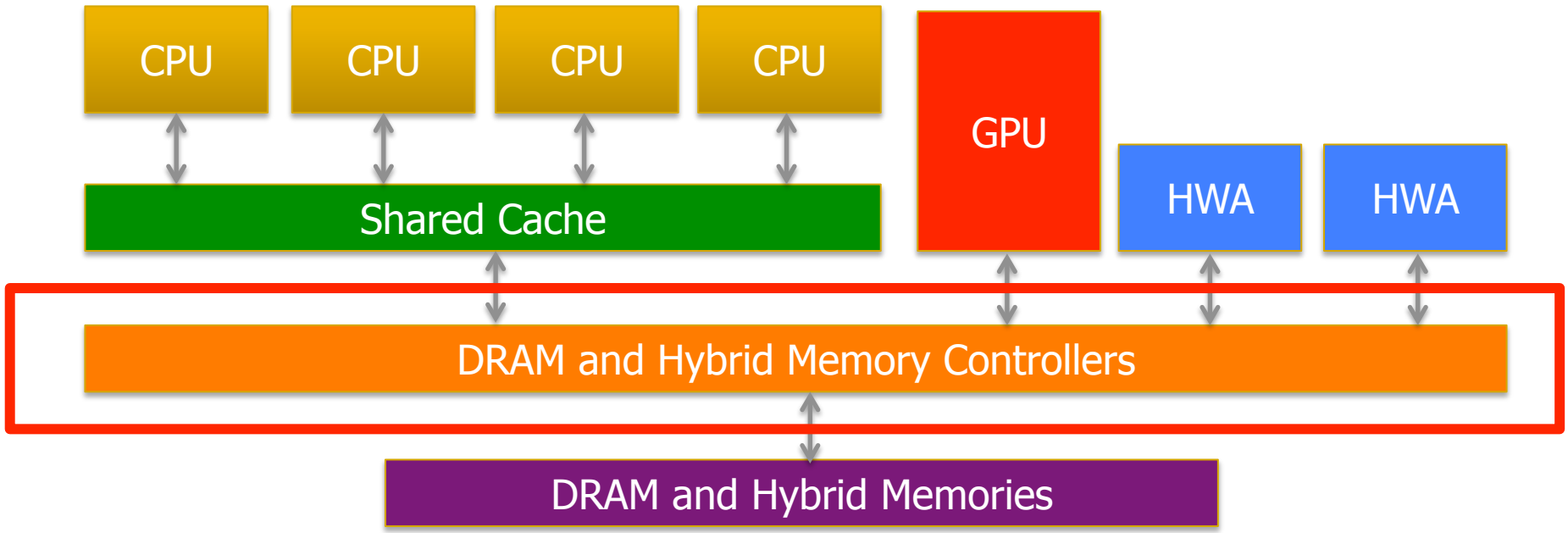


Figure 5. Three Phases of DRAM Access

Table 2. Timing Constraints (DDR3-1066) [43]

Phase	Commands	Name	Value
1	ACT → READ ACT → WRITE	tRCD	15ns
	ACT → PRE	tRAS	37.5ns
2	READ → *data* WRITE → *data*	tCL tCWL	15ns 11.25ns
	data burst	tBL	7.5ns
3	PRE → ACT	tRP	15ns
1 & 3	ACT → ACT	tRC (tRAS+tRP)	52.5ns

DRAM Controller Design Is Becoming More Difficult



- Heterogeneous agents: CPUs, GPUs, and HWAs
- Main memory interference between CPUs, GPUs, HWAs
- Many timing constraints for various memory types
- Many goals at the same time: performance, fairness, QoS, energy efficiency, …

Reality and Dream

- Reality: It difficult to optimize all these different constraints while maximizing performance, QoS, energy-efficiency, …
- Dream: Wouldn't it be nice if the DRAM controller automatically found a good scheduling policy on its own?

Self-Optimizing DRAM Controllers

- Problem: DRAM controllers difficult to design → It is difficult for human designers to design a policy that can adapt itself very well to different workloads and different system conditions

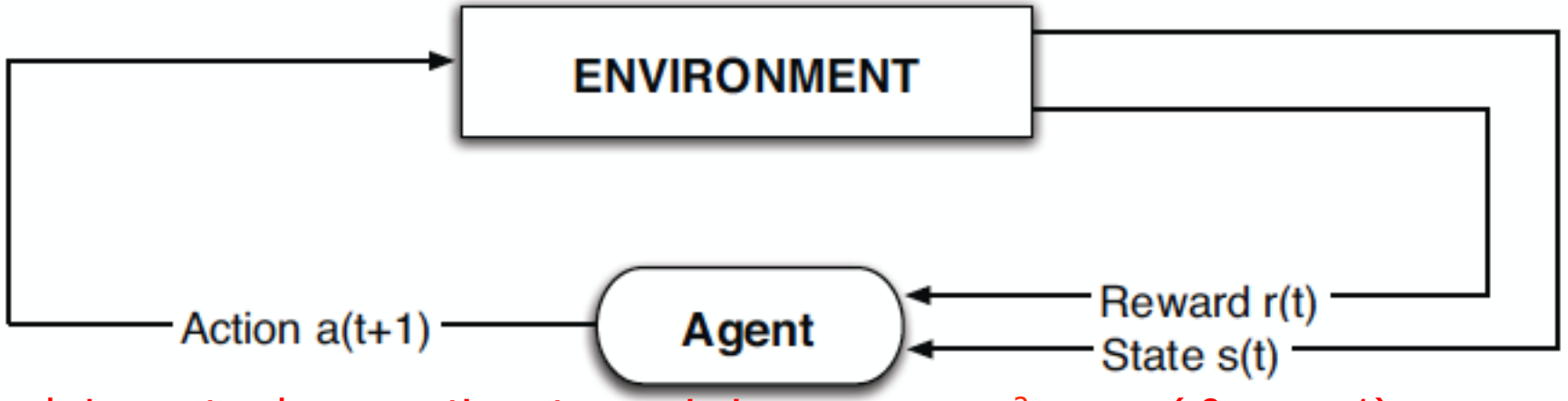
- Idea: Design a memory controller that adapts its scheduling policy decisions to workload behavior and system conditions using machine learning.

- Observation: Reinforcement learning maps nicely to memory control.

- Design: Memory controller is a reinforcement learning agent that dynamically and continuously learns and employs the best scheduling policy.

Ipek+, "Self Optimizing Memory Controllers: A Reinforcement Learning Approach," ISCA 2008.

Self-Optimizing DRAM Controllers

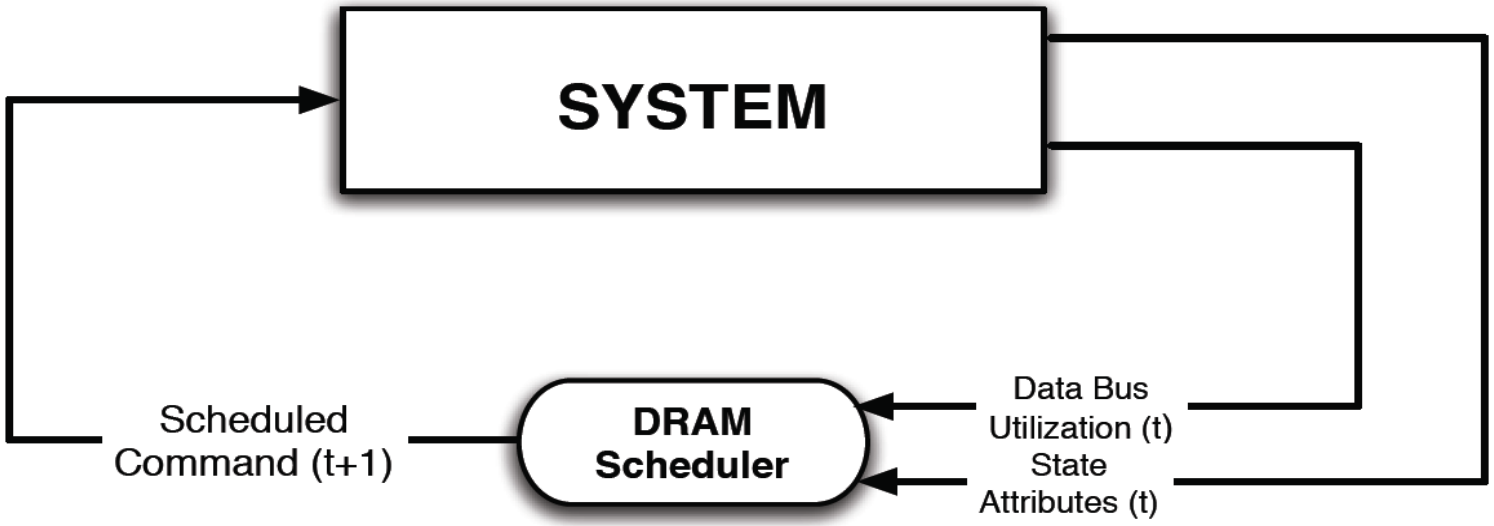


Goal: Learn to choose actions to maximize $r_0 + \gamma r_1 + \gamma^2 r_2 + \ldots$ ($0 \leq \gamma < 1$)

Figure 2: (a) Intelligent agent based on reinforcement learning principles;

Self-Optimizing DRAM Controllers

- Dynamically adapt the memory scheduling policy via interaction with the system at runtime
  - Associate system states and actions (commands) with long term reward values: each action at a given state leads to a learned reward
  - Schedule command with highest estimated long-term reward value in each state
  - Continuously update reward values for <state, action> pairs based on feedback from system



Self-Optimizing DRAM Controllers

- Engin Ipek, Onur Mutlu, José F. Martínez, and Rich Caruana, **"Self Optimizing Memory Controllers: A Reinforcement Learning Approach"**
  *Proceedings of the 35th International Symposium on Computer Architecture (**ISCA**)*, pages 39-50, Beijing, China, June 2008.

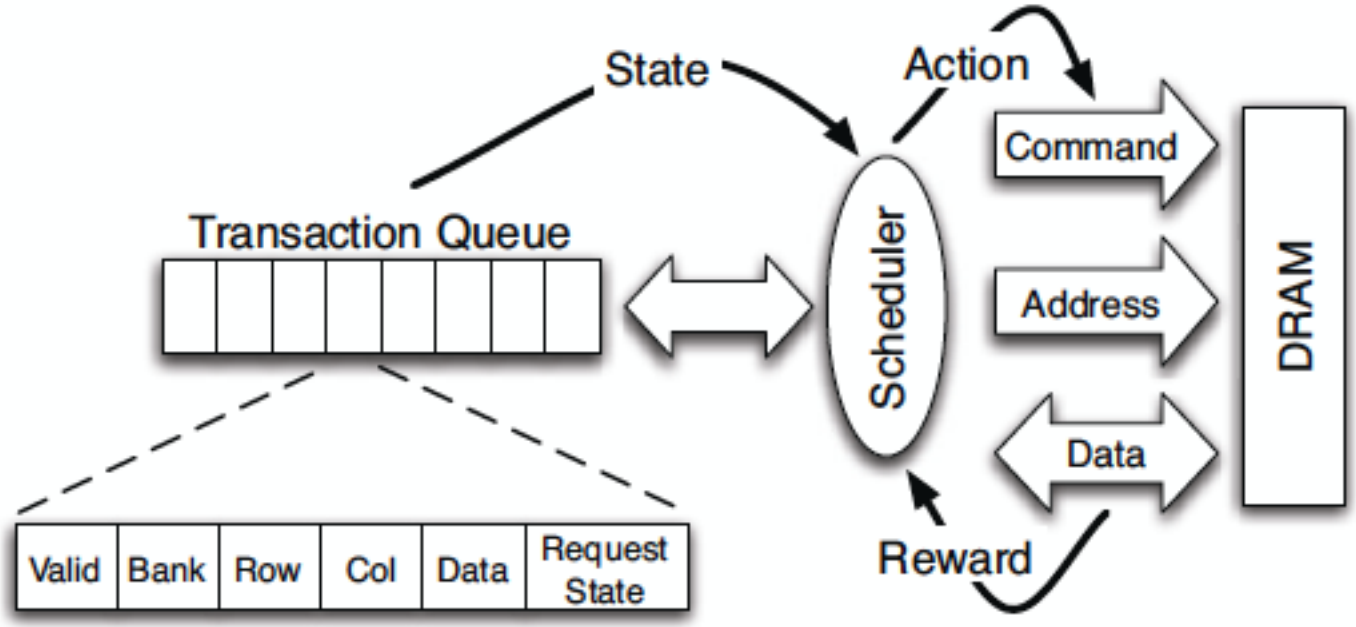


Figure 4: High-level overview of an RL-based scheduler.

States, Actions, Rewards

- Reward function
  - +1 for scheduling Read and Write commands
  - 0 at all other times

  Goal is to maximize data bus utilization
- State attributes
  - Number of reads, writes, and load misses in transaction queue
  - Number of pending writes and ROB heads waiting for referenced row
  - Request's relative ROB order
- Actions
  - Activate
  - Write
  - Read - load miss
  - Read - store miss
  - Precharge - pending
  - Precharge - preemptive
  - NOP

Performance Results

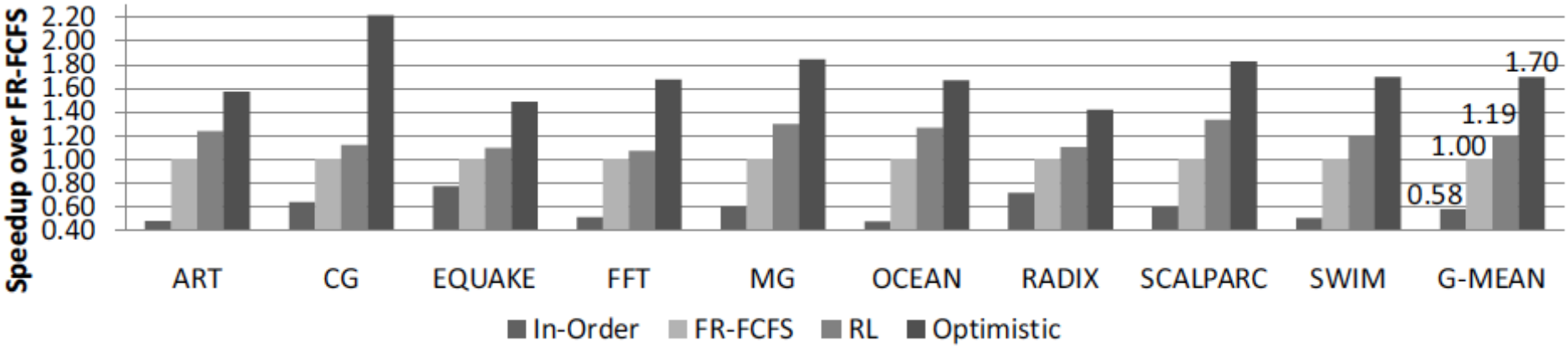


Figure 7: Performance comparison of in-order, FR-FCFS, RL-based, and optimistic memory controllers

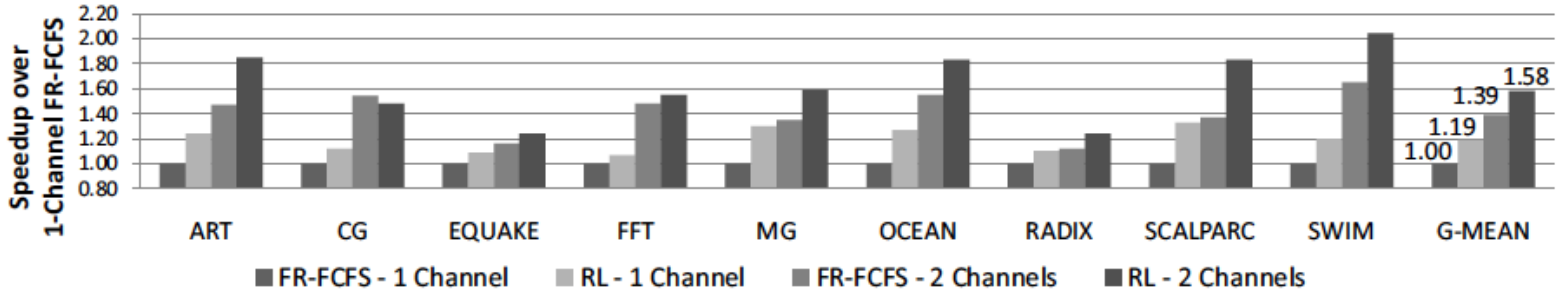


Figure 15: Performance comparison of FR-FCFS and RL-based memory controllers on systems with 6.4GB/s and 12.8GB/s peak DRAM bandwidth

Self Optimizing DRAM Controllers

- Advantages

  + Adapts the scheduling policy dynamically to changing workload behavior and to maximize a long-term target

  + Reduces the designer's burden in finding a good scheduling policy. Designer specifies:

    1) What system variables might be useful

    2) What target to optimize, but not how to optimize it

- Disadvantages and Limitations

  -- Black box: designer much less likely to implement what she cannot easily reason about

  -- How to specify different reward functions that can achieve different objectives? (e.g., fairness, QoS)

  -- Hardware complexity?

More on Self-Optimizing DRAM Controllers

- Engin Ipek, Onur Mutlu, José F. Martínez, and Rich Caruana, **"Self Optimizing Memory Controllers: A Reinforcement Learning Approach"**
  *Proceedings of the 35th International Symposium on Computer Architecture (**ISCA**)*, pages 39-50, Beijing, China, June 2008.

Self-Optimizing Memory Controllers: A Reinforcement Learning Approach

Engin İpek[1,2] **Onur Mutlu**[2] **José F. Martínez**[1] **Rich Caruana**[1]

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Evaluating New Ideas for New (Memory) Architectures

Simulation: The Field of Dreams

Dreaming and Reality

- An architect is in part a dreamer, a creator
- Simulation is a key tool of the architect
- Simulation enables
  - The exploration of many dreams
  - A reality check of the dreams
  - Deciding which dream is better
- Simulation also enables
  - The ability to fool yourself with false dreams

Why High-Level Simulation?

- Problem: RTL simulation is intractable for design space exploration → too time consuming to design and evaluate
  - Especially over a large number of workloads
  - Especially if you want to predict the performance of a good chunk of a workload on a particular design
  - Especially if you want to consider many design choices
    - Cache size, associativity, block size, algorithms
    - Memory control and scheduling algorithms
    - In-order vs. out-of-order execution
    - Reservation station sizes, ld/st queue size, register file size, …
    - …
- Goal: Explore design choices quickly to see their impact on the workloads we are designing the platform for

Different Goals in Simulation

- Explore the design space quickly and see what you want to
  - potentially implement in a next-generation platform
  - propose as the next big idea to advance the state of the art
  - the goal is mainly to see relative effects of design decisions
- Match the behavior of an existing system so that you can
  - debug and verify it at cycle-level accuracy
  - propose small tweaks to the design that can make a difference in performance or energy
  - the goal is very high accuracy
- Other goals in-between:
  - Refine the explored design space without going into a full detailed, cycle-accurate design
  - Gain confidence in your design decisions made by higher-level design space exploration

Tradeoffs in Simulation

- Three metrics to evaluate a simulator
  - Speed
  - Flexibility
  - Accuracy

- Speed: How fast the simulator runs (xIPS, xCPS)
- Flexibility: How quickly one can modify the simulator to evaluate different algorithms and design choices?
- Accuracy: How accurate the performance (energy) numbers the simulator generates are vs. a real design (Simulation error)

- The relative importance of these metrics varies depending on where you are in the design process

Trading Off Speed, Flexibility, Accuracy

- Speed & flexibility affect:
  - How quickly you can make design tradeoffs
- Accuracy affects:
  - How good your design tradeoffs may end up being
  - How fast you can build your simulator (simulator design time)
- Flexibility also affects:
  - How much human effort you need to spend modifying the simulator
- You can trade off between the three to achieve design exploration and decision goals

High-Level Simulation

- Key Idea: Raise the abstraction level of modeling to give up some accuracy to enable speed & flexibility (and quick simulator design)

- Advantage

  + Can still make the right tradeoffs, and can do it quickly

    + All you need is modeling the key high-level factors, you can omit corner case conditions

    + All you need is to get the "relative trends" accurately, not exact performance numbers

- Disadvantage

  -- Opens up the possibility of potentially wrong decisions

    -- How do you ensure you get the "relative trends" accurately?

Simulation as Progressive Refinement

- High-level models (Abstract, C)
- …
- Medium-level models (Less abstract)
- …
- Low-level models (RTL with eveything modeled)
- …
- Real design

- As you refine (go down the above list)
  - Abstraction level reduces
  - Accuracy (hopefully) increases (not necessarily, if not careful)
  - Speed and flexibility reduce
  - You can loop back and fix higher-level models

Making The Best of Architecture

- A good architect is comfortable at all levels of refinement
  - Including the extremes

- A good architect knows when to use what type of simulation

Ramulator: A Fast and Extensible DRAM Simulator

[IEEE Comp Arch Letters'15]

Ramulator Motivation

- DRAM and Memory Controller landscape is changing
- Many new and upcoming standards
- Many new controller designs
- A fast and easy-to-extend simulator is very much needed

Segment	*DRAM Standards & Architectures*
Commodity	DDR3 (2007) [14]; DDR4 (2012) [18]
Low-Power	LPDDR3 (2012) [17]; LPDDR4 (2014) [20]
Graphics	GDDR5 (2009) [15]
Performance	eDRAM [28], [32]; RLDRAM3 (2011) [29]
3D-Stacked	WIO (2011) [16]; WIO2 (2014) [21]; MCDRAM (2015) [13]; HBM (2013) [19]; HMC1.0 (2013) [10]; HMC1.1 (2014) [11]
Academic	SBA/SSA (2010) [38]; Staged Reads (2012) [8]; RAIDR (2012) [27]; SALP (2012) [24]; TL-DRAM (2013) [26]; RowClone (2013) [37]; Half-DRAM (2014) [39]; Row-Buffer Decoupling (2014) [33]; SARP (2014) [6]; AL-DRAM (2015) [25]

Table 1. Landscape of DRAM-based memory

Ramulator

- Provides out-of-the box support for many DRAM standards:
  - DDR3/4, LPDDR3/4, GDDR5, WIO1/2, HBM, plus new proposals (SALP, AL-DRAM, TLDRAM, RowClone, and SARP)
- ~2.5X faster than fastest open-source simulator
- Modular and extensible to different standards

Simulator (clang -O3)	*Cycles (10^6)*		*Runtime (sec.)*		*Req/sec (10^3)*		*Memory (MB)*
	Random	*Stream*	*Random*	*Stream*	*Random*	*Stream*	
Ramulator	652	411	752	249	133	402	2.1
DRAMSim2	645	413	2,030	876	49	114	1.2
USIMM	661	409	1,880	750	53	133	4.5
DrSim	647	406	18,109	12,984	6	8	1.6
NVMain	666	413	6,881	5,023	15	20	4,230.0

Table 3. Comparison of five simulators using two traces

Case Study: Comparison of DRAM Standards

Standard	*Rate (MT/s)*	*Timing (CL-RCD-RP)*	*Data-Bus (Width×Chan.)*	*Rank-per-Chan*	*BW (GB/s)*
DDR3	1,600	11-11-11	64-bit × 1	1	11.9
DDR4	2,400	16-16-16	64-bit × 1	1	17.9
SALP†	1,600	11-11-11	64-bit × 1	1	11.9
LPDDR3	1,600	12-15-15	64-bit × 1	1	11.9
LPDDR4	2,400	22-22-22	32-bit × 2*	1	17.9
GDDR5 [12]	6,000	18-18-18	64-bit × 1	1	44.7
HBM	1,000	7-7-7	128-bit × 8*	1	119.2
WIO	266	7-7-7	128-bit × 4*	1	15.9
WIO2	1,066	9-10-10	128-bit × 8*	1	127.2

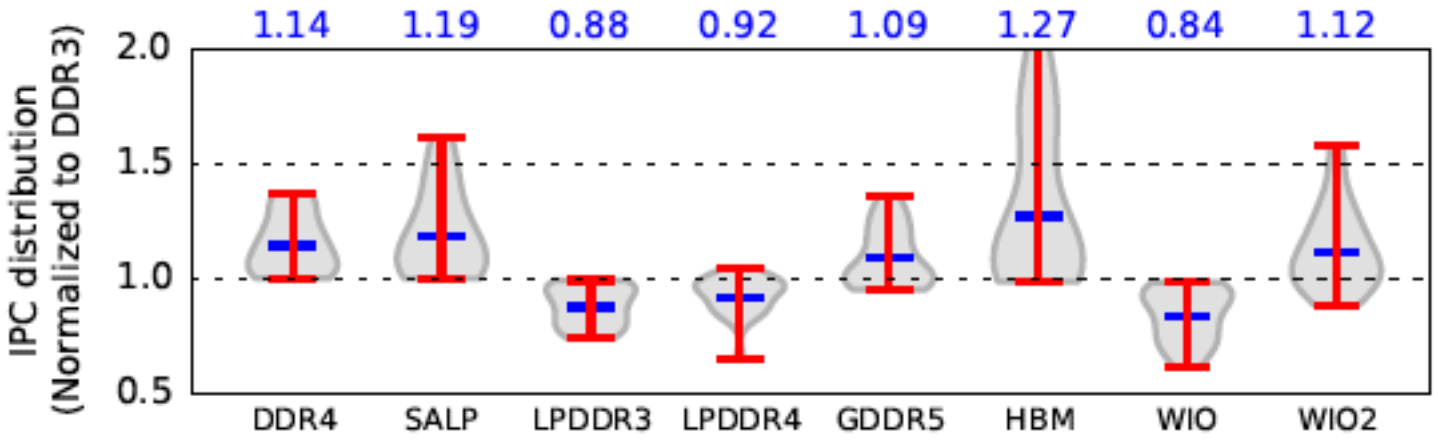

Figure 2. Performance comparison of DRAM standards

Across 22 workloads, simple CPU model

Ramulator Paper and Source Code

- Yoongu Kim, Weikun Yang, and Onur Mutlu,
  "Ramulator: A Fast and Extensible DRAM Simulator"
  IEEE Computer Architecture Letters (***CAL***), March 2015.
  [Source Code]

- Source code is released under the liberal MIT License
  - https://github.com/CMU-SAFARI/ramulator

Ramulator: A Fast and Extensible DRAM Simulator

Yoongu Kim[1] Weikun Yang[1,2] Onur Mutlu[1]
[1]Carnegie Mellon University [2]Peking University

Extra Credit Assignment

- Review the Ramulator paper
  - Send your reviews to me (omutlu@gmail.com)

- Download and run Ramulator
  - Compare DDR3, DDR4, SALP, HBM for the libquantum benchmark (provided in Ramulator repository)
  - Upload your brief report to Moodle and send an email to our instructor mailing list